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# An examination of the use of an HP9836 desktop computer in microelectronic device characterization experiments.

F Matthew Rhodes

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AN EXAMINATION OF THE USE OF AN HP9836  
DESKTOP COMPUTER  
IN MICROELECTRONIC DEVICE CHARACTERIZATION EXPERIMENTS

by

F. Matthew Rhodes

A Thesis  
Presented to the Graduate Committee  
of Lehigh University  
in Candidacy for the Degree of  
Master of Science  
in the Department of  
Electrical and Computer Engineering

Lehigh University

May 1983

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## ABSTRACT

This thesis examines the use of an HP9836 desktop computer in two microelectronic device characterization experiments. The first is the Pulsed C-t experiment utilizing the Zerbst analysis technique. From this experiment values of surface recombination velocity and recombination lifetime are derived. The second experiment is an admittance measurement with the analysis based on the theory of Nicollian and Goetzburger. The theory of the measurements are examined. A discussion of automation techniques and advantages is included.

## INTRODUCTION

Today's society is increasingly affected by the advent of the computer. It is utilized to save man the drudgery and boredom of well-defined repetitious tasks and speed the results of tedious and often untenuable numeric calculations. It has entered the home, the business office and in the case of current concern, the experimental laboratory. The question addressed by this thesis is, "What is the role of the computer in an experimental laboratory?". To resolve this question, the paper will examine the use of an HP9836 desktop computer in the control and analysis of several microelectronic device characterization experiments. Through these experiments the advantages and limitations of the computer's use will be apparent.

Each experiment begins with a discussion of the device physics involved followed by experiment documentation. The last part of each section includes a discussion of the programming techniques and their advantages.

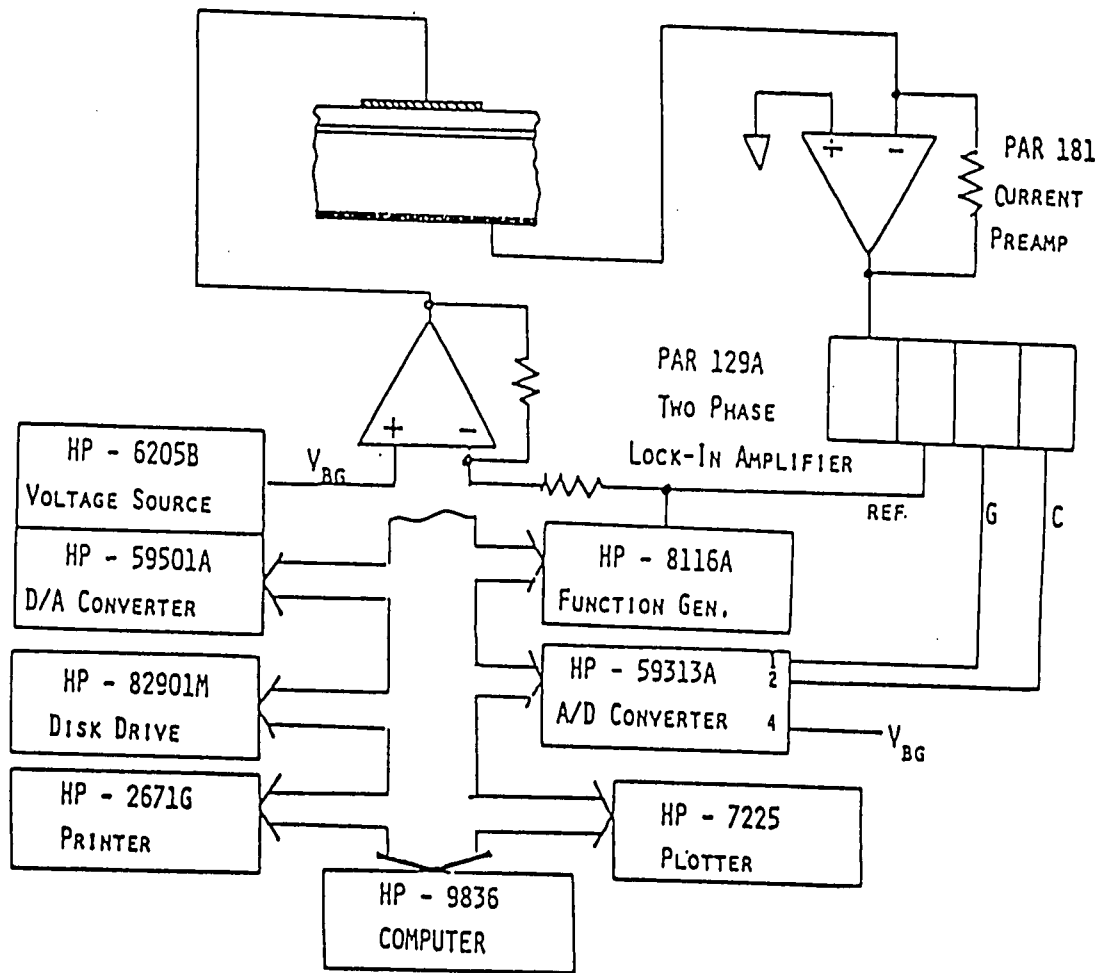
The thesis concentrates on two experiments. The first experiment is the non-equilibrium or 'Pulsed' C-t experiment. Here the computer applies a voltage pulse across the terminals of a MOS capacitor and the

resulting capacitance transient is monitored. This experiment is especially interesting because it demonstrates the measurement of time by the computer. The data in this experiment is analyzed with the Zerbst technique. The second experiment measures the admittance of a MOS capacitor as it is swept through various equilibrium bias states. In this experiment the time factor is not a problem; however, there will be much more instrumental control involved. The data is analyzed with a theory developed by Nicollian and Goetzberger. This experiment is more concerned with the interaction between the user and the computer, since in this case control is not completely automatic. Instead some compromise between automatic and manual control causes some special programming considerations.

The equipment available in the laboratory for automation includes the HP9836 computer and several peripheral instruments which the computer communicates with over a Hewlett-Packard Interface Bus (HP-IB). The measurement equipment includes an A/D converter with four measurement channels for data acquisition, three D/A converters for DC voltage control and a programmable function generator to create measurement signals. A

schematic of this setup is included on the following page. This equipment and the software packages developed form the basis of this thesis.

5



Schematic of Laboratory Set-up in Device Characterization Lab

PART 1

PULSED C-t EXPERIMENT



## THEORY OF THE PULSED C-t EXPERIMENT

The problem, in general, is to study how a MOS device comes to thermal equilibrium after an external electrical disturbance. More specifically, a MOS device is pulsed from some equilibrium bias level to a non-equilibrium deep depletion level. The device capacitance is monitored as the charges redistribute until a new equilibrium state occurs. The mechanisms of charge redistribution will be discussed and several proposed methods of analysis will be presented. The analytical method of Zerbst /6/ will be discussed in detail with experimental results given. Further correction to this analysis will also be given.

When the device is pulsed into deep depletion the majority and minority carrier quasi-fermi levels ( $\mu_{n,p}$ ) will separate. Because of this carriers will redistribute themselves until equilibrium is reached (Figure 1.1). There are basically three electrical paths through which charge can redistribute: 1) Carrier pair generation in the bulk, 2) Carrier generation through surface states, and 3) Diffusion of carriers through the bulk (minority carriers). Historically some sort of resistive network has been associated with each of these paths so that the

MOS capacitor can be represented by an A.C. equivalent circuit. This equivalent circuit was first proposed by Lehovec and Slobodsky /7/ and was fully discussed by Hofstein and Warfield /2/. The equivalent circuit is shown in Figure 1.2.

The equivalent circuit proposed is quite cumbersome and some simplifying assumptions must be made before it can be analyzed. First, the modulation of the inversion layer width is small and so the inversion capacitance can be considered infinite. The capacitance associated with the surface states is small and can be neglected. Applying these approximations the equivalent circuit becomes three resistive paths to ground in parallel with the depletion capacitance all in series with the oxide capacitance. The relative importance of these paths was carefully considered by Hofstein and Warfield /2/. They concluded that under the conditions of heavy inversion the resistance associated with the pair generation will dominate the response. The resistive path through the surface states may also be effective in devices with low bulk generation rates (high lifetimes). See Figure 1.3 for the equivalent circuit.

As a note, if there is a finite conductance along the surface of the device, then there will be an RC

network attached to the circuit of Figure 1.3 which will invalidate the analysis. The experiment therefore must be designed to minimize this surface conductance.

Two methods of analysis will be considered, one by Hofstein /1/ in which he considered only generation in the bulk and one by Zerbst /6/ in which bulk generation and surface generation were considered.

The analysis by Hofstein considers the equivalent circuit shown in Figure 1.4. For this circuit it was shown by Sah et al. /3/ that:

$$R_g = \tau_o \left( \frac{V_{sp}}{qn_i d} \right) \quad (1.1)$$

where  $V_{sp}$  = voltage across space charge region

$\tau_o$  = generation lifetime

$d$  = depletion layer width

With this expression for resistance the RC time constant of this circuit is:

$$\tau_r = \tau_o \left( \frac{V_{sp}}{qn_i d} \right) * (C_d + C_{ox}) \quad (1.2)$$

Utilizing the relations:

$$d = \frac{\epsilon_s}{C_d} \quad \& \quad C_m = \frac{C_{ox} C_d}{C_{ox} + C_d} \quad (1.3)$$

Equation (1.2) can be solved to  $\tau_o$  to give:

$$\tau_o = \tau_r \left( \frac{V_{sp}}{qn_i \epsilon_s} \right) \frac{C_{ox}^3 C_m}{(C_{ox} - C_m)^2} \quad (1.4)$$

Hofstein used this result to experimentally measure the recombination lifetime. To make sure his analysis was valid Hofstein superimposed a small step voltage ( $\sim 25\text{mV}$ ) over a bias voltage which kept his device in heavy inversion. This insured low surface recombination velocity since in heavy inversion most of the surface states are full. With his experimental setup he was able to obtain reasonable values of lifetime for his devices. Hofstein's experiment is represented schematically in Figure 1.5.

The analytical method of Zerbst is more complicated than that of Hofstein's in that it considers both surface effects and bulk effects. As shown in Appendix A, a relationship can be derived between the capacitances

measured in a non-equilibrium experiment:

$$-\frac{d}{dt} \left( \frac{C_{ox}}{C} \right)^2 = \frac{2C_{ox}}{N_d C_f} \left[ \frac{n_i}{2\tau_g} \left( \frac{C_f}{C} - 1 \right) + \frac{n_i C_f S}{\epsilon_s} \right] \quad (1.5)$$

If the bulk generation lifetime and the surface recombination velocity are constant, then a plot of  $\frac{d}{dt} \left( \frac{C_{ox}}{C} \right)^2$  versus  $\frac{C_f}{C} - 1$  will yield a straight line. Looking at the converse of this statement, a straight line fit to a good portion of a plot of these two variables provides a slope and intercept which yield the generation lifetime and the surface recombination velocity. This analysis technique is carried out in the experimental section.

A consideration due to Nathanson and Schroder /3/ is that upon application of a deep depleting voltage step a lateral spread of the space charge region occurs in addition to the longitudinal penetration. This lateral portion can be extremely important because the exposed surface does not invert leaving many surface states unoccupied and therefore maintains a high surface recombination velocity. The return to equilibrium then occurs due to three processes:

- (i) - Bulk generation with lifetime  $\tau_g$

- (ii) - Surface generation of the lateral surface with recombination velocity  $S_o$  (depleted surface)
- (iii) - Surface generation of the surface under the gate with recombination velocity  $S$ .

Re-examining equation (A-3) in Appendix A in the Zerbst analysis in conjunction with Figure 1.6 the expression for  $\frac{dQ_i}{dt}$  can be written as:

$$\frac{dQ_i}{dt} = \frac{qn_i}{2\tau_g}(W-W_f) + qn_i \frac{A_g}{A} + n_i S_o (W-W_f) \frac{P}{A} \quad (1.6)$$

where  $A_g$  = area of the gate =  $\pi r^2$   
 $A$  = area of the gate & lateral surface  
 $P$  = peripheral length of the gate

For a circular gate of diameter  $d$  Equation (1.6) becomes:

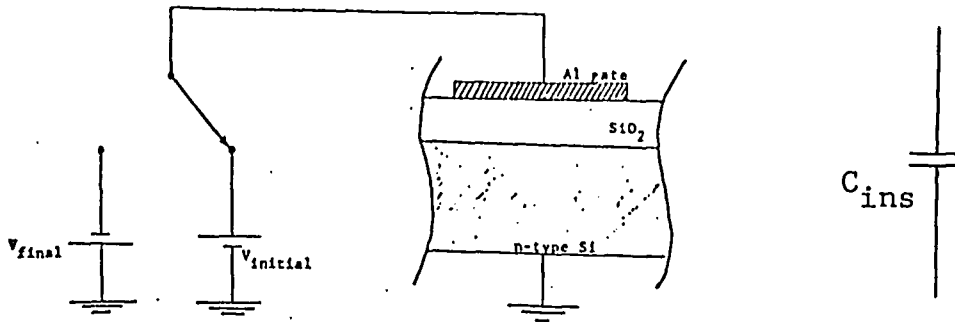
$$\frac{dQ_i}{dt} = qn_i (W-W_f) \left( \frac{1}{\tau_g} + \frac{4S}{d} + \frac{4S_o}{d} \right) + n_i S \quad (1.7)$$

For the linear portion of the Zerbst plot  $S \ll S_o$  so that equation (1.7) can be written as:

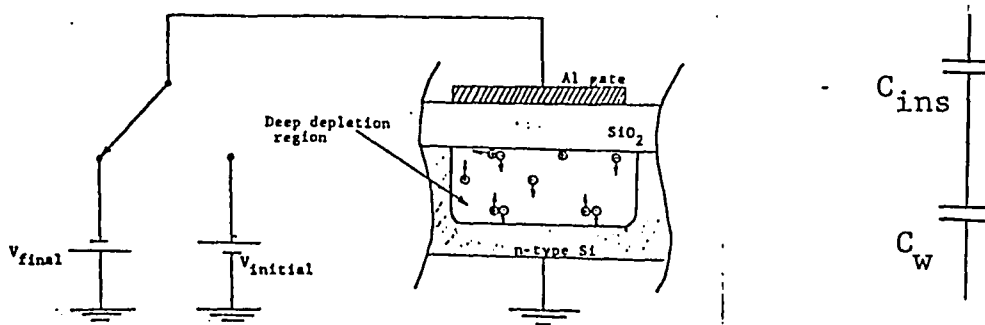
$$\frac{dQ_i}{dt} = qn_i \frac{(W-W_f)}{\tau_g'} + n_i S \quad (1.8)$$

where  $\tau_g' = \left( \frac{1}{\tau_g} + \frac{4S_o}{d} \right)^{-1}$

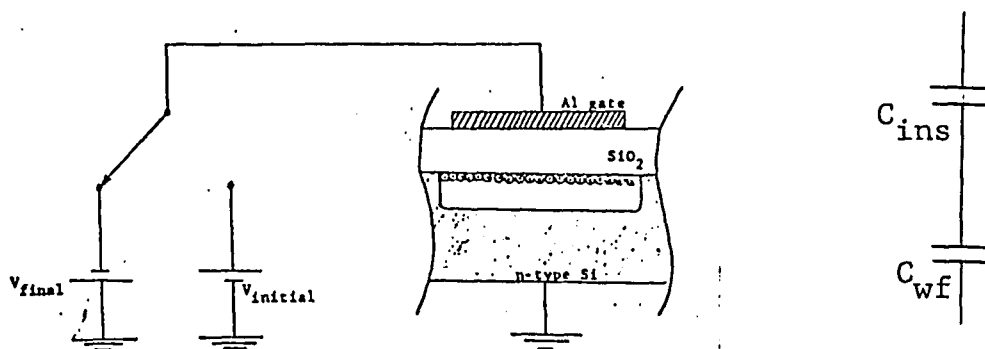
Thus according to Schroder and Nathanson the lifetime that is measured must be corrected because it includes a component of surface generation from a non-inverted surface. This additional correction is not considered in the analysis of the experimental section.



(a) Device set to initial equilibrium bias (accumulation on n-type Si shown). Equivalent circuit is shown.



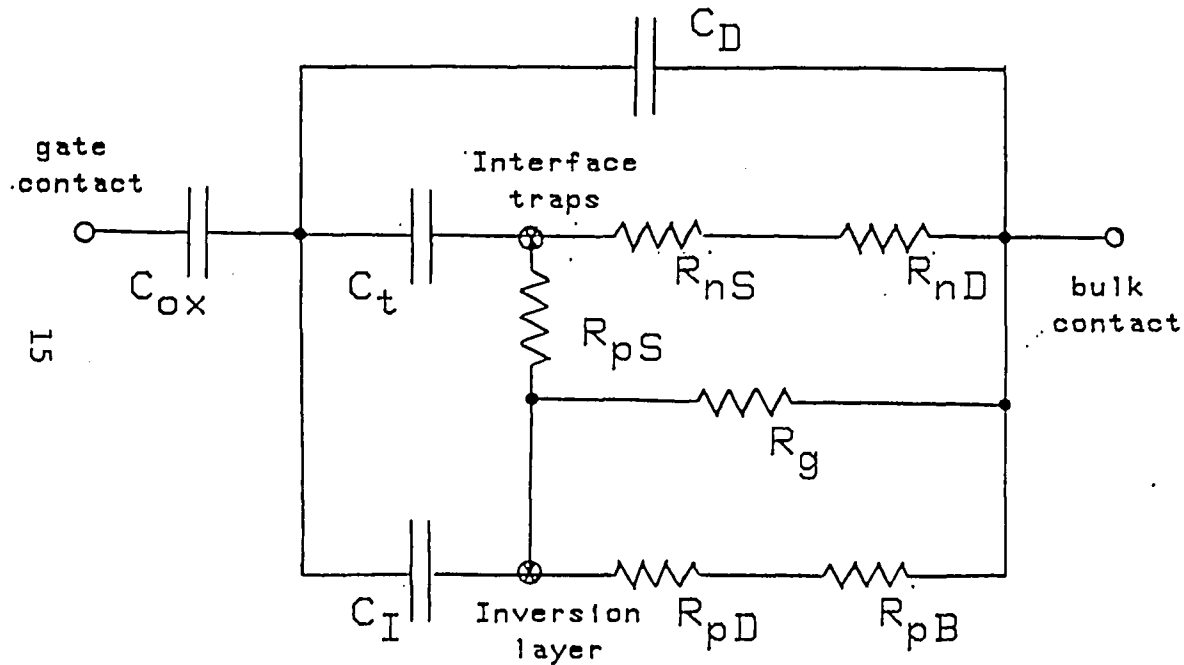
(b) Device immediately after voltage pulse. Non-equilibrium deep depletion region has formed. Pair generation occurring in depletion region and at surface to bring device back to equilibrium.



(c) Device after long time has returned to equilibrium. Inversion layer has formed at surface.

Fig. 1.1 - Schematic Representation of Pulsed C-t Experiment





- $C_{ox}$  - Oxide Capacitance
- $C_D$  - Depletion layer Capacitance
- $C_I$  - Inversion layer Capacitance
- $C_t$  - Trap Capacitance
- $R_{pD}$  - Hole dep. layer resistance
- $R_{pB}$  - Hole bulk resistance
- $R_{pS}$  - Hole trapping resistance
- $R_g$  - Pair Generation resistance
- $R_{nS}$  - Electron trapping resistance
- $R_{nD}$  - Electron dep. layer resistance

Figure 1.2 - Equivalent Circuit of Lehovec & Slobodsky

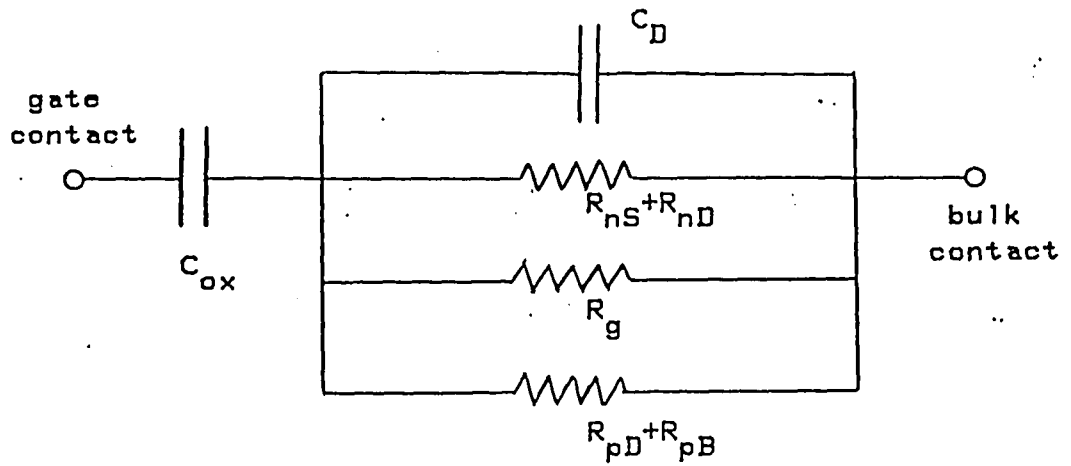


Figure 1.3 - Simplified Equivalent Circuit

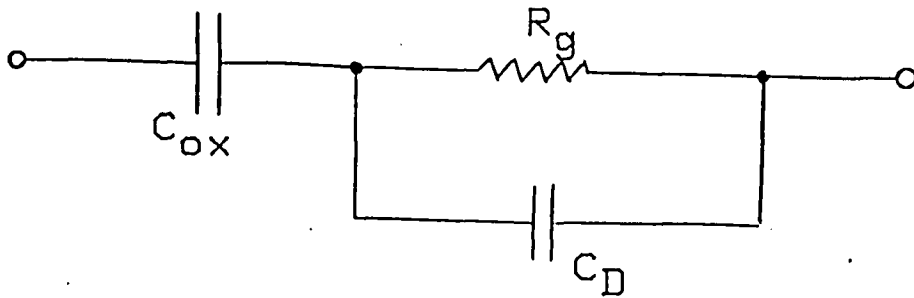


Figure 1.4 - Equivalent Circuit Considered by Hofstein

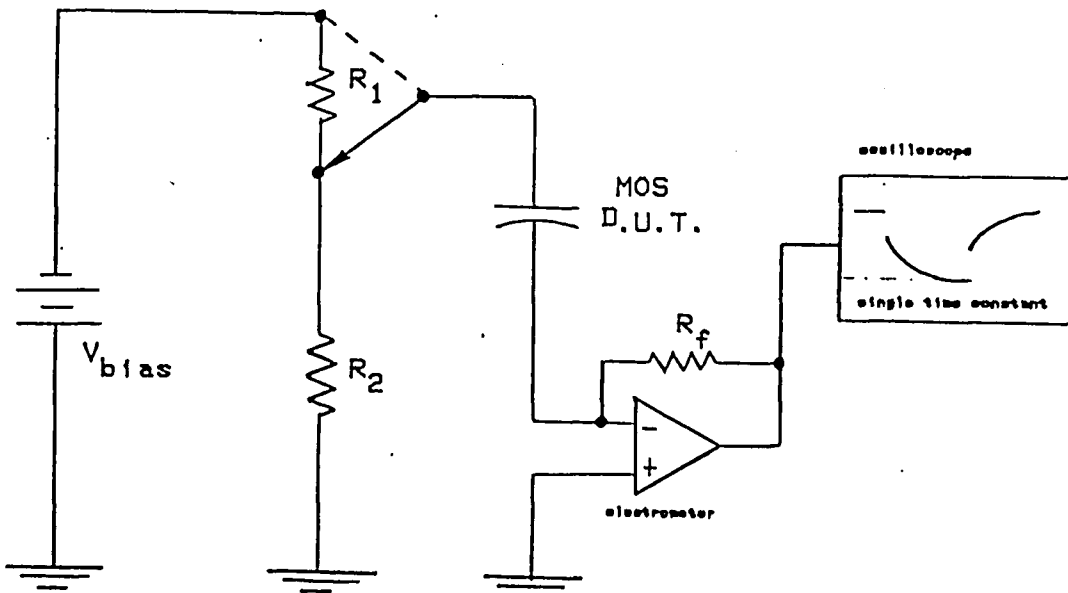


Figure 1.5 - Schematic Representation of Hofstein's Experiment

cross section

top view

note lateral  
depletion area

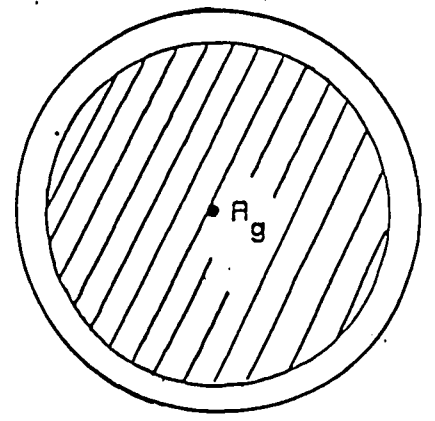
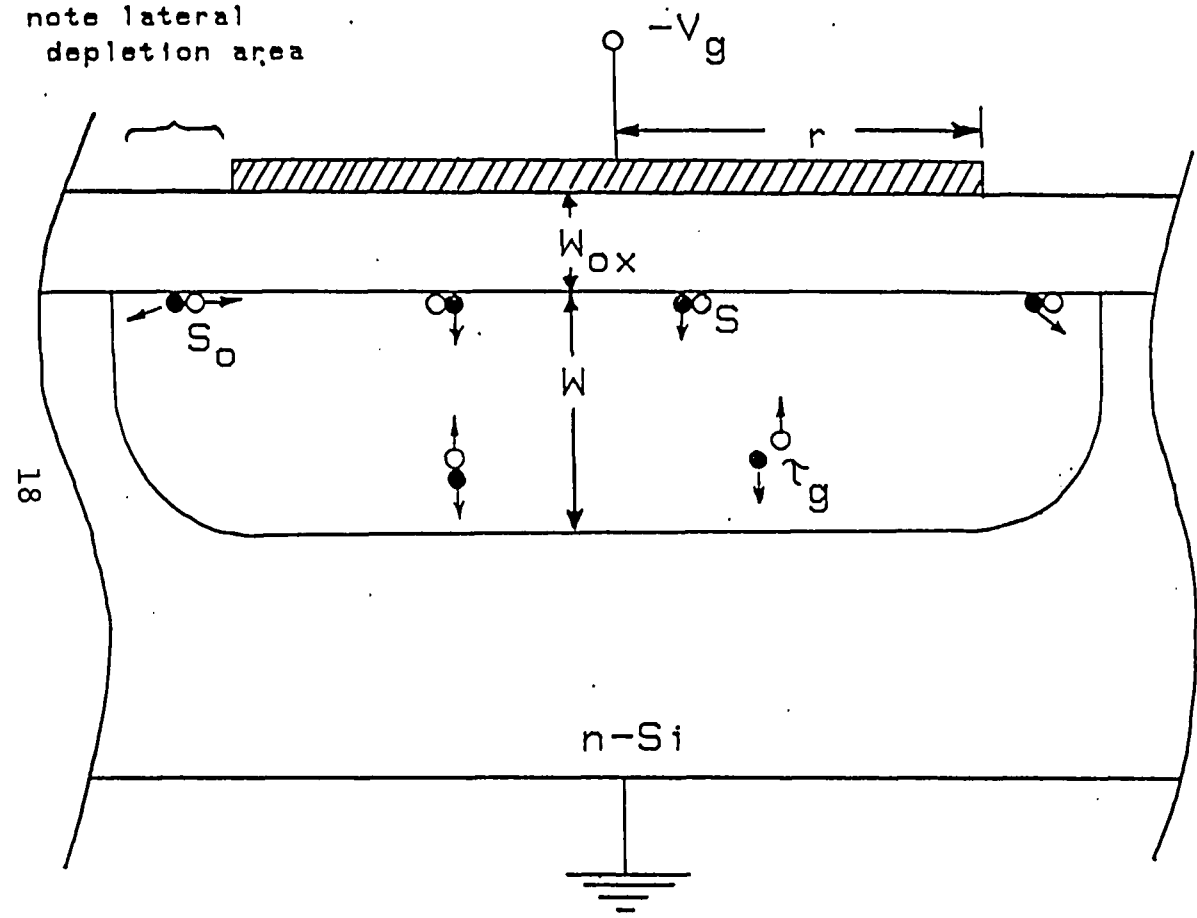


Figure 1.6 - Device Considerations of Nathanson & Schroder

## PULSED C-t EXPERIMENTAL PROCEDURE

The pulsed C-t experiment is performed in the device characterization laboratory under the control of the HP9836 computer with loaded control program. The control program is documented in Appendix E; the experimental configuration is shown in Figure 1.7.

Briefly, at the beginning of the experiment, the device is set to a desired bias level. The control program monitors the device capacitance by taking measurements at the selected pacing rate of the A/D converter. When a software key is pressed a voltage pulse is applied to the device. The 9836 continues to monitor the capacitance while the device returns to equilibrium. The experiment completes when the computer has gathered 1000 data points at which time data analysis can occur.

The measurements presented in this section are taken on a simple MOS .75mm circular dot capacitor. A microphotograph of the device is shown in Figure 1.8. The device was fabricated with a standard MOS capacitor process: The silicon was precleaned followed by a gate oxidation at 1100°C for 40 min in a dry oxygen atmosphere, which grew approximately 1000Å of oxide. Subsequently,

the oxide was annealed in-situ for 15 min in nitrogen. To complete processing an aluminum gate was deposited by filament and photographically etched. Back contact was formed with an aluminum deposition followed by a "sinter" operation at 450°C in forming gas. A table of device parameters is shown in Table 1.1.

Two pulsed measurements were performed on this device. In the first, the device was set initially into strong accumulation by the application of +5V equilibrium bias on the gate. A -15V pulse was applied causing a final bias of -10V, well into inversion. A capacitance transient was observed which lasted approximately 1 minute. The capacitance versus time curve is shown in Figure 1.9. Data analysis was performed with the Zerbst technique as documented in Appendix E. The results of curve fitting are shown in Table 1.2. It is important to note that the best fits are found corresponding to the data at the end of the transient. At this point in the transient the surface is heavily inverted and therefore the surface recombination velocity calculated corresponds to a heavily inverted surface. In a heavily inverted surface, with most of the surface states filled and therefore a lack of recombination centers, the surface recombination velocity should be low. The results are shown

in the Zerbst plot of Figure 1.10.

A second set of measurements were performed on the same device in which the initial equilibrium bias was set at -3V, already in inversion. A -7V pulse was applied which again caused a final bias of -10V. The resulting capacitance transient is shown in Figure 1.11. The calculated recombination lifetime and surface recombination velocity are very consistent between the two measurements. Note that in the Zerbst plot of the second measurement (Figure 1.12) the fitted straight line follows the data for a much greater portion of the transient. This is consistent since the device was initially set into inversion and therefore the surface is heavily inverted for a much larger portion of the transient. The Zerbst assumptions of constant surface recombination velocity and recombination lifetime are valid for a larger portion of the transient in the second measurement and therefore the second measurement could be considered the better of the two. The consistency between measurements can be accounted for since as noted the data was fit at the end of the transient of the first measurement where the surface is heavily inverted.

These results point to the validity of the Zerbst

technique as applied in this program.



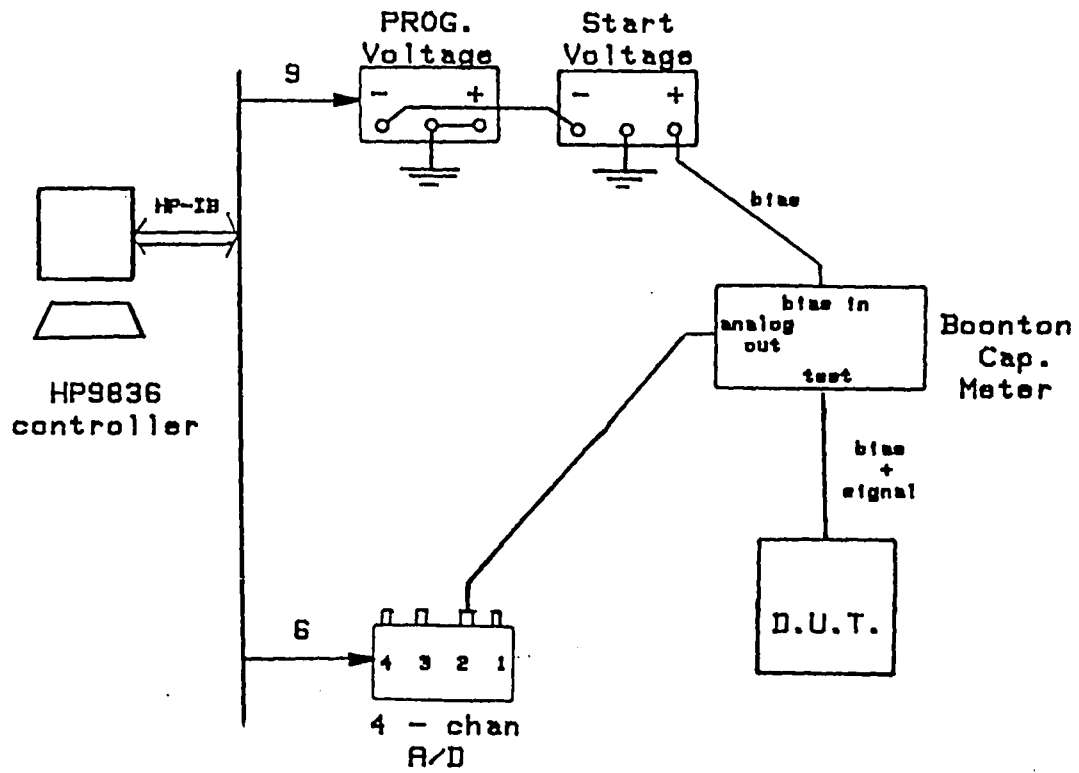


Figure 1.7 - Experimental Configuration of Pulsed C-t Experiment

Table 1.1 Device Parameters for Measured MOS Capacitor

Sample Name:	T2 N 100
Doping Type:	N
Doping Density:	$1 \times 10^{15} / \text{cm}^3$
Gate Area:	$4.42 \times 10^{-3} \text{cm}^2$
Oxide Thickness:	$810 \pm 10 \text{ \AA}$
Oxide Capacitance:	$185 \pm 5 \text{ pF}$
Temperature:	295 deg C

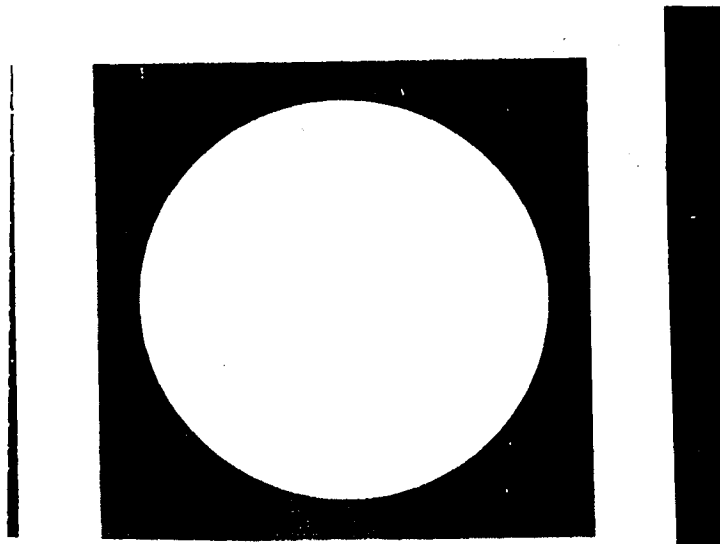


Figure 1.8 - Microphotograph of circular MOS capacitor.

Table 1.2 The results of the data analysis technique is shown for the device pulsed from accumulation to inversion. The results for the function coefficients from linear least square fit are shown at the top, a comparison of the actual and fitted data is also shown. Results of the regional linear least square fit is shown at the bottom.

FUNCTION COEFFICIENTS AND RESIDUAL VARIANCE FROM CURVE FIT

COEFFICIENTS:  
 A 1--1541.65690164  
 A 2- 6051.52507551  
 A 3--5976.48854744  
 A 4- 2521.98298402  
 A 5--924.209361768  
 A 6- 148.709140874  
 A 7--.12058494722  
 A 8- 57.9882341168  
 A 9--31.6000339468

RESIDUAL VARIANCE- 1.85079928367

COMPARISON OF SEVERAL DATA POINTS WITH FITTED CURVE

POINT NO.	DATA POINTS	FITTED POINTS
1	304.4194	304.4203
27	253.7788	247.6586
53	206.4575	207.8153
79	177.5193	175.7777
105	149.1655	149.3327
131	127.0996	127.2391
157	109.5910	108.6720
183	92.9702	93.0305
209	79.8626	79.8518
235	69.3435	68.7655
261	59.5009	59.4670
287	51.6144	51.7010
313	45.1979	45.2492
339	39.9075	39.9232
365	35.4945	35.5581
391	31.7749	32.0083
417	29.0331	29.1442
443	26.6314	26.8496
469	24.8506	25.0199
495	23.5514	23.5600
521	22.6428	22.3833

REPORT FROM LEAST SQUARE LINE FIT TO CURVE

TEST LINES:	SLOPE	INTERCEPT	RESIDUAL VAR
	7.5258	-2.5055	.479477
	6.7122	-1.5559	.175721
	6.1693	-.9246	.080142
	5.7602	-.6019	.041751
	5.4532	-.3470	.025872
	5.1965	-.1615	.017014
	4.9834	-.0283	.012143
	4.7971	.0693	.008171
	4.6296	.1411	.004708
	4.4806	.1928	.002131
	4.3709	.2240	.000915
	4.2968	.2404	.000446

FITTED SLOPE: 4.2968  
 FITTED INTER: .2404

Table 1.3 The Results of the Data Analysis Technique on Device Pulsed from Light to Heavy Inversion.

FUNCTION COEFFICIENTS AND RESIDUAL VARIANCE FROM CURVE FIT

COEFFICIENTS:

A 1- 209.432000148  
 A 2--25.4296337772  
 A 3- 105.900992832  
 A 4- 25.627512343  
 A 5--111.210591245  
 A 6- 31.2126212615  
 A 7--.0312139653478  
 A 8--.355070931589  
 A 9- 1.86298931607

RESIDUAL VARIANCE- 1.27421661449

.....COMPARISION OF SEVERAL DATA POINTS WITH FITTED CURVE.....

POINT NO.	DATA POINTS	FITTED POINTS
1	253.7788	253.7781
25	214.7983	213.5590
49	184.1550	180.1994
73	154.2648	153.6543
97	131.1025	131.9202
121	112.7906	113.7950
145	98.0635	98.5036
169	86.0432	85.5106
193	74.3247	74.4254
217	64.8467	64.9518
241	57.0726	56.8579
265	49.6483	49.9576
289	44.3798	44.0985
313	39.2283	39.1538
337	34.9243	35.0160
361	31.7749	31.5936
385	29.0331	28.8072
409	26.6314	26.5877
433	24.8506	24.8743
457	23.5514	23.6131
481	22.6428	22.7562

REPORT FROM LEAST SQUARE LINE FIT TO CURVE

TEST LINES:

SLOPE	INTERCEPT	RESIDUAL VAR
-2.3737	8.6368	560.650468
7.2276	-2.0890	.320473
6.5032	-1.2964	.183697
5.9181	-.7325	.095930
5.4688	-.3507	.051010
5.1260	-.0979	.025233
4.8679	.0661	.011139
4.6925	.1606	.004782
4.5704	.2149	.001813
4.5063	.2361	.000870
4.4778	.2394	.000584
4.5087	.2220	.000969
4.5892	.1927	.001741

FITTED SLOPE: 4.4778  
 FITTED INTER: .2394

# CAPACITANCE VS. TIME

GRAPH DATE: 29 MAR 1983  
 MCAS. DATE: 28 MAR 1983

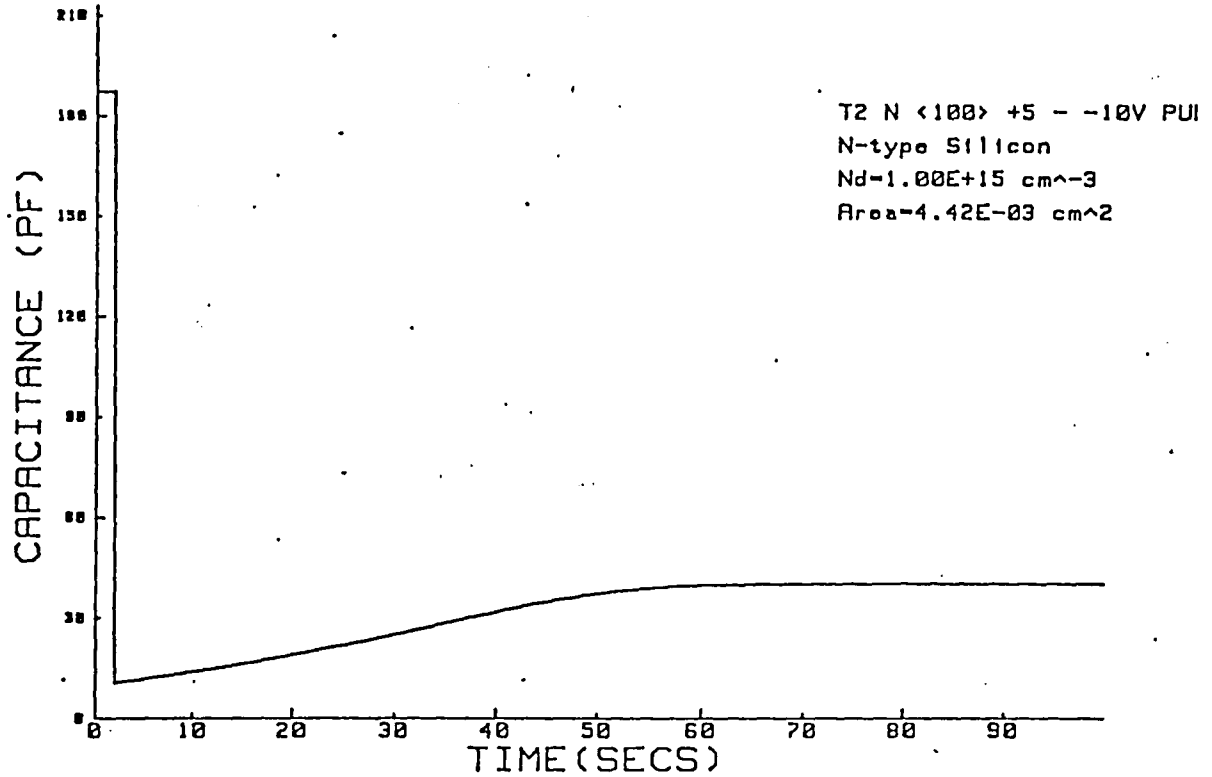


Figure 1.9 Capacitance vs. Time curve for MOS capacitor pulsed from accumulation into inversion. The initial capacitance is the accumulation capacitance which corresponds to the oxide capacitance. After pulse a non-equilibrium deep depletion capacitance is observed which eventually recovers to an equilibrium inversion capacitance.

# CAPACITANCE VS. TIME

GRAPH DATE: 129 APR 1983  
 NUMS: DATE: 128 APR 1983

T2 N <100> +5 -- -10V PUI  
 N-type Silicon  
 ND-1.00E+15 cm^-3  
 Area-4.42E-03 cm^2

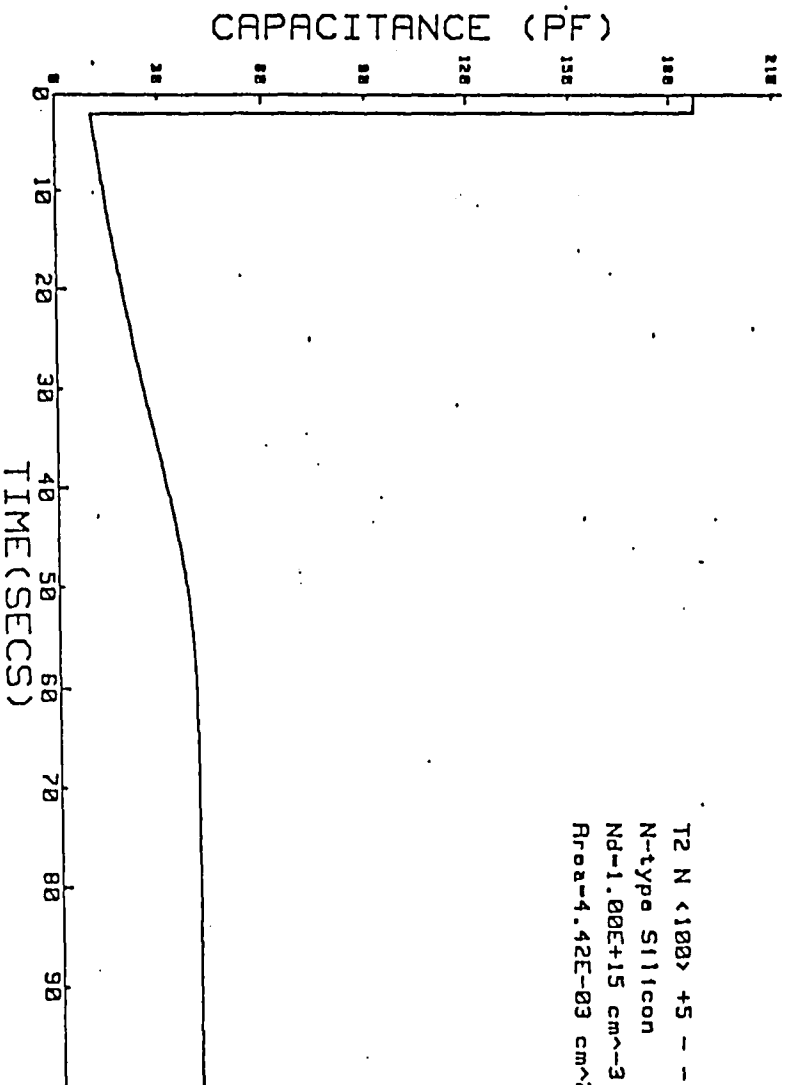


Figure 1.9 Capacitance vs. Time curve for MOS capacitor pulsed from accumulation into inversion. The initial capacitance is the accumulation capacitance which corresponds to the oxide capacitance. After pulse a non-equilibrium deep depletion capacitance is observed which eventually recovers to an equilibrium inversion capacitance.

# ZERBST PLOT

GRAPH DATE: 29 MAR 1983  
 REVS. DATE: 28 MAR 1983

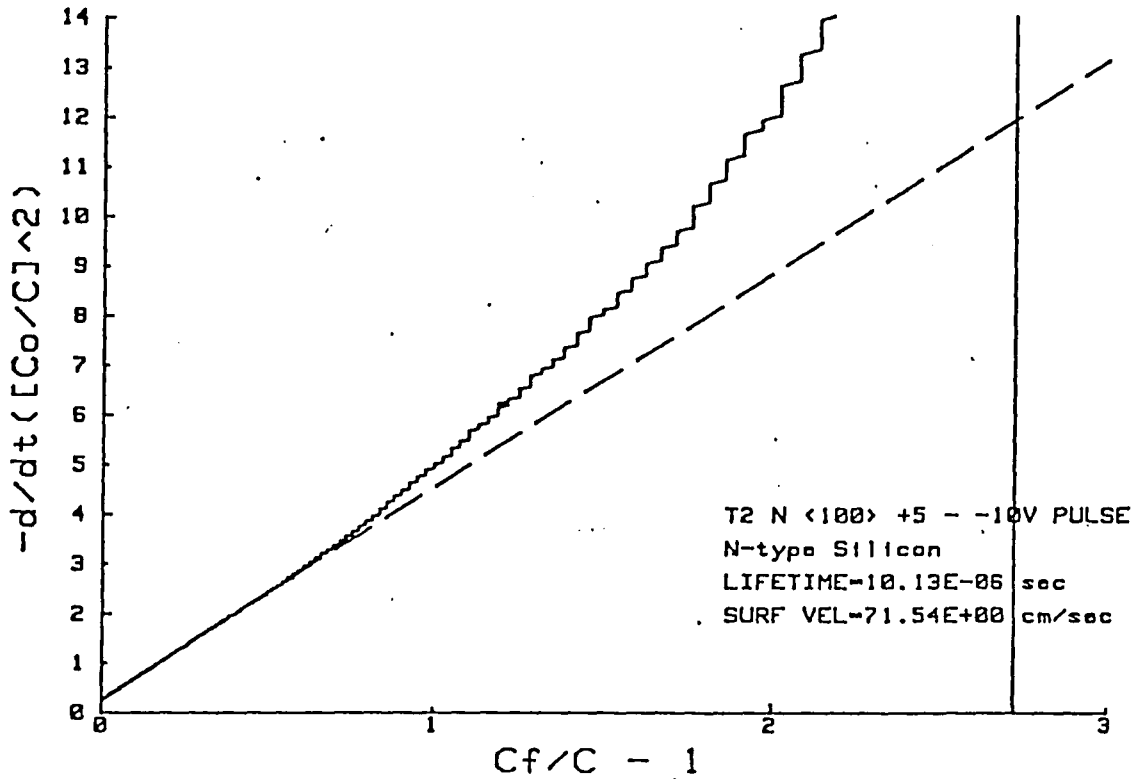


Figure 1.10 Zerbst plot of  $d/dt(C_o/C)^2$  vs.  $C_f/C - 1$  for capacitor pulsed from accumulation into inversion. Data points correspond to the solid line. Dotted line is best straight line fit to a portion of the graph. Note that fit occurs at low values of  $C_f/C - 1$  which corresponds to the end of the transient.<sup>f</sup> Values of lifetime and surface velocity shown are calculated from slope and y-intercept of fitted straight line.

# ZERBST PLOT

GRAPH DATE:29 APR 1962  
 MESS. DATE:28 APR 1962

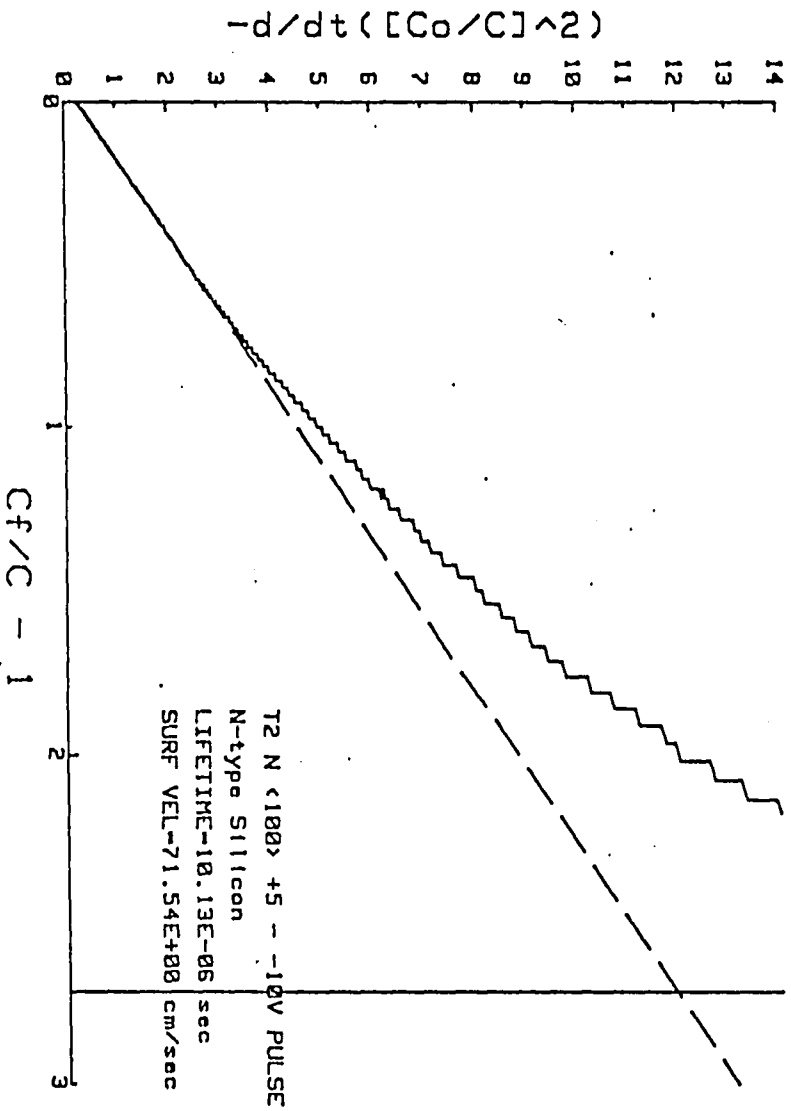


Figure 1.10 Zerbst plot of  $d/dt(C_f/C)^2$  vs.  $C_f/C - 1$  for capacitor pulsed from accumulation into inversion. Data points correspond to the solid line. Dotted line is best straight line fit to a portion of the graph. Note that fit occurs at low values of  $C_f/C - 1$  which corresponds to the end of the transient. Values of lifetime and surface velocity shown are calculated from slope and y-intercept of fitted straight line.



# CAPACITANCE VS. TIME

GRAPH DATE: 29 MAR 1983  
 NCHS. DATE: 28 MAR 1983

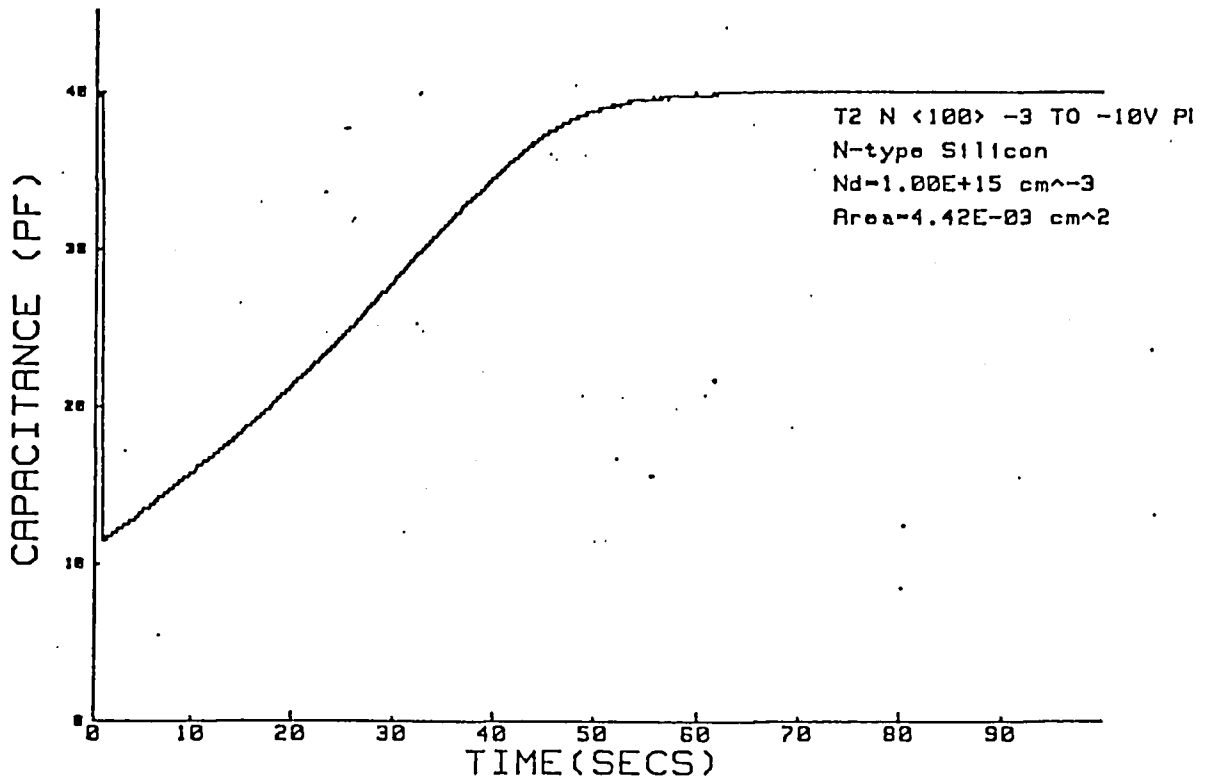


Figure 1.11 Capacitance vs. Time curve for MOS capacitor pulsed from light to heavy inversion. Both initial and final capacitance correspond to equilibrium inversion capacitance. Non-equilibrium deep depletion values of capacitance occur immediately after device is pulsed.

# CAPACITANCE VS. TIME

CORPN DITEL:29 MSR 1983  
MERS. DITEL:28 MSR 1983

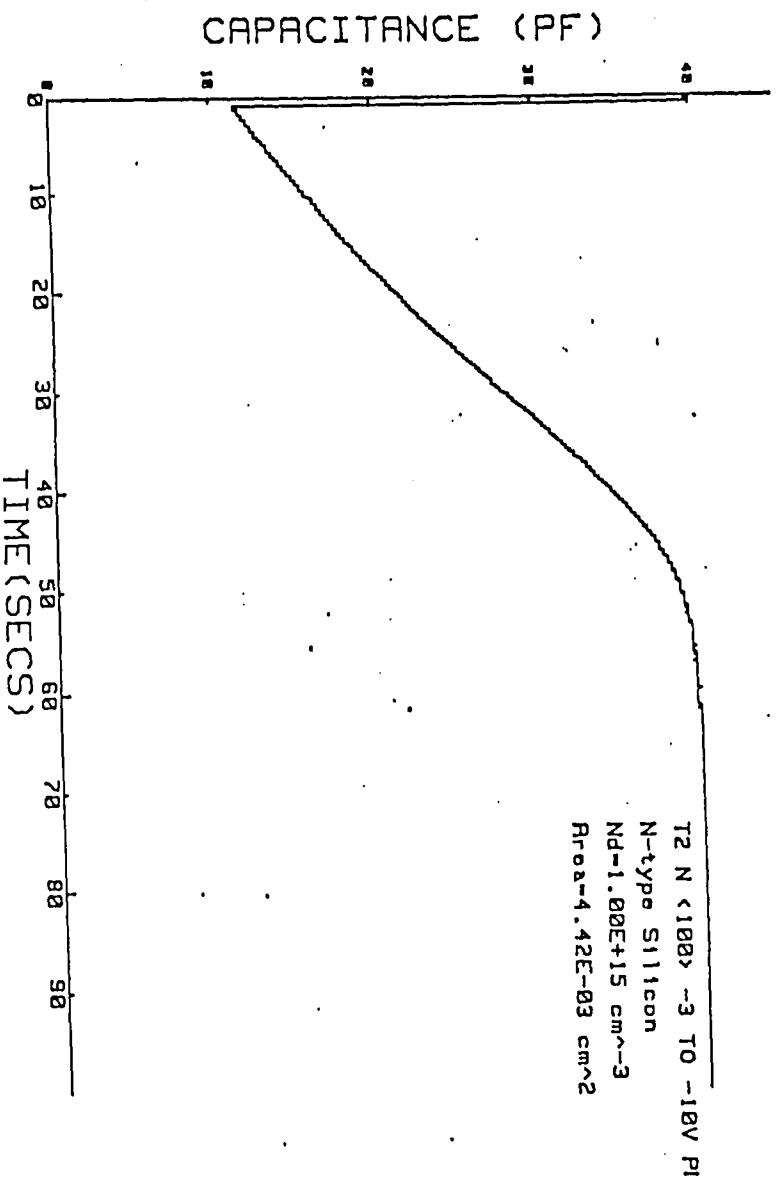


Figure 1.11 Capacitance vs. Time curve for MOS capacitor pulsed from light to heavy inversion. Both initial and final capacitance correspond to equilibrium inversion capacitance. Non-equilibrium deep depletion values of capacitance occur immediately after device is pulsed.

# ZERBST PLOT

GRAPH DATE: 29 MAR 1983  
MEAS. DATE: 29 MAR 1983

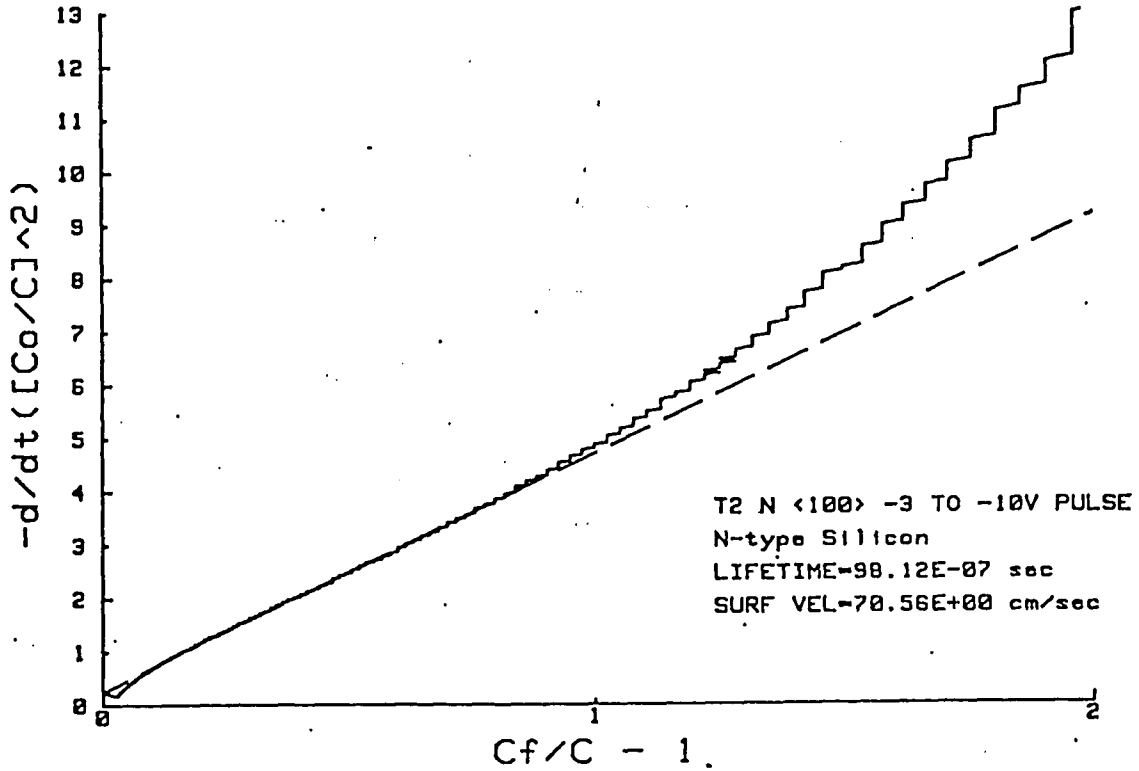


Figure 1.12 Zerbst plot for capacitor pulsed from light to heavy inversion. Data points are shown with solid line and straight line fit with dashed line. Note the large region over which the straight line fit is valid. This is caused by the constant surface condition of heavy inversion.

# ZERBST PLOT

GRAPH DATE: 29 APR 1983  
 MEAS. DATE: 28 APR 1983

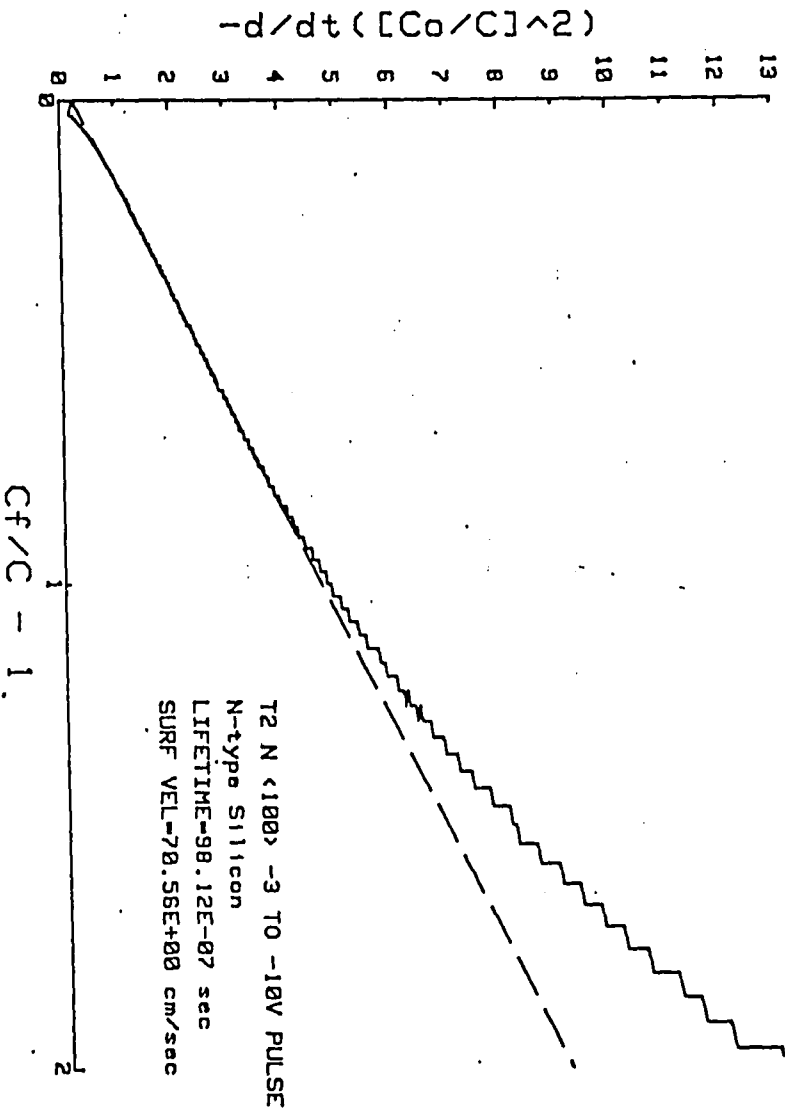


Figure 1.12 Zerbst plot for capacitor pulsed from light to heavy inversion. Data points are shown with solid line and straight line fit with dashed line. Note the large region over which the straight line fit is valid. This is caused by the constant surface condition of heavy inversion.

## DISCUSSION OF PULSED C-t AUTOMATION

The software program used in the control and analysis of this experiment needed to implement a variety of control and data gathering functions as well as data processing techniques. As can be seen by the program listing of Appendix E, the resulting code is well over 1000 lines. Though the documentation of the program should make the code clear there are several factors of the program that deserve discussion.

Though the code is long, it successfully simplifies the task of performing the pulsed C-t experiment. One very general reason that this software package could be considered successful is due to the use of a modular design scheme. The term modular design means that the program is not defined procedurally by instead certain subtasks are programmed which are then made available to the user. In this way the user can define the experimental procedure without reprogramming of the software. For example, the program might have been written such that the user initially provided input parameters followed by data acquisition, and finally analysis. Instead, there are three separate subroutines written to perform each of these tasks, SETUP to get input parameters and

re-initialize the experiment, MEASURE to gather data points, and subroutine ZERBST to perform the Zerbst type analysis on the gathered data. Each of these subroutines (and several others) are then attached to a software key under user control. In this way the user can perform the SETUP and MEASURE subroutines and at this point, if there are initial indications that the data is not good, then the MEASURE routine can be rerun. This type of flexibility seems essential in an experimental environment where procedural need and results can not always be anticipated. This programming philosophy is also apparent in the admittance software documented in this thesis and is suggested for any future program development in the laboratory.

In contrast to the generalized program structure, a software problem specific to the C-t experiment was the monitoring of an experimental parameter with respect to time. The obvious solution to this problem (and the method first attempted) was to obtain the monitored parameter from the data bus line and then obtain the time from the processor's internal clock. The problem in this scheme is that there is a finite amount of time which elapses between the time when the data is gathered and the time when the system clock is checked. If this time

lapse is long compared to the time resolution required, then the time marked for the data will be useless for analysis purposes. An analogy to this scheme of processing would be a single experimenter taking data by hand, say recording a voltage level as recorded on a DVM with respect to time. The experimenter would look at the readout of the DVM and mark its value and then look at the clock and mark the time. If the time necessary to perform this task is longer than any meaningful transients in the voltage level then those transients would be lost.

The problem is solved in this case by the use of an off-line dedicated processor in the form of an A/D converter. With this instrument the control unit (the 9836) presets the A/D by giving it a measurement pacing rate. The A/D is then triggered by some start instruction and then at the given pacing rate the data is presented to the 9836 controller. The analogy here would be an experimenter with an instrument that would only measure at say 5 second intervals. At these times the instrument provides data readouts which the experimenter records. He would then know that the first point occurred at time zero, the second at time 5 seconds, etc.. Because there is less work for the experimenter to do he can record much quicker

transients. This holds true for the computer as well and with this scheme the computer was able to mark the capacitance transient with down to a 5 millisecond resolution.

There are limits to this scheme as well however in that the central controller must be able to accept the data as quickly as it is gathered and because of the generality of the CPU it is not always extremely fast. To record even faster transients the use of dedicated processors with buffered memory is needed. In this way an offline instrument could be instructed to gather data at a given pacing rate and started. At this time the instrument could measure the data and store it in internal memory without trying to communicate with the central controller. At the end of some meaningful observation time the controller would stop the instrument and pull the data from the memory as convenient. The analogy in this case would be an experimenter starting some similar instrument and going for a cup of coffee. At the end of the observation time he could return and stop the instrument and at his leisure pull the data values from the internal memory. This scheme is especially attractive if there is more than one parameter to be monitored. With the use of the offline processor doing the work the number of parameters that can be monitored is limited only by the number of instruments available



instead of the cycling time of the CPU.

Along with the control problem of monitoring time, this experiment raised an interesting data processing problem, the problem of taking the derivative of a set of gathered data points with respect to some other parameter. In this case, the Zerbst analysis requires the time derivative of the created array of  $(C_{\text{ox}}/C)^2$ . This was accomplished in the documented program by performing a least squares fit of the created array to nine analytical functions. Using the extracted function coefficients then, the derivative was taken analytically. This may not, unfortunately, be the best method of attacking this problem. Because of the number of data points and the good resolution of the measurement system it might be better to take the derivative numerically through a differencing technique. If the derivative is found to be not well smoothed due to the digitizing of the data it could at this point be fit in a least square sense. In this way, the unique features of the data would be retained through the derivation process.

The use of this software package is, in general, quite easy and any user can now quickly get excellent estimates of the generation lifetime and surface recombination

velocity. For example, the measurements presented here were all performed in one afternoon. The use of the program however does not necessarily give a better understanding of the physics behind carrier generation and unique devices may not be well characterized by this program due to the many assumptions that go into the Zerbst analysis. For the person who wants a quick measurement of lifetime in a simple device the program is an excellent working tool.

PART 2

ADMITTANCE MEASUREMENTS

## THEORY OF ADMITTANCE MEASUREMENTS

Historically, investigators have demonstrated the usefulness of the capacitance technique in probing the properties of the MOS system. These techniques have some serious limitations as discussed in the paper of Zaininger and Warfield /8/. A more general technique, and the technique of present concern, is to measure the overall admittance of the MOS system. This technique provides both the conductance and the capacitance of the system, and as is shown, the conductance part of the measurement is a much more sensitive indicator of the trapping properties in the MOS system.

Briefly, in this technique a bias is applied between the bulk and the gate of an MOS capacitor which determines the band bending at the Si-SiO<sub>2</sub> interface. This sets the position of the equilibrium Fermi level at some point in the Silicon bandgap. If an AC measurement signal is superimposed on top of this bias, then we can disturb the equilibrium Fermi level slightly. This will cause movement of the charge carriers between the traps and the bands. This population and depopulation of the traps will be detected by the measured admittance. The nature of the interface can be characterized by measuring the admittance

through a complete range of bias and measurement frequency.

To interpret these measurements the admittance of the MOS capacitor is derived assuming Shockley, Read, Hall type traps exist at the interface. This admittance is related to an equivalent circuit of the type proposed by Lehovec /7/. Qualitative observations are made and the theory extended to fit the measurements. In the present work, only majority carrier contributions are analyzed. Where appropriate an indication of how to include minority carrier effects is shown. A complete treatment of this theory is given by Nicollian and Brews in their book, MOS Physics and Technology /10/.

A schematic of the MOS system is shown in Figure 2.1. The physical device is represented in Figure 2.1a and the energy band diagram is shown in Figure 2.1b. The present analysis assumes a good ohmic contact to a perfectly conducting metallic gate which is completely DC isolated from the silicon by the oxide layer. A finite trap distribution will be assumed at the Si-SiO<sub>2</sub> interface. These traps will communicate with both the conduction and valence bands by capture and emission processes. Through donor (n) type doping the electrons in the conduction band far outnumber the holes in the valence band, therefore

electrical connection through detailed balance is made to the conduction band only.

Consider a single level trap located somewhere within the silicon bandgap at the Si-SiO<sub>2</sub> interface. As shown in Figure 2.2 there are four separate processes by which this trap communicates with the conduction and valence band. For a n-type device, in either accumulation or depletion (i.e. n>>p), only the electron capture and emission processes will be of concern. Considering the effect of these processes on the current flowing in the conduction band caused by a small AC signal, it is shown in Appendix C that the small signal admittance of this process in the silicon is given by:

$$Y_s = j\omega \frac{q^2 N_{it} f_o (1-f_o)}{kT \{1 + j\omega f_o / (c_n n_o)\}} \quad (2.1)$$

where  $f_o$  is the equilibrium Fermi function given by:

$$f_o = \frac{1}{1 + \exp \frac{E - E_F}{kT}} \quad (2.2)$$

Looking again at the MOS device in Figure 2.1 a simple equivalent circuit for this system can be proposed. The SiO<sub>2</sub> insulator can be replaced by a simple capacitor, C<sub>ox</sub>.

Assuming the device is biased in depletion there will be some depletion capacitance between the back of the device and the Si-SiO<sub>2</sub> interface. With the assumed trap distribution at the interface there will be additional charge storage at the interface which can be represented by some trap capacitance, C<sub>t</sub>, and fed by a resistive mechanism given by G<sub>n</sub>. Considering the gate, the Si-SiO<sub>2</sub> interface and the silicon back contact to be equipotential surfaces the equivalent circuit of the MOS system is given by Figure 2.3. Analyzing this circuit, the silicon admittance (i.e. ignoring the oxide capacitance) is given by:

$$Y_s' = j\omega C_d + \frac{j\omega C_t G_n}{G_n + j\omega C_t} \quad (2.3)$$

Comparing the second term of this equation to the admittance derived in equation (2.1), G<sub>n</sub> and C<sub>t</sub> can be defined as follows:

$$C_t = \frac{q^2}{kT} N_{it} f_o (1-f_o) \quad (2.4a)$$

$$G_n = \frac{q^2}{kT} N_{it} c_n n_{so} (1-f_o) \quad (2.4b)$$

An extension of this equivalent circuit motivation to include minority carrier effects is shown in Figure 2.4.

For explanation purposes consider the circuit of Figure 2.5 for the device admittance. This circuit represents the silicon system as some conductance,  $G_p$  and some capacitance,  $C_p$  in parallel. Comparing this circuit to the admittance given by equation (2.3),  $G_p$  and  $C_p$  are defined as:

$$\frac{G_p}{\omega} = \frac{C_t \omega \tau}{1 + (\omega \tau)^2} \quad \text{where } \tau = \frac{C_t}{G_n} \quad (2.5a)$$

$$C_p = \frac{C_t}{1 + (\omega \tau)^2} + C_d \quad (2.5b)$$

Plots of the dimensionless quantities  $(G_p/\omega C_t)$  and  $(C_p - C_d)/C_t$  vs. frequency are shown in Figure 2.6.

Note the behavior of the  $(C_p - C_d)/C_t$  curve. At low frequencies the curve approximately equals 1, i.e.  $C_p = C_d + C_t$ . This means that the trap is responding immediately to the AC signal. As the frequency increases the traps no longer respond and the trap capacitance does not enter into the circuit, note:  $(C_p - C_d)/C_t \rightarrow 0$  or  $C_p \rightarrow C_d$ .



Note also the behavior of the  $G_p/(\omega C_t)$  curve. At low frequencies the trap responds in phase with the signal, therefore there is no energy loss and the equations show  $G_p/(\omega C_t) \rightarrow 0$ . As frequency increases the curve peaks at the point where  $\omega\tau=1$ . As  $\omega$  is increased further the traps no longer respond and the curve again goes toward zero.

Though the theoretical curves developed thus far show the same qualitative response as measured curves, the theory is not yet general enough to produce exact fits. So far a simple theory has been developed which indicates how a single energy level interface trap responds to an AC measurement signal. This theory must be extended two ways before the desired fits can be achieved. First, it is a gross simplification to assume a single trapping level at the interface. There is in fact a continuous energy distribution of interface traps. For each trap level there would be a parallel addition to the equivalent circuit consisting of a trap conductance and an electron capacitance as shown in Figure 2.7. To express this mathematically a continuous trap distribution  $D_{it}$  is assumed and the admittance as given by equation (2.1) is integrated over the bandgap. This is shown in Appendix D and the result is given by:

$$\frac{G_p}{\omega} = \frac{qN_{it}}{2\omega\tau_n} \ln(1 + \omega^2\tau_n^2) \quad (2.6a)$$

$$C_p = \frac{qN_{it}}{\omega\tau_n} \tan^{-1}(\omega\tau_n) \quad (2.6b)$$

where  $\tau_n = \frac{1}{c_n n_{so}}$

The second theoretical extension is due to the discrete nature of the fixed oxide charge and other processing effects causing chemical inhomogeneities. This causes a lateral non-uniformity in the location of the Fermi level within the bandgap. To mathematically account for this effect, a Gaussian approximation to a Poisson distributed surface potential will be assumed and the conductance and capacitance as given above in equation (2.6) will be integrated over this distribution. The resulting admittance as shown in Appendix E is given by:

$$\frac{G_p}{\omega} = \frac{qD_{it}}{2\omega\tau_n (2\pi\sigma_s)^{\frac{1}{2}}} \int_{-\infty}^{\infty} \exp\left(-\frac{\eta^2}{2\sigma_s^2}\right) \exp(-\eta) \ln(1 + \omega^2\tau_n^2 \exp 2\eta) d\eta \quad (2.7a)$$

$$C_p = C_d +$$

$$\frac{qD_{it}}{\omega\tau_n (2\pi\sigma_s)^{\frac{1}{2}}} \int_{-\infty}^{\infty} \exp\left(-\frac{\eta^2}{2\sigma_s^2}\right) \exp(-\eta) \tan^{-1}(\omega\tau_n \exp \eta) d\eta \quad (2.7b)$$

$$\text{where } \eta = u_s - \bar{u}_s$$

The resulting equations given equation (2.7) are shown to fit experimental data. A comparison of the conductance curves produced by each of the theories is shown in Figure 2.8.

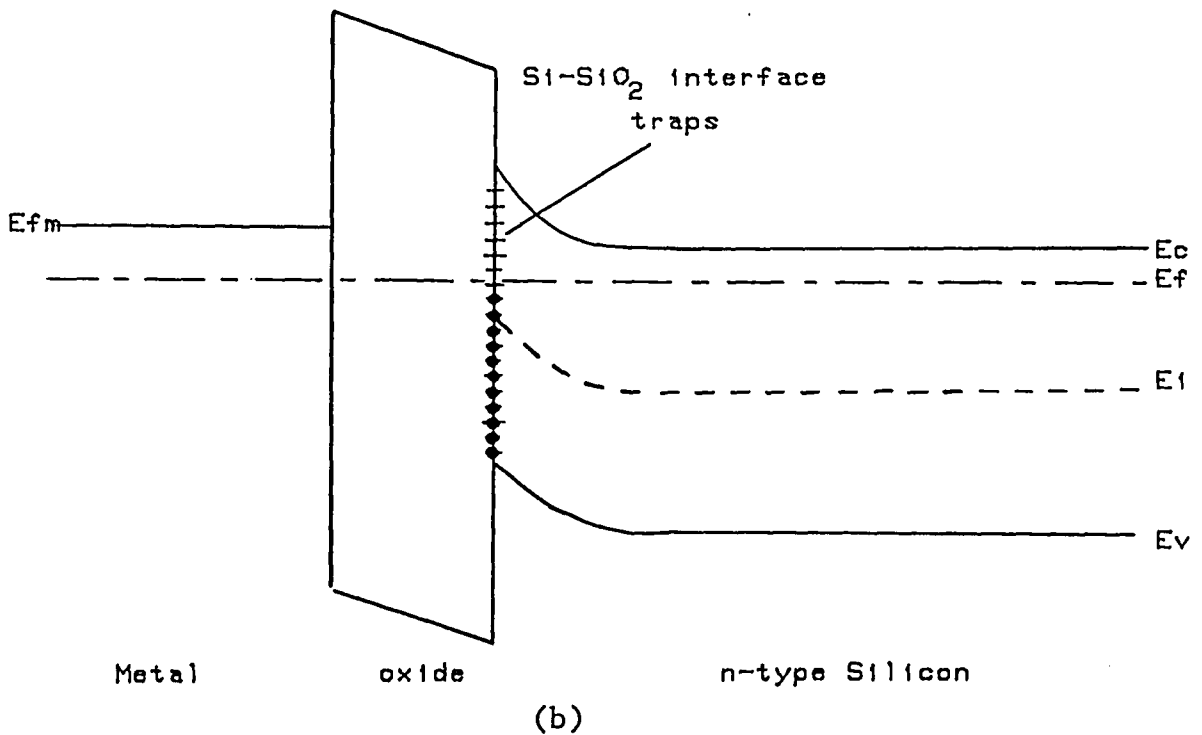
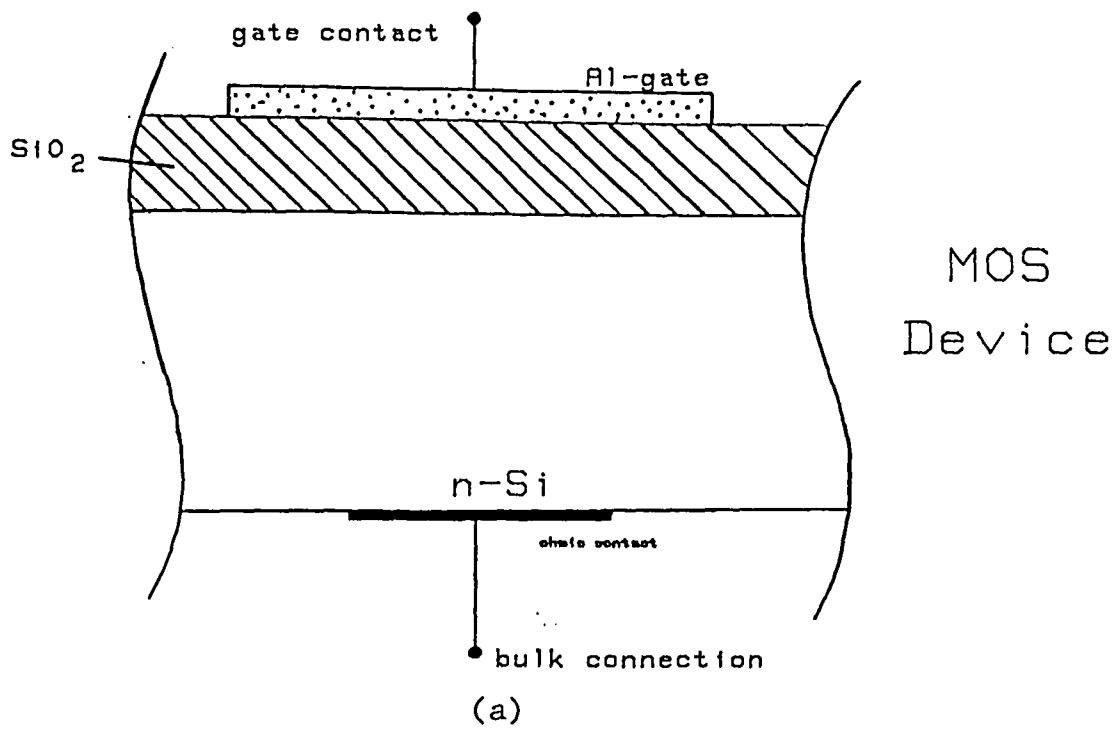


Figure 2.1 - (a) Schematic of MOS System; (b) Band Diagram of MOS System

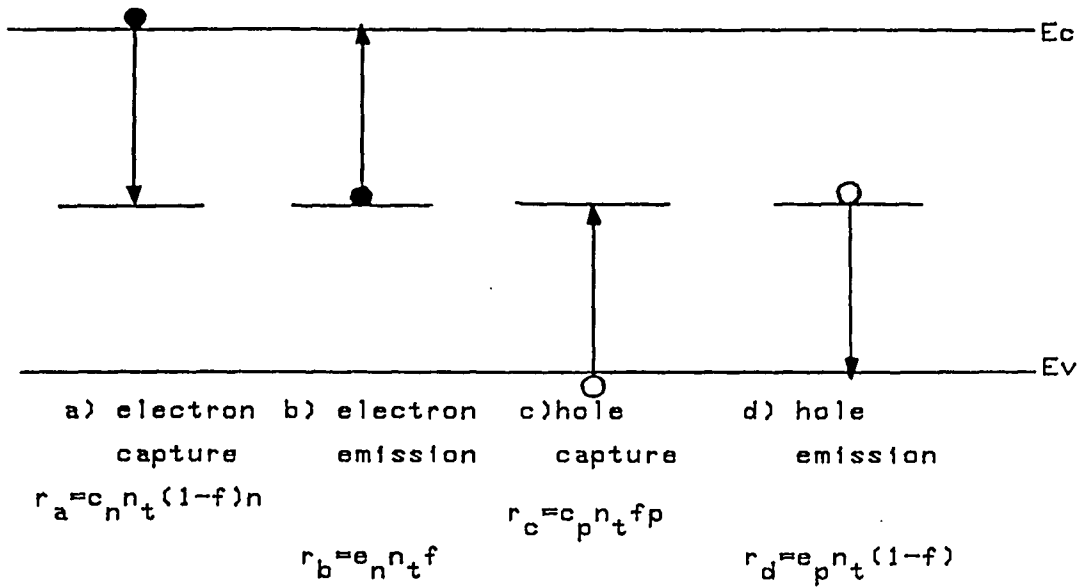


Figure 2.2 - Schematic of Trapping and Emission Processes

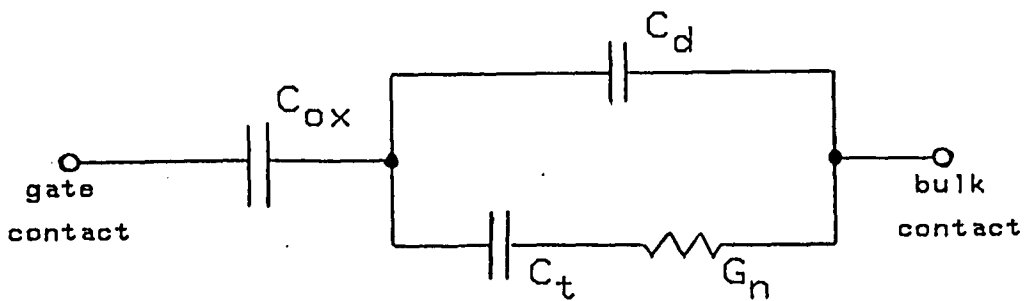


Figure 2.3 - Equivalent Circuit of MOS Device

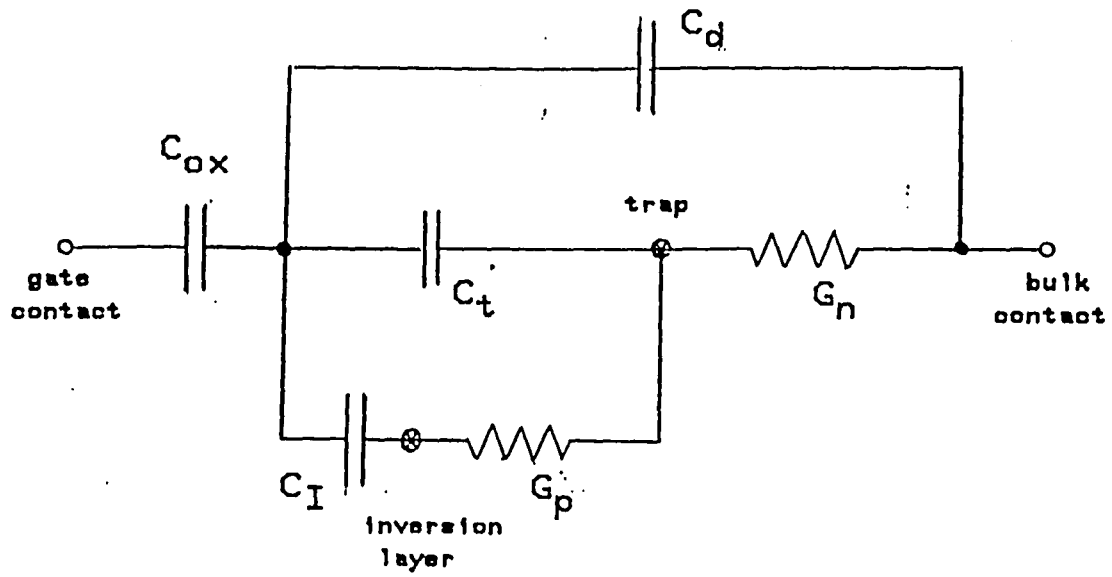


Figure 2.4 - Extended Equivalent Circuit to include Hole Effects

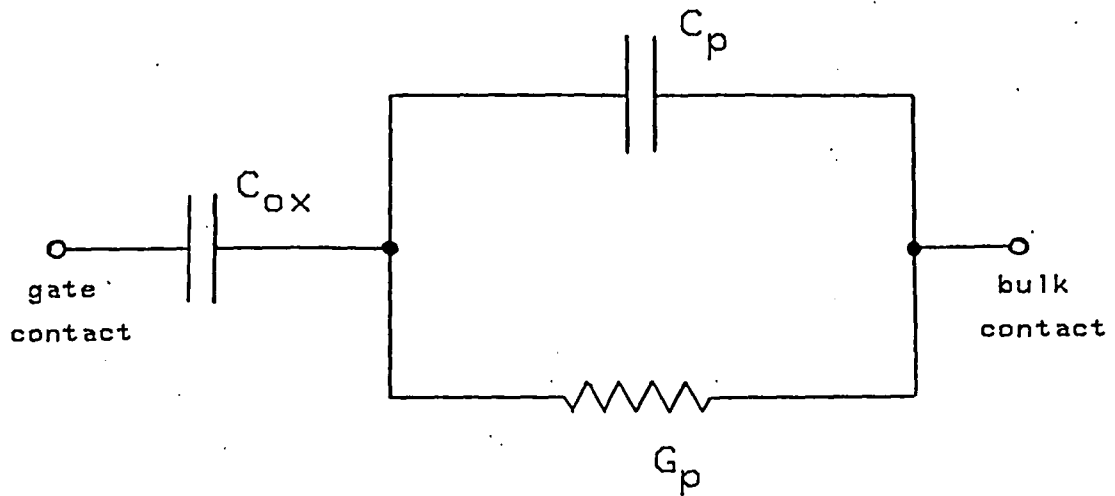


Figure 2.5 - Circuit which considers Silicon as equivalent parallel Conductance and Capacitance

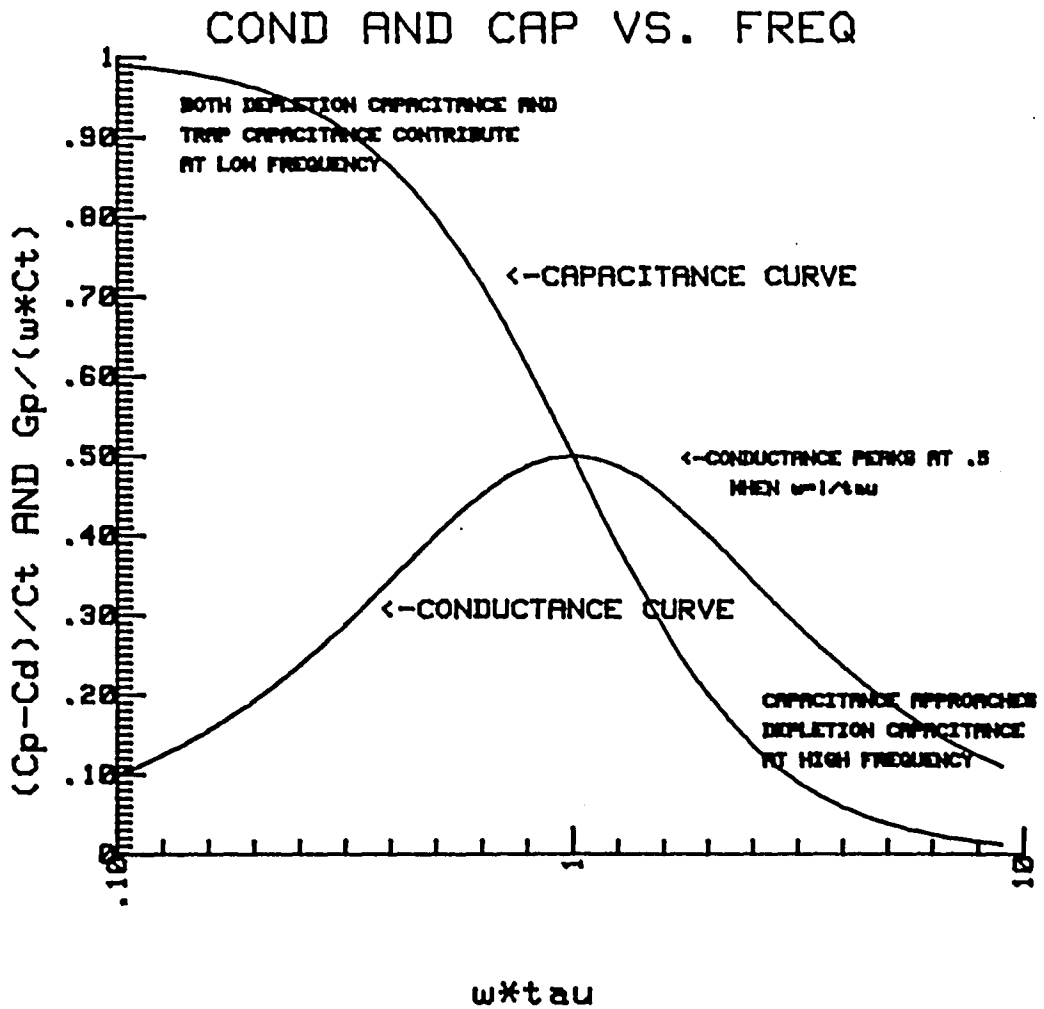


Figure 2.6 - Plots of dimensionless quantities  $(C_p - C_t) / C_t$  and  $G_p / \omega C_t$  versus frequency



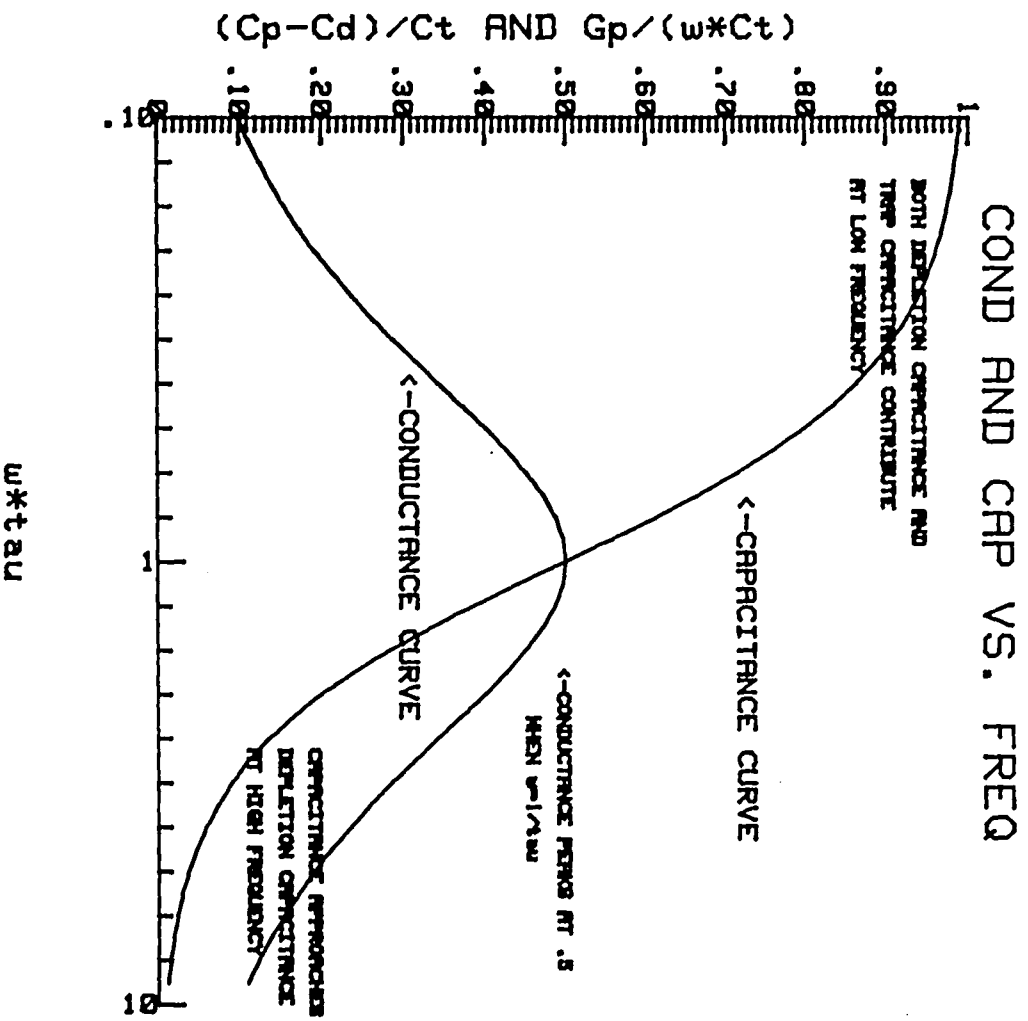


Figure 2.6 - Plots of dimensionless quantities  $(C_p - C_d) / C_t$  and  $G_p / w C_t$  versus frequency

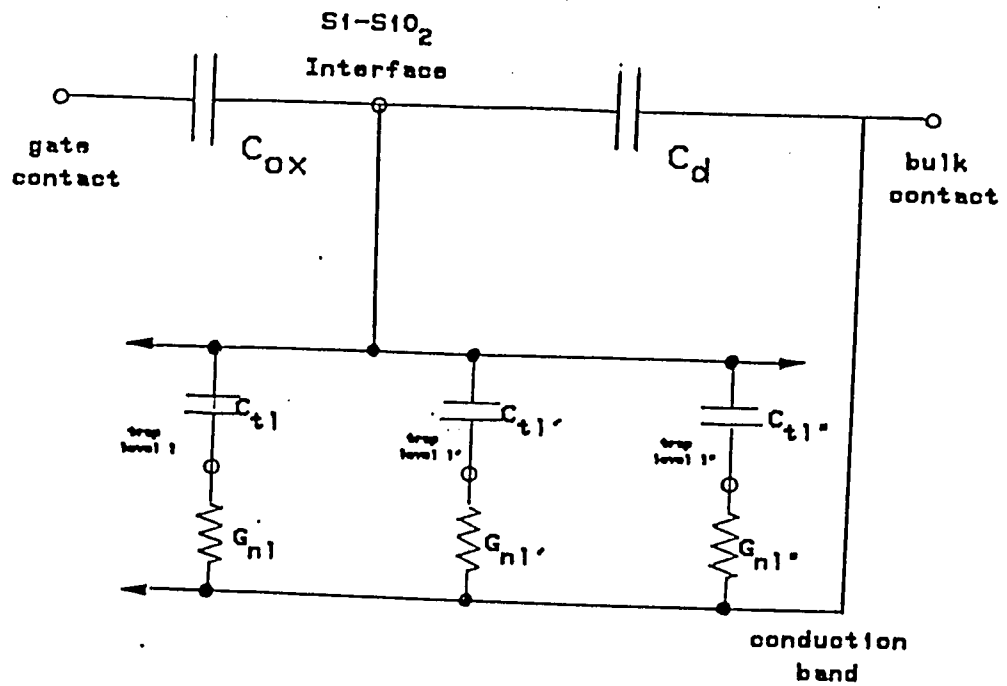


Figure 2.7 - Equivalent Circuit for a Continuum of Traps

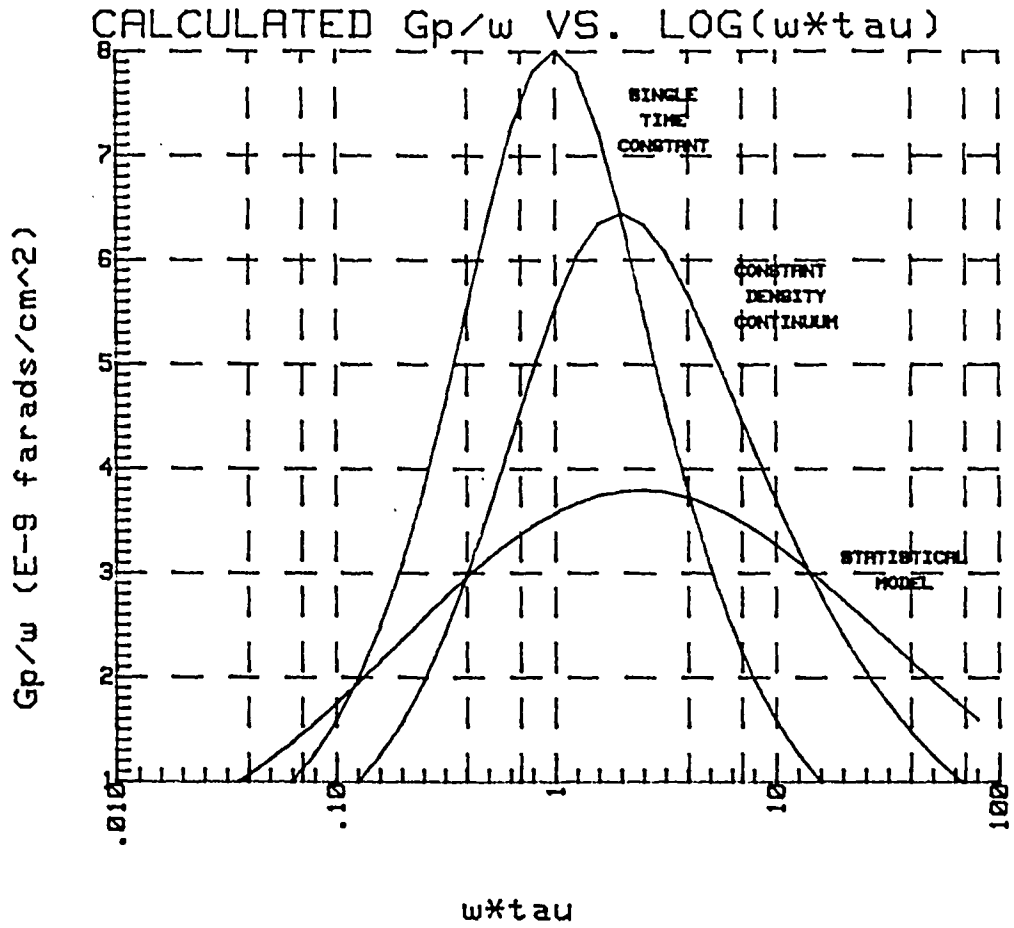


Figure 2.8 - Comparison of Conductance Curves produced by each Theory

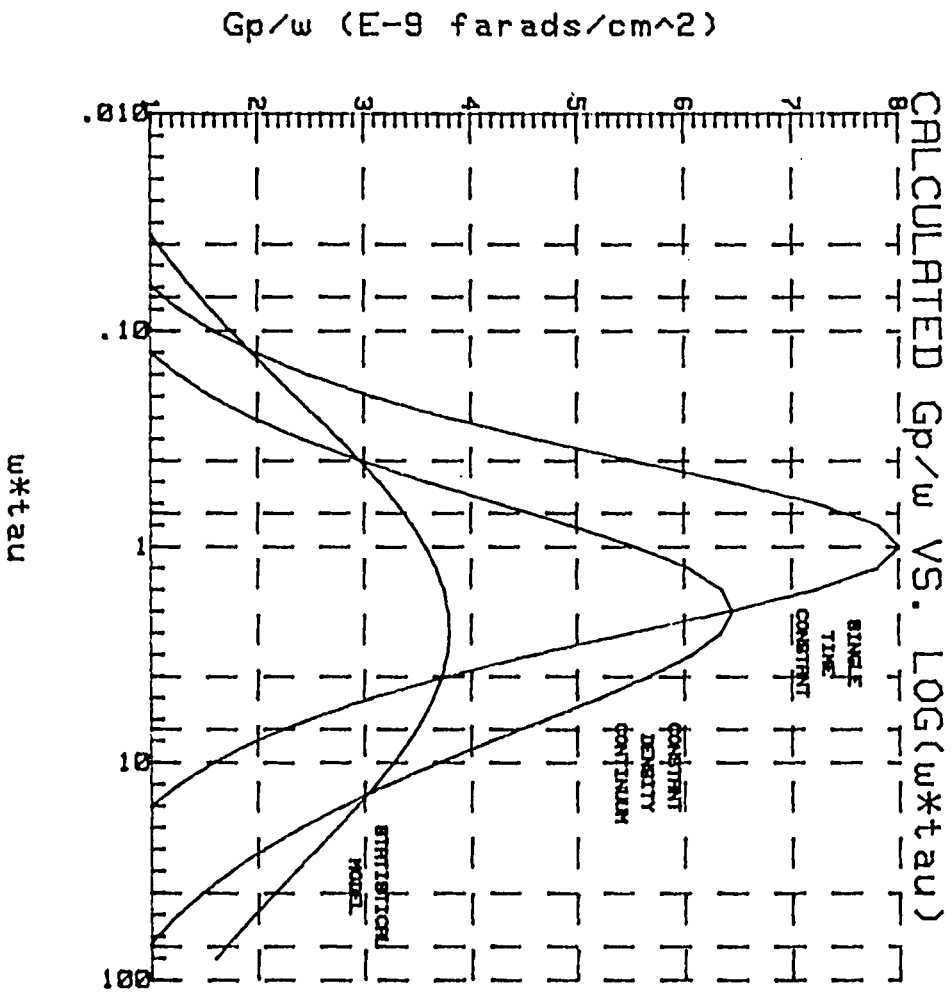


Figure 2.8 - Comparison of Conductance Curves produced by each Theory

## ADMITTANCE MEASUREMENTS PROCEDURE

The experimental setup used to perform the admittance measurements is shown in Figure 2.9. Figure 2.9a shows a schematic representation of the instrumentation and Figure 2.9b shows the electrical equivalent of the measurement circuit. As is shown, a signal frequency is mixed with a bias voltage and applied to the device. The signal, after passing through the device under test and a current preamplifier arrives at the input of the lock-in amplifier. At this point, it has suffered some phase shift which is characteristic of the measurement circuit and the D.U.T. The shifted signal is compared to the original signal by the lock-in and resulting in-phase and quadrature component levels are indicated. To perform measurements the experiment is first calibrated by placing some known capacitor in the D.U.T. position and adjusting the phase compensation on the lock-in such that there is no deflection in the in-phase component meter. Next, the actual device is put in place and measurements are performed. The measurements in this case are performed under the control of a software program which sets the bias and gathers the data at each point. The program documentation is given in Appendix F.

Note, the circuit being measured, as shown in Figure 2.10, is some capacitance and conductance in parallel. However, the circuit on which the theoretical calculations are based is the oxide capacitance in series with a silicon parallel capacitance and conductance (Figure 2.5). To extract the parallel capacitance and conductance from the measured data the impedance of the oxide capacitance must be subtracted from the expression for measured impedance and the real and imaginary parts of the resulting admittances must be equated. The resulting formulas are given by:

$$\frac{G_p}{\omega C_{ox}} = \frac{G_m / C_{ox}}{\{G_m / \omega C_{ox}\}^2 + \{1 - C_m / C_{ox}\}^2} \quad (2.8a)$$

$$\frac{C_p}{C_{ox}} = \frac{1 - C_m / C_{ox}}{\{G_m / C_{ox}\}^2 + \{1 - C_m / C_{ox}\}^2} - 1 \quad (2.8b)$$

The formulas are applied to the measured data before fits are attempted. The fitting program used is documented in Appendix G.

Measurements were performed on the identical device of part 1 of this thesis, the .75mm circular dot capacitor. Preliminary information was obtained about the device

with the Quasi-static C-V technique. The measured C-V curve is shown in figure 2.11. From this curve a plot of  $D_{it}$  versus energy within the bandgap was obtained which yielded the plot of Figure 2.12. This plot shows a  $D_{it}$  of slightly more than  $1 \times 10^{11} / \text{cm}^2 \text{eV}$ . These curves were also integrated to obtain a plot of surface potential versus gate bias as shown in Figure 2.13.

Admittance measurements were performed on this device at twelve discrete frequencies by sweeping the bias between -2.5V and 0V. The measured curve at 1kHz is shown in Figure 2.14. From the measured curves a bias in depletion was chosen and the data was "cross sectioned" to obtain conductance and capacitance versus frequency curves. The bias chosen was -1.05V which from Figure 2.13 corresponds to a surface potential of about -.21V. Since the bulk Fermi potential is about -.29V this is near the center of the depletion biases. The measured and fitted curves are shown in Figure 2.15.

The fits for the curves are especially good and agree well with the results of the Quasi-static C-V measurement. The Quasi-static C-V technique indicated a  $D_{it}$  of slightly over  $1 \times 10^{11} / \text{cm}^2 \text{eV}$ , whereas the conductance measurements were fit with a  $D_{it}$  of  $9 \times 10^{10} / \text{cm}^2 \text{eV}$ .

From the fitting parameter  $\tau_n$ , the trap response time, the electron capture cross section can be calculated from the equation:

$$\sigma_n = \frac{1}{v_t \tau_n N_d} \exp - \left( \frac{q\psi_s}{kT} \right) \quad (2.9)$$

where  $v_t$  is the electron thermal velocity (about  $10^7$  at room temperature). A surface potential of  $-.2V$  yields a capture cross section of about  $7 \times 10^{-16} \text{ cm}^2$ . Because of the exponential dependance of the cross section on surface potential this can at best be considered an order of magnitude calculation. The overall consistency of the data points to the validity of the technique.

A second experiment was performed to investigate the fitting parameter  $\sigma_g$ . The theory states that due to the discrete nature of the electron point charges, the surface potential exhibits a granularity which follows the point charge distribution. Thus, a variation in the interface charge distribution alters the character of the surface potential fluctuations. This postulate was first investigated by Castagne and Vapaille /11/, who drifted charged lithium ions through the oxide layer to a region near the interface. Their measurements showed a qualitative agreement with theory.

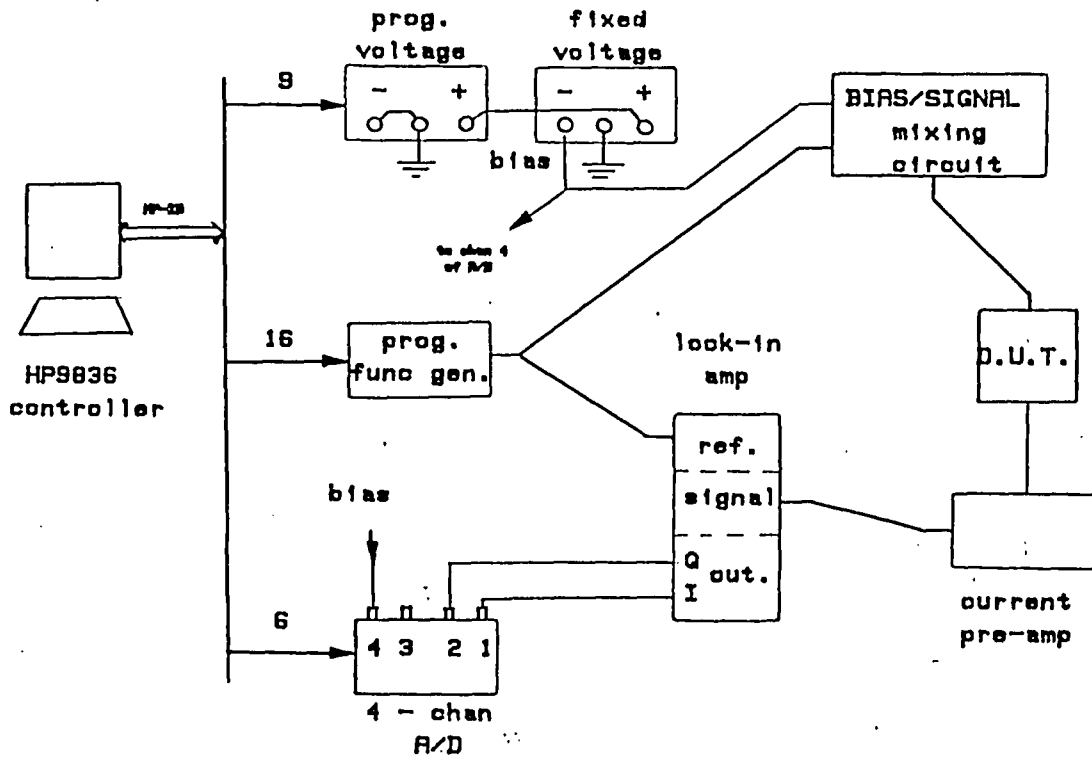


In this experiment, an MNOS capacitor was used as the MIS system. With this device the point charge distribution near the interface may be electrically altered by tunneling various amounts of charge into the nitride-oxide layer. To apply the admittance technique to the MNOS device requires special consideration to avoid the read-disturb effect caused by changes in the gate bias. The measurements are performed by allowing the device to settle into a "quasi-equilibrium" condition at a particular gate bias corresponding to some average surface potential. This potential is indicated by a peak in the conductance versus bias curve at a specified search frequency. At this potential, the admittance is measured with respect to frequency only. The experimental technique is to first characterize the admittance of a virgin (electrically unperturbed) MNOS device with respect to frequency. Next, the device is perturbed by the application of a large positive or negative gate voltage, thereby altering the charge near the interface. The admittance is again measured at the same average surface potential, indicated by the peak in the conductance curve at the search frequency. Finally, the measurements are fit to theory to obtain the parameter which represents the variance in surface potential,  $\sigma_s$ .

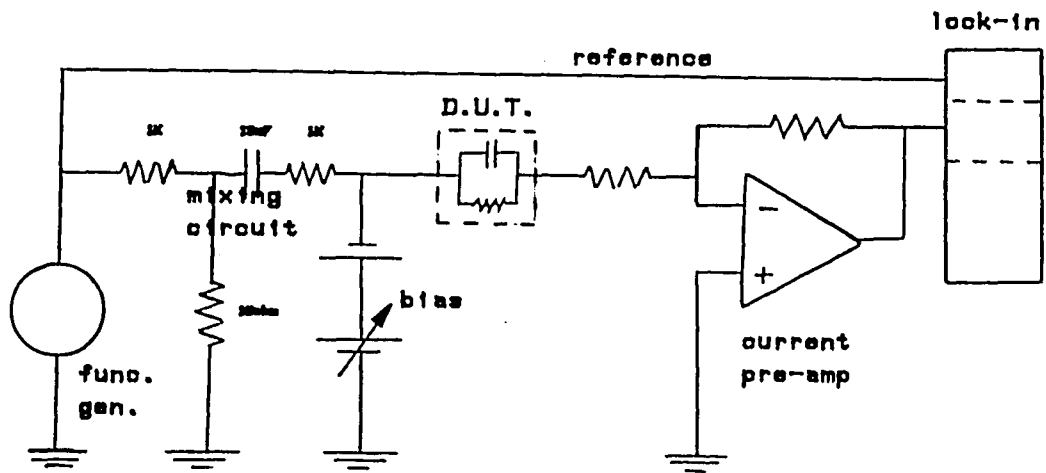
Reasonable fits with theory may be obtained with this technique and, as predicted by theory there is an increase in the surface potential fluctuation when the amount of charge near the interface is increased, independent of the sign of the charge. The data and fits are shown in Figure 2.16. Theory predicts /10/ that the square of the variance is proportional to the interface charge (i.e.  $\sigma_s^2 \sim Q_i$ ). If the flatband voltage is proportional to the interface charge, then the following relationship can be derived:

$$\sigma_s^2 = K|V_{fb}| \quad (2.10)$$

where K is a proportionality constant. Using  $V_{fb}$  of -2.5V and  $\sigma_s$  of 2.4 for a virgin device, K solves to 2.3. Using this value of K and equation (2.10) predicted values of  $\sigma_s$  can be obtained and compared with measured values. The results are shown in Table 2.1. These results further verify the validity of the admittance technique and show evidence of the physical reality of the postulated potential fluctuations.



(a)



(b)

Figure 2.9 - Admittance Measurement Experimental Setup  
 (a) Schematic ; (b) Electrical Equivalent

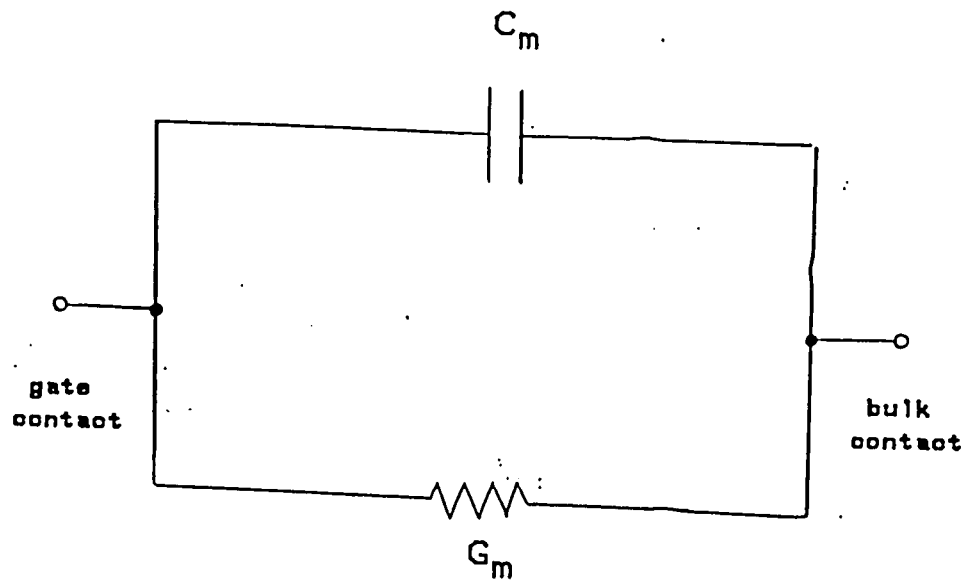


Figure 2.10 - Measured Circuit

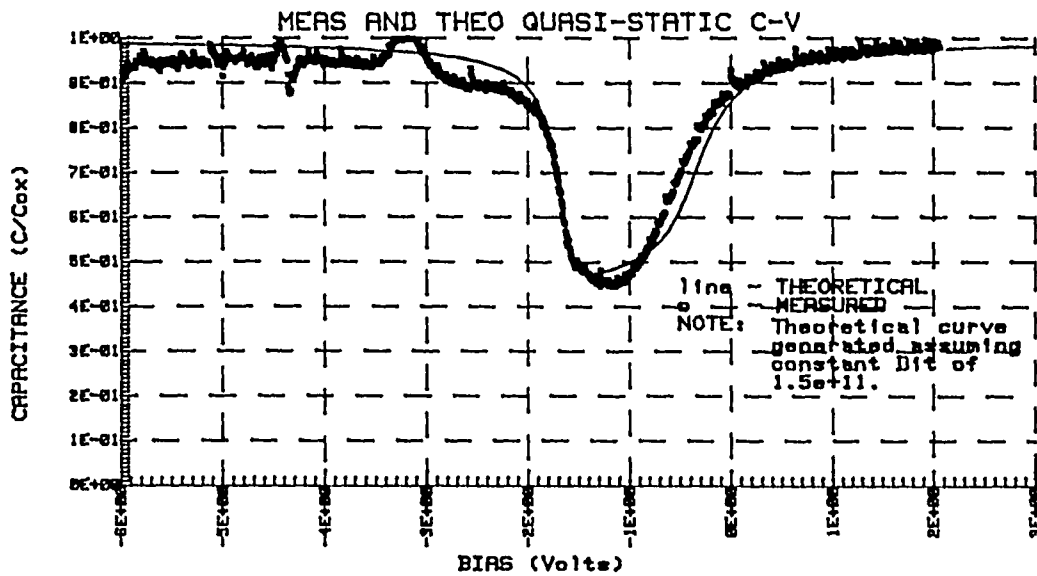


Figure 2.11 - Measured Quasi-static C-V Curve

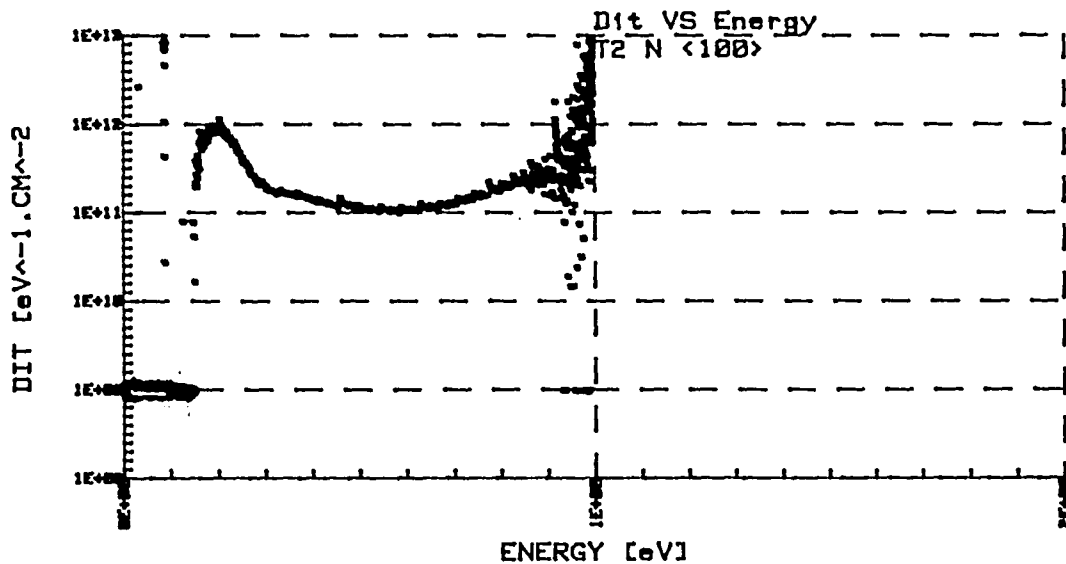


Figure 2.12 - Curve of  $D_{it}$  vs. Energy extract from QSCV

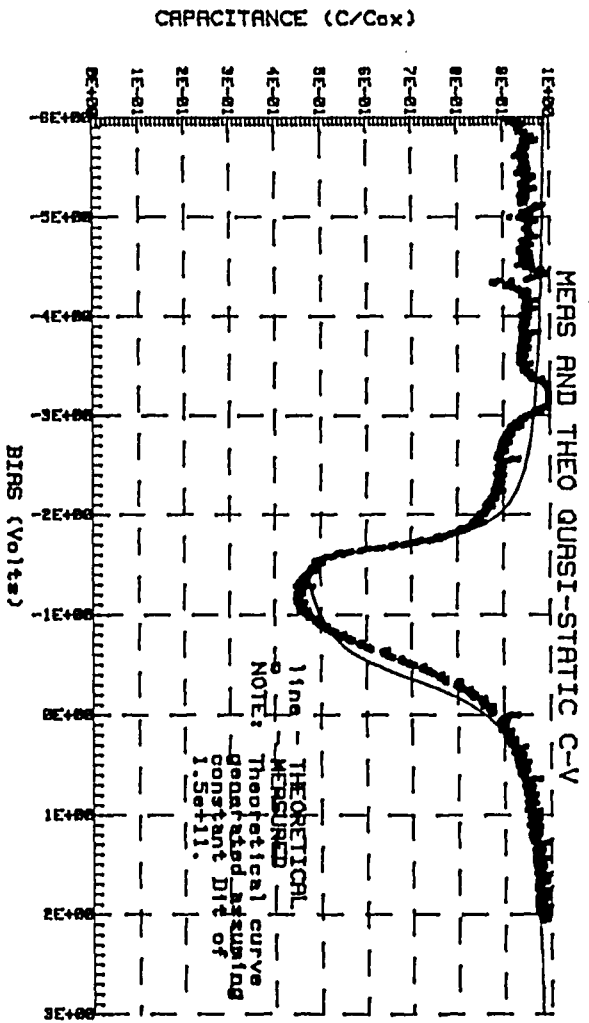


Figure 2.11 - Measured Quasi-static C-V Curve

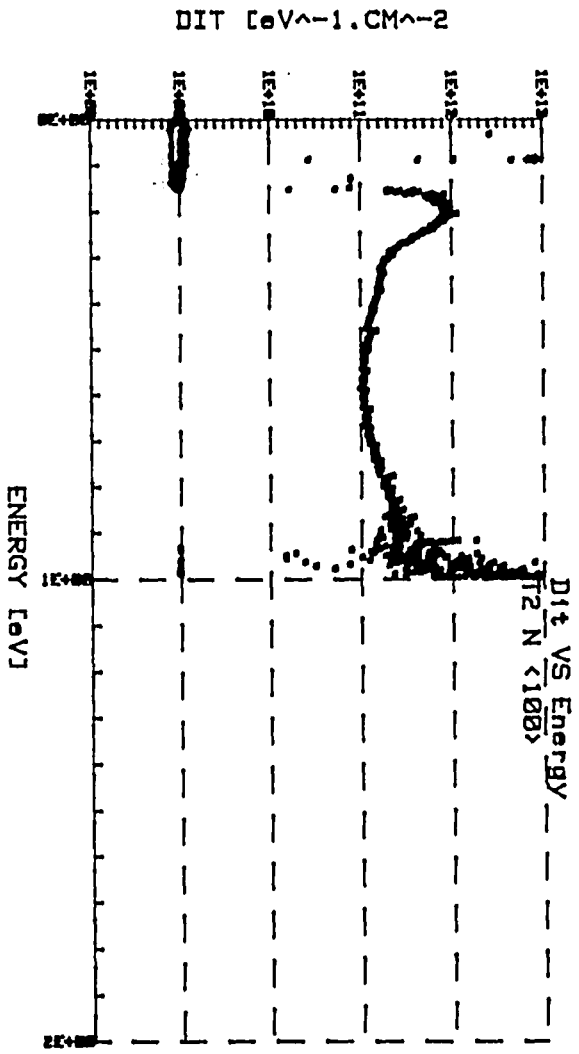


Figure 2.12 - Curve of  $D_{it}$  vs. Energy extract from QSCV

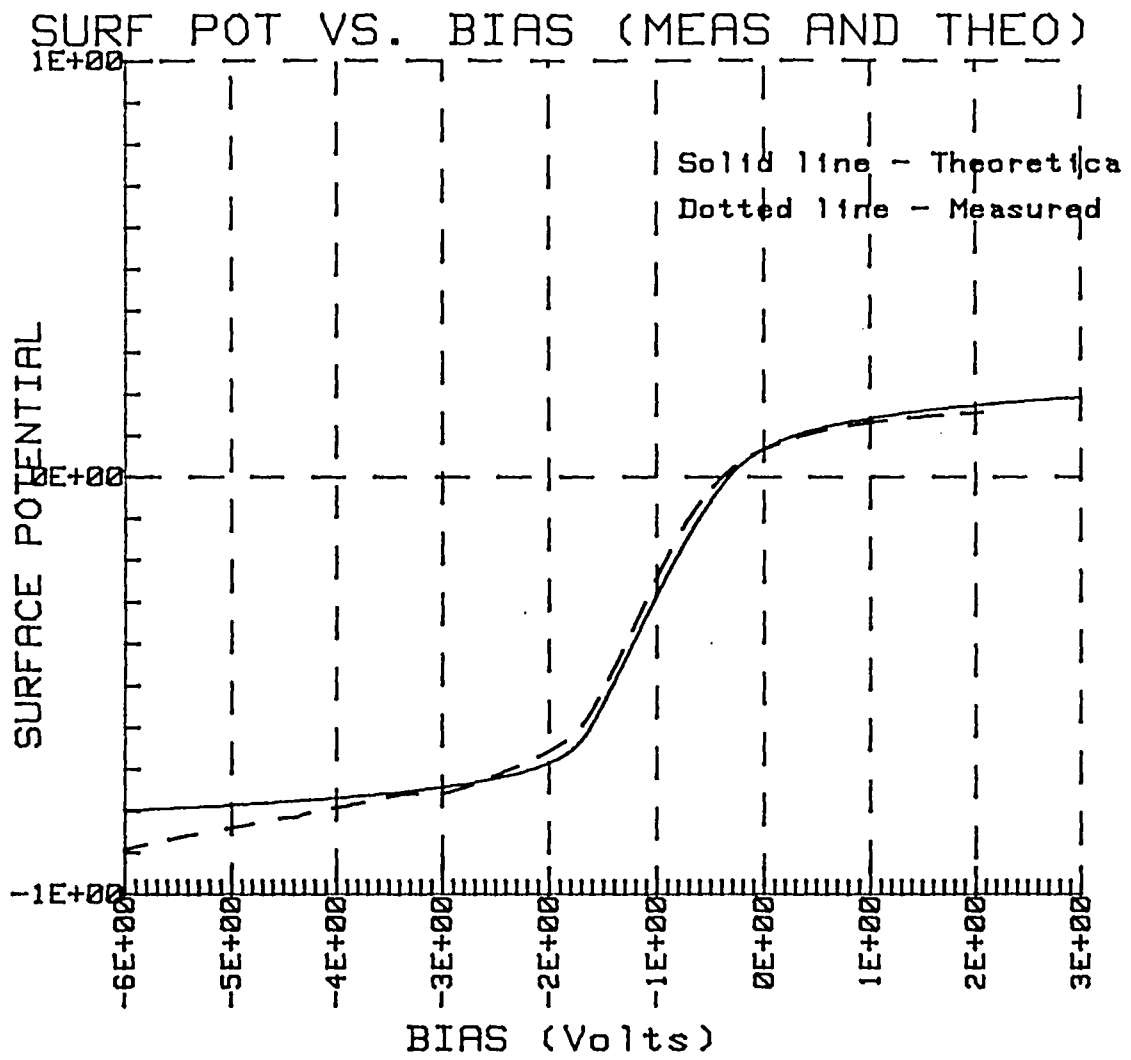


Figure 2.13 - Curve of Surface Potential vs. Gate Bias  
Extracted from QSCV

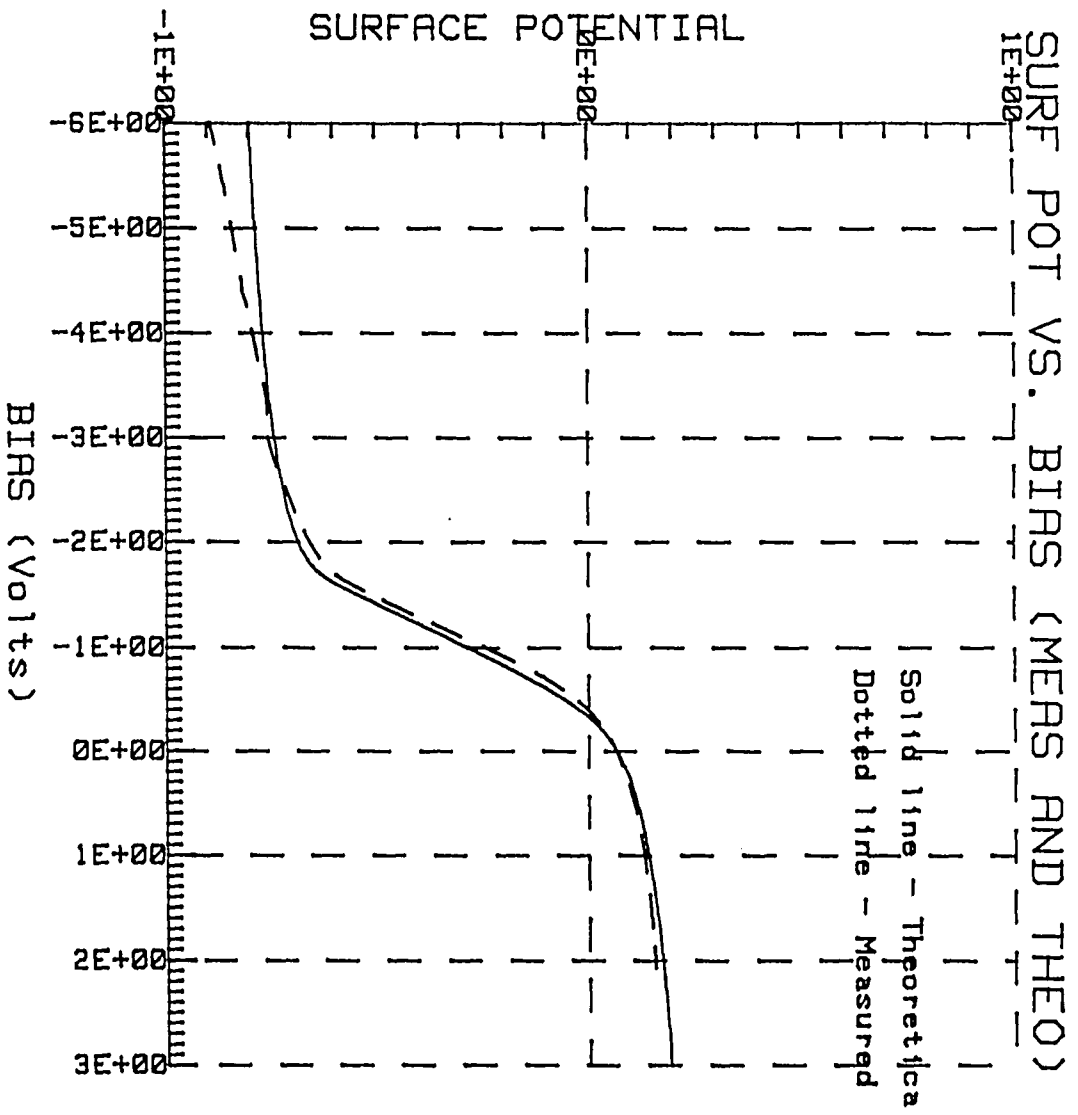


Figure 2.13 - Curve of Surface Potential vs. Gate Bias  
 Extracted from QSCV



# COND. AND CAP. VS VOLTAGE.

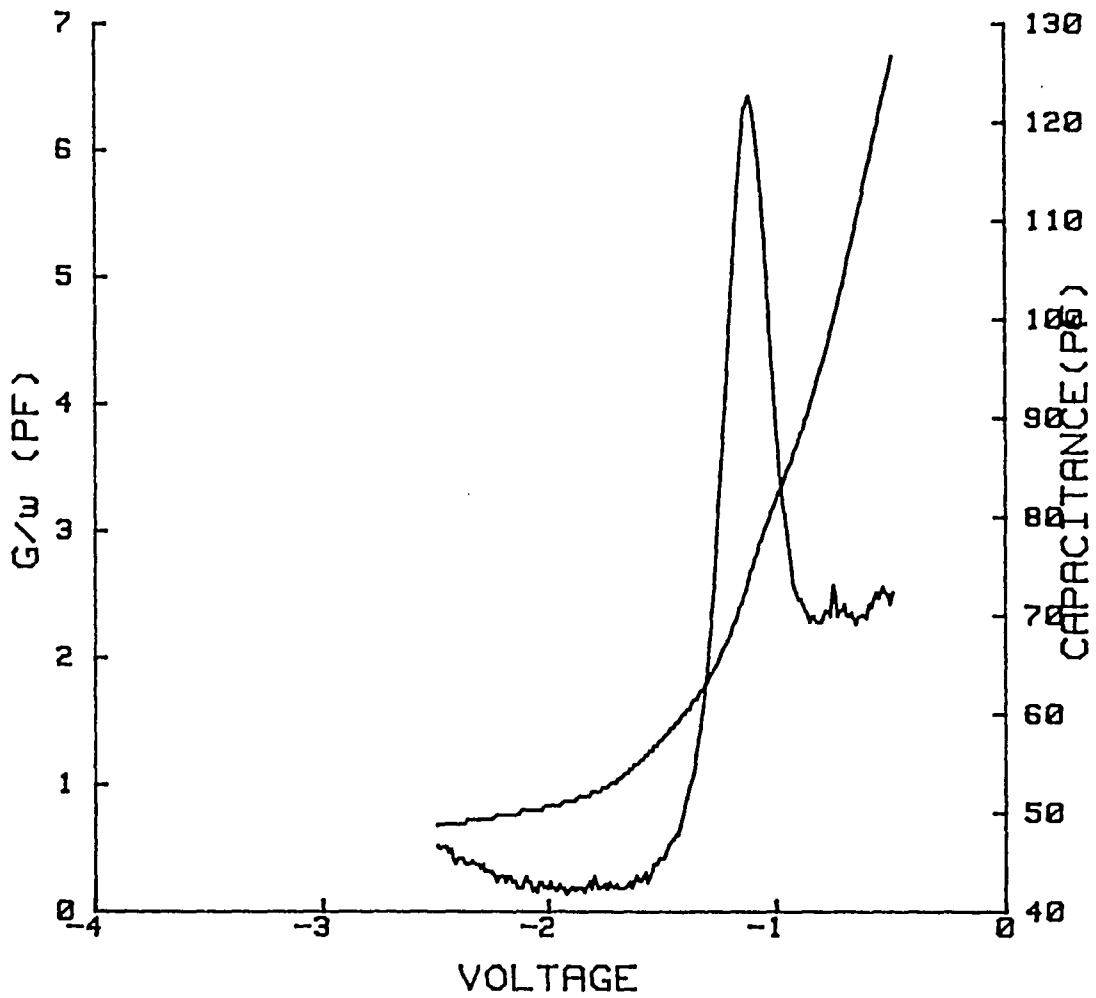


Figure 2.14 - Admittance Curve Measured at 1KHz

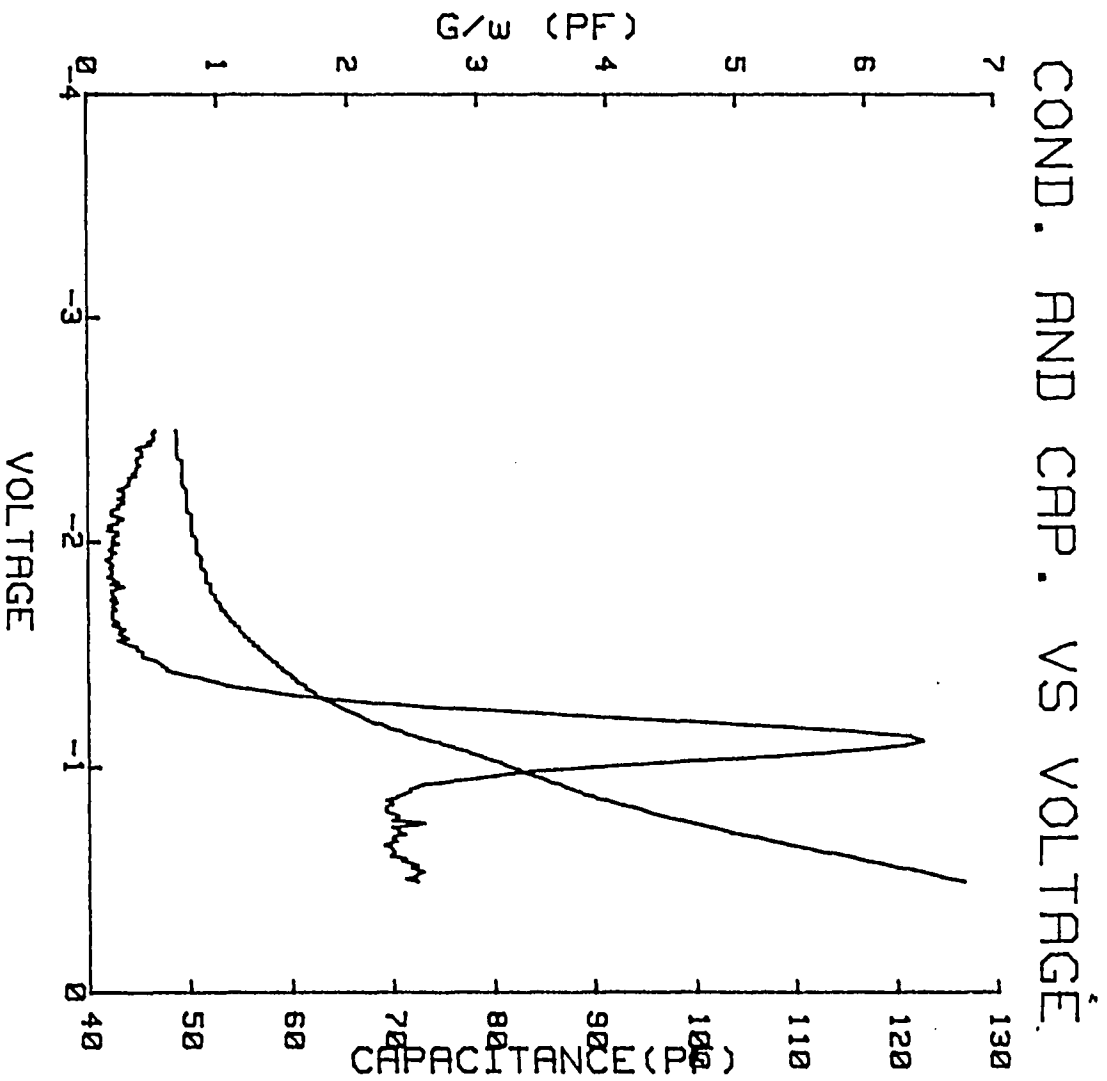


Figure 2.14 - Admittance Curve Measured at 1KHz

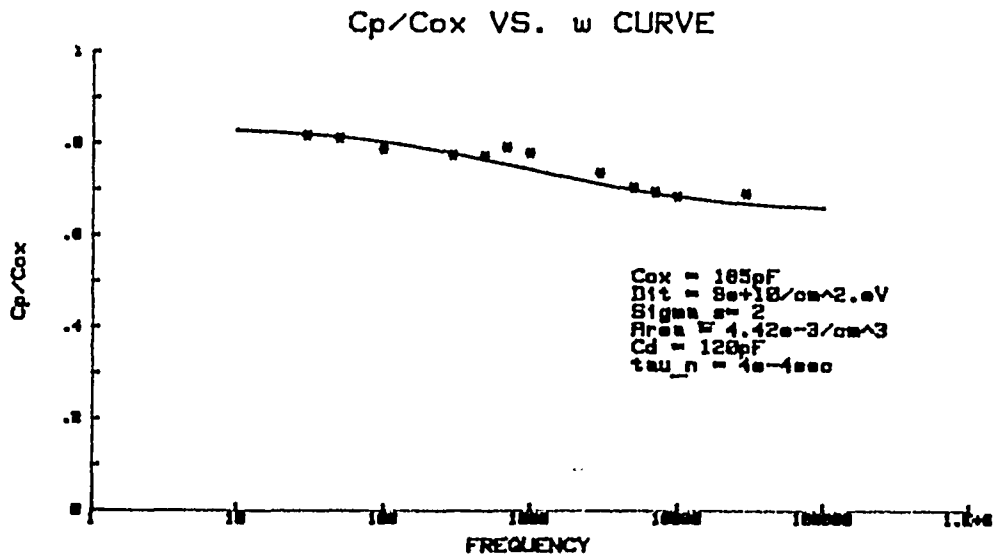
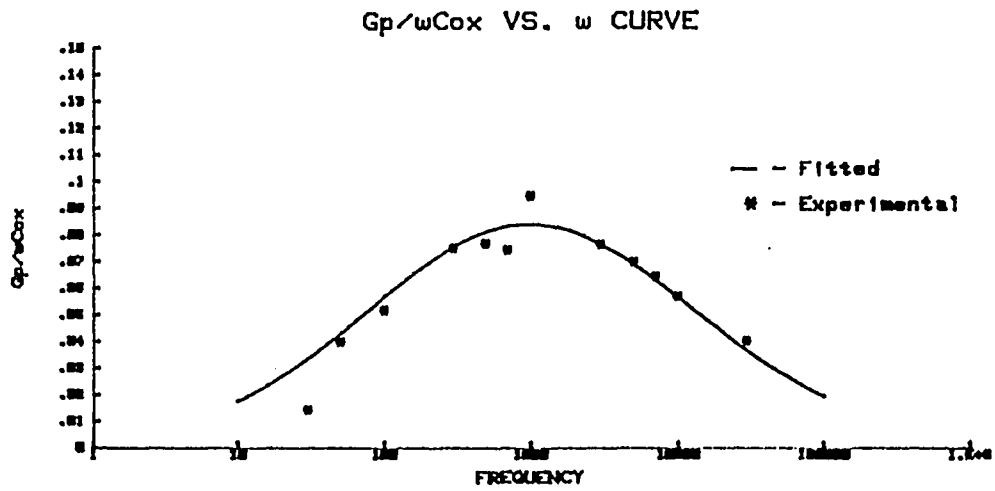


Figure 2.15 - Measured and Fitted Admittance vs. Frequency Curves

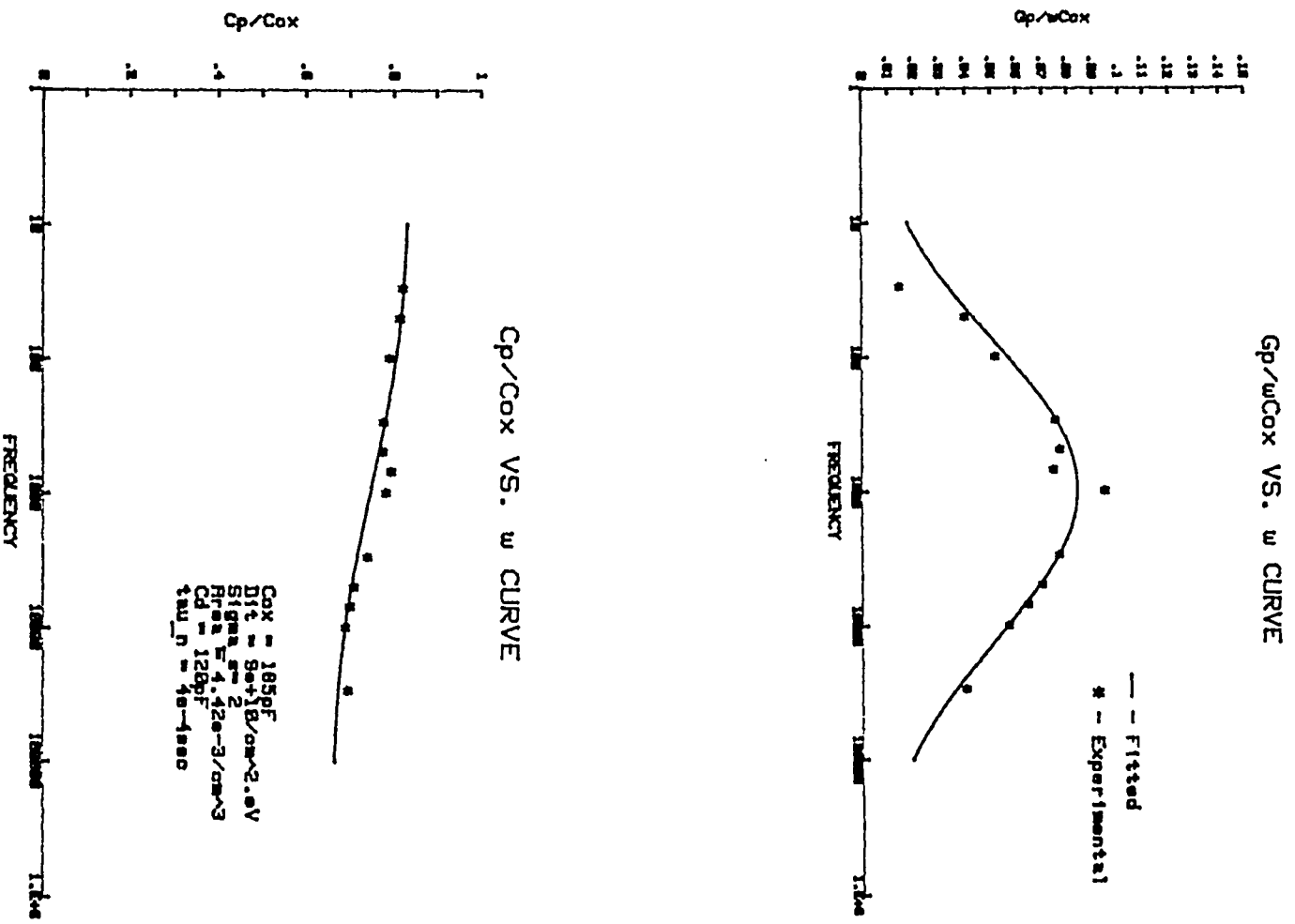


Figure 2.1.15 - Measured and Fitted Admittance vs. Frequency Curves

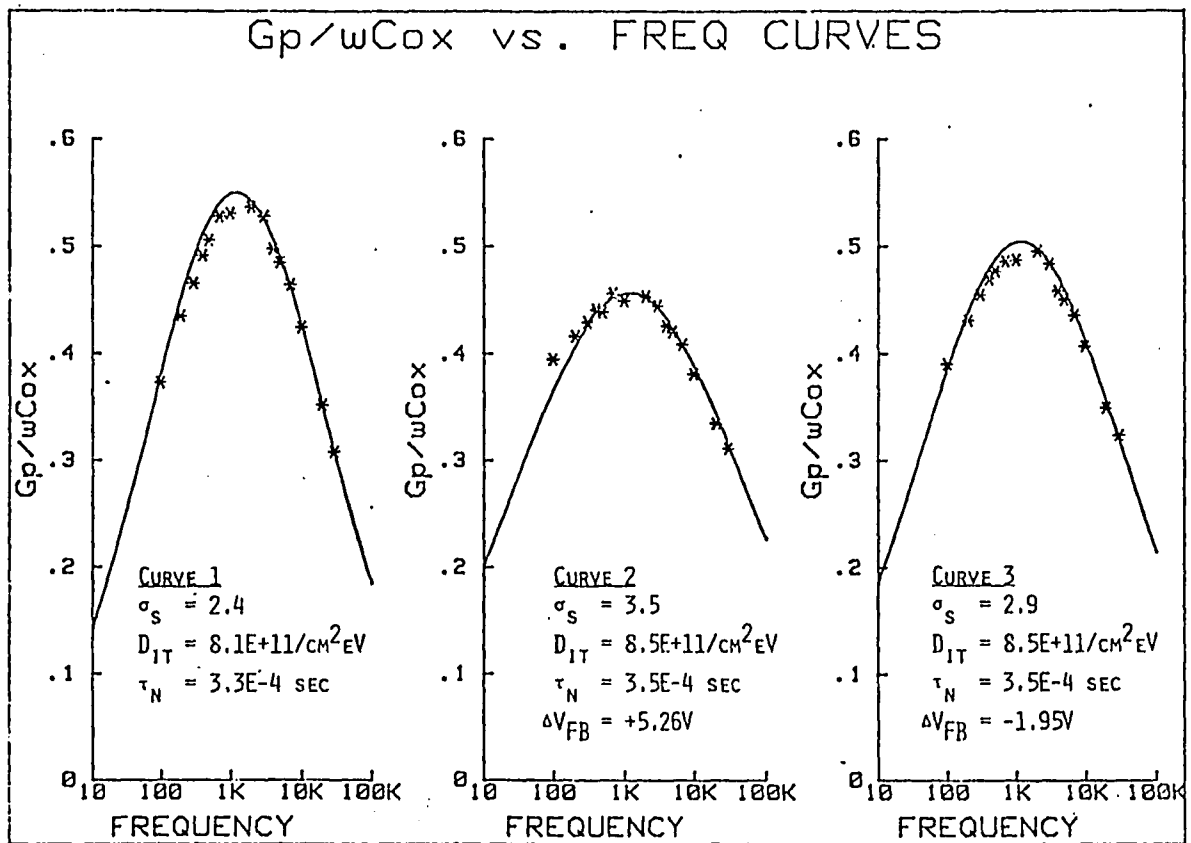


Figure 2.16 Results of measurements on MNOS devices.

Table 2.1 - Comparison of Predicted and Measured Values  
of  $\sigma_s$ .

Device History	$V_{fb}$	Predicted $\sigma_s$	Measured $\sigma_s$
Virgin	-2.5V	-	2.4
Virgin written w/ +21.2V	+2.75V	2.5	2.9
Virgin written w/ -21.2V	-4.5V	3.2	3.5

## DISCUSSION OF ADMITTANCE MEASUREMENT AUTOMATION

The admittance software package is an excellent example of the advantageous use of an automated control system in an experimental laboratory. This program again used the modular design technique as discussed in the C-t program but to an even greater extent. The tasks programmed here were often simpler and more limited, therefore allowing even greater program flexibility. This is especially true in the analysis program where the steps of the analysis were left to the user instead of procedurally automated. The result is a compromise between automatic and manual control. The advantage gained is that the user of this program will obtain some understanding of the analysis technique because he is guiding the analysis through the use of the software keys and numeric inputs. This is a much better scheme than the kind of black box approach where data goes into analysis and the answer comes out the other end. This is especially true in a research environment where understanding of where the answers come from rather than the answers themselves is often the important factor.

The experimental results presented here were taken in approximately two days time. This amount of data

if taken by conventional techniques, would probably have taken at least a week. Considering the amount of information extracted from these measurements this is an extreme experimental advantage.



## CONCLUSIONS

From the experiments presented here the advantages to the user of the computer in the experimental laboratory can be seen. The computer saves work and frees the researcher from time consuming data gathering tasks. These advantages are best exploited through the use of a modular programming scheme where simple, well-defined tasks are programmed for use in any appropriate procedural manner. With this type of programming scheme the use of the computer will not hide the complexities of analytical techniques by producing answers out of a "black box" type of environment. It is suggested that all future software be developed in such a manner and the automation of long, complex analytical techniques be avoided. The automation of the Zerbst technique may be an example of the automation of too complex a task. The user who sits down and uses this program will probably not get a good feel for the device physics involved, instead he will get numbers for generation lifetime and surface recombination velocity which may or may not be relevant.

Some more functional conclusions that can be drawn from the automation performed are one; the time monitoring

of experimental parameters can be best accomplished by dedicated processors and two, taking the derivative of computer gathered data may be best performed numerically instead of analytically. Further discussion of these points are included in the C-t experiment.

From the experience gained in using the Zerbst technique it can be concluded that its use is valid. The results obtained are good and with use of initial condition which inforce the analytical assumptions (i.e. starting in inversion) consistent results are obtained.

From the use of the Admittance technique it can be concluded that it is an excellent candidate for automation. The data measured fits well to theoretical calculations. Investigations into the fitting parameter  $\sigma_s$  also show evidence of its physical reality.

## APPENDIX A

### Derivation of the Zerbst Analysis Technique

Consider the MOS Capacitor in which the total charge on the device is equal to zero. Mathematically stated:

$$Q_g + Q_i + Q_d = 0 \quad (\text{A.1})$$

$Q_g$  = Charge on Gate

$Q_i$  = Charge in Inversion Layer

$Q_d$  = Charge in Depletion Layer

The current in the circuit external to the device is:

$$I_g = \frac{dQ_g}{dt} = - \left( \frac{dQ_i}{dt} + \frac{dQ_d}{dt} \right) \quad (\text{A.2})$$

Now inversion charge is supplied by generation current in the depletion region (non-equilibrium) and also by generation in the surface states. Therefore:

$$\frac{dQ_i}{dt} = \frac{qn_i}{2\tau_g}(W - W_f) + qn_i S \quad (\text{A.3})$$

where  $\tau_g$  = generation lifetime

$S$  = surface recombination velocity

$W_f$  = final or equilibrium  
depletion layer width

Also:

$$\frac{dQ_d}{dt} = qN_d \left( \frac{dW}{dt} \right) \quad (\text{A.4})$$

Substituting equations (A.3) & (A.4) into equation (A.1):

$$I_g = -q \frac{n_i}{2\tau_g}(W-W_f) + n_i S + N_d \left( \frac{dW}{dt} \right) \quad (\text{A.5})$$

Now consider the expression for gate voltage:

$$V_g = \frac{Q_g}{C_{ox}} + \psi_s = \frac{Q_g}{C_{ox}} - \frac{qN_d W^2}{2\epsilon_s} \quad (\text{A.6})$$

With non-varying gate voltage then:

$$\frac{dV_g}{dt} = 0 = \frac{I_g}{C_{ox}} - \frac{qN_d W}{\epsilon_s} \left( \frac{dW}{dt} \right) \quad (\text{A.7})$$

Substituting expression for  $I_g$  from (A.5) into equation (A.7):

$$0 = \frac{1}{C_{ox}} \frac{n_i}{2\tau_g}(W-W_f) + n_i S - \frac{N_d}{C_{ox}} \frac{dW}{dt} - \frac{N_d W}{\epsilon_s} \left( \frac{dW}{dt} \right) \quad (\text{A.8})$$

Solving equation (A.8) for  $\frac{dW}{dt}$ :

$$\frac{dW}{dt} = - \frac{\frac{n_i}{2\tau_g}(W-W_f) + n_i S}{C_{ox} \left( \frac{N_d}{C_{ox}} + \frac{N_d W}{\epsilon_s} \right)} \quad (\text{A.9})$$

Noting that for capacitances for the silicon and oxide in series  $1/C = 1/C_{ox} + 1/C_s$ , we can anticipate our result and write an expression for the time derivative

of  $(C_{\text{ox}}/C)^2$ :

$$\frac{C_{\text{ox}}}{C}^2 = \left( 1 + \frac{C_{\text{ox}}W}{\epsilon_s} \right)^2 \quad (\text{A.10})$$

$$\frac{d}{dt} \left( \frac{C_{\text{ox}}}{C} \right)^2 = 2 \left( 1 + \frac{C_{\text{ox}}W}{\epsilon_s} \right) \left( \frac{C_{\text{ox}}}{\epsilon_s} \right) \left( \frac{dW}{dt} \right) \quad (\text{A.11})$$

Substituting equation (A.9) into (A.11):

$$\frac{d}{dt} \left( \frac{C_{\text{ox}}}{C} \right)^2 = -2 \left( 1 + \frac{C_{\text{ox}}W}{\epsilon_s} \right) \frac{\frac{n_i}{2\epsilon_s \tau_g} (W - W_f) + \frac{n_i S}{\epsilon_s}}{\frac{N_d}{C_{\text{ox}}} + \frac{N_d W}{\epsilon_s}} \quad (\text{A.12})$$

Now note that:

$$\frac{W}{\epsilon_s} = \frac{1}{C_s} = \frac{1}{C} - \frac{1}{C_{\text{ox}}} = \frac{C_{\text{ox}} - C}{C_{\text{ox}} C} \quad \text{and} \quad \frac{W_f}{\epsilon_s} = \frac{C_{\text{ox}} - C_f}{C_{\text{ox}} C_f} \quad (\text{A.13})$$

Therefore by substituting equation (A.13) into (A.12) and reducing:

$$-\frac{d}{dt} \left( \frac{C_{\text{ox}}}{C} \right)^2 = \frac{2C_{\text{ox}}}{N_d C_f} \left( \frac{n_i}{2\tau_g} \left( \frac{C_f}{C} - 1 \right) + \frac{n_i C_f S}{\epsilon_s} \right) \quad (\text{A.14})$$

This is the final result of the Zerbst derivation.

## APPENDIX B

### Admittance Between Conduction Band and Interface Trap

In conjunction with figure 2.2 consider the current between the conduction band and a trap:

$$i_n(t) = qn_t c_n \{1-f(t)\}n(t) - qn_t e_n f(t) \quad (B.1)$$

Separate the fermi function and surface population function into AC and DC components

$$f(t) = f_o + \delta f(t) \quad n(t) = n_o + \delta n(t) \quad (B.2)$$

The equation for current becomes:

$$i_n = qn_t c_n \{(1-f_o)n_o + (1-f_o)\delta n - n_o \delta f\} - qe_n n_t (f_o + \delta f) \quad (B.3)$$

Note the condition that the conduction band is in thermal equilibrium with the traps.

$$\begin{aligned} \text{i.e.} \quad r_{ao} &= r_{bo} \\ qn_t c_n (1-f_o)n_o &= e_n n_t f_o \end{aligned} \quad (B.4)$$

Therefore

$$i_n = qn_t c_n \left( (1-f_o)\delta n - n_o \frac{\delta f}{f_o} \right) \quad (B.5)$$

Also by definition

$$i_n = qn_t \frac{\delta f}{\delta t} \quad (B.6)$$

Equating (B.5) and (B.6):

$$\frac{\delta f}{\delta t} = c_n(1-f_o)\delta n - c_n n_o \frac{\delta f}{f_o} \quad (\text{B.7})$$

Consider small signal fluctuations of the Fermi function of the form  $\delta f = f_m \exp(j\omega t)$ . Therefore:

$$\frac{\delta f}{\delta t} = j\omega \delta f$$

$$j\omega \delta f = c_n(1-f_o)\delta n - c_n n_o \frac{\delta f}{f_o}$$

$$\delta f = \frac{f_o(1-f_o)\delta n}{\{1 + j\omega f_o/(c_n n_o)\}n_o} \quad (\text{B.8})$$

Substituting equation (B.8) into (B.5):

$$i_n = \frac{j\omega q n_t f_o(1-f_o)\delta n}{1 + j\omega f_o/(c_n n_o)\delta n_o} \quad (\text{B.9})$$

Note that  $n = \exp(u)$  where  $u$  : surface band bending, so that  $\delta n = \exp(u) \delta u$ . Therefore:

$$\frac{\delta n}{n} = \delta u = \frac{q}{kT} \delta \psi \quad (\text{B.10})$$

Then by substituting equation (B.10) into (B.9):

$$i_n = \frac{j\omega q^2 n_t f_o (1-f_o) \delta\psi}{kT [1 + j\omega f_o / (c_n n_o)]} \quad (\text{B.11})$$

Since  $i_n = Y_n \delta\psi$  the small signal admittance can be defined as:

$$Y_n = j\omega \frac{q^2 n_t f_o (1-f_o)}{kT \{1 + j\omega f_o / (c_n n_o)\}} \quad (\text{B.12})$$



## APPENDIX C

### Admittance of Continuum of States

Integrating the expression given by equation (2.1) over a continuum of states:

$$Y'_s = j\omega \frac{q^2}{kT} \int_{-\infty}^{\infty} \frac{D_{it} f_o (1-f_o)}{1 + j\omega f_o / (c_n n_{so})} d\psi_s \quad (C.1)$$

where now  $D_{it}$  is the interface state density per unit area per eV across the bandgap.

With the state occupation function given by the fermi function of equation (2.2) it can be shown that:

$$f_o (1-f_o) = \frac{kT}{q} \left( \frac{df_o}{d\psi_s} \right) \quad (C.2)$$

Substituting (C.2) into (C.1) and changing the limits of integration.

$$Y'_s = j\omega q \int_0^1 \frac{D_{it}}{1 + j\omega \tau_n f_o} df_o \quad \text{where } \tau_n = \frac{1}{c_n n_{so}} \quad (C.3)$$

Since the magnitude of the function being integrated peaks over a fairly small range and  $D_{it}$  is a slowly changing function the integral of equation (C.3) can be rearranged as:

$$Y'_s = j\omega D_{it} q \int_0^1 \frac{df_o}{1 + \omega^2 \tau_n^2 f_o^2} + j\omega D_{it} q \int_0^1 \frac{j\omega \tau_n f_o df_o}{1 + \omega^2 \tau_n^2 f_o^2} \quad (C.4)$$

Evaluating the integrals.

$$\int_0^1 \frac{df_o}{1 + \omega^2 \tau_n^2 f_o^2} = \frac{1}{\omega \tau_n} \tan^{-1}(\omega \tau_n) \quad (\text{C.5a})$$

$$\int_0^1 \frac{f_o df_o}{1 + \omega^2 \tau_n^2 f_o^2} = \frac{1}{2\omega^2 \tau_n^2} \ln(1 + \omega^2 \tau_n^2) \quad (\text{C.5b})$$

Substituting (C.5) back into (C.4)

$$Y'_s = \frac{jqD_{it}}{\tau_n} \tan^{-1}(\omega \tau_n) + \frac{qD_{it}}{2\tau_n} \ln(1 + \omega^2 \tau_n^2) \quad (\text{C.6})$$

From equation (C.6) the Conductance and Capacitance can be defined as:

$$\frac{G_p}{\omega} = \frac{qD_{it}}{2\omega \tau_n} \ln(1 + \omega^2 \tau_n^2) \quad (\text{C.7a})$$

$$C_p = \frac{qD_{it}}{\omega \tau_n} \tan^{-1}(\omega \tau_n) \quad (\text{C.7b})$$

## APPENDIX D

### Statistical Admittance Model

Assuming a Gaussian approximation for a Poission distributed surface potential and integrating the expressions for admittance as given by equation 2.6 for n-type silicon:

$$\frac{\langle G_p \rangle}{\omega} = \frac{q}{2} \int_{-\infty}^{\infty} \frac{c_n n_{so} D_{it}}{\omega} \ln\left(1 + \frac{\omega^2}{2 c_n n_{so}}\right) P(\psi_s) d\psi_s \quad (D.1a)$$

$$\langle C_p \rangle = C_d + q \int_{-\infty}^{\infty} \frac{c_n n_{so} D_{it}}{\omega} \tan^{-1}\left(\frac{\omega}{c_n n_{so}}\right) P(\psi_s) d\psi_s \quad (D.1b)$$

$$\text{where } P(\psi_s) = (2\pi\sigma_s)^{-\frac{1}{2}} \exp\left[-\frac{(\psi_s - \langle\psi_s\rangle)^2}{2\sigma_s^2}\right]$$

Realizing the  $n_{so}$  can be written as  $N_d \exp(-\psi_s)$  and assuming  $D_{it}$  and  $c_n$  to be approximately constant we can rewrite the conductance expression as:

$$\frac{G_p}{\omega} = \frac{q D_{it}}{2\omega} c_n N_d \exp(-\langle\psi_s\rangle) (2\pi\sigma_s)^{-\frac{1}{2}} \int_{-\infty}^{\infty} \exp\left[-\frac{(\psi_s - \langle\psi_s\rangle)^2}{2\sigma_s^2}\right] * \exp(\langle\psi_s\rangle - \psi_s) \ln\left[1 + \frac{\omega^2}{c_n^2 N_d^2 \exp(-2\langle\psi_s\rangle)}\right] \quad (D.2)$$

$$* \exp(2\psi_s - 2\langle\psi_s\rangle) d\psi_s$$

$$\text{letting } \eta = \psi_s - \langle\psi_s\rangle \text{ and } n = \frac{1}{c_n N_d \exp(-\langle\psi_s\rangle)}$$

$$\frac{G_p}{\omega} = \frac{qD_{it}}{2\omega\tau_n(2\pi\sigma_s)^{\frac{1}{2}}} \int_0^{\infty} \exp\left(-\frac{\eta^2}{2\sigma_s^2}\right) \exp(-\eta) \ln(1+\omega^2\tau_n^2\exp 2\eta) d\eta$$

Similar substitution in the capacitance expression leads to the result of equation 2.7b.

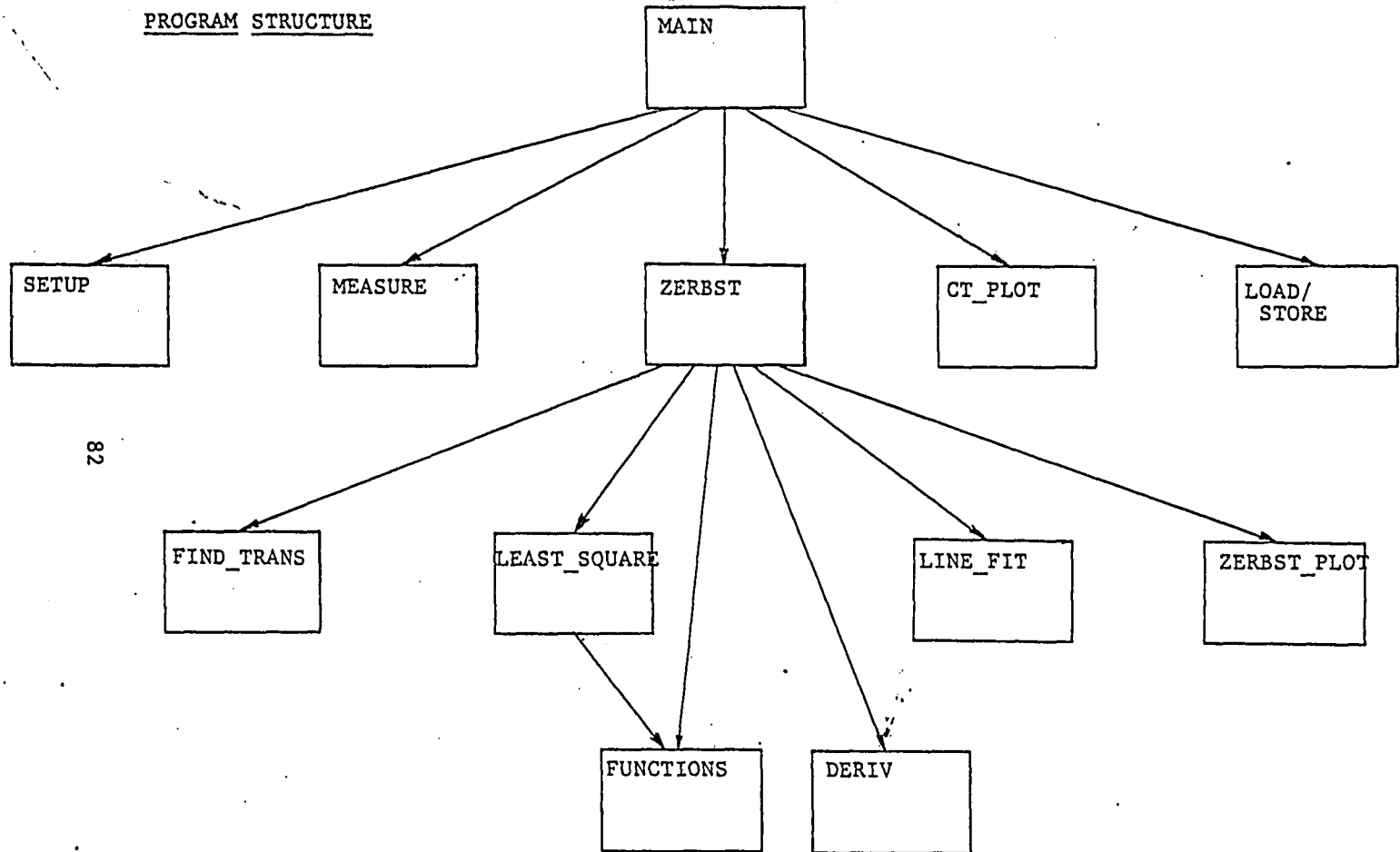
## APPENDIX E

### Pulsed C-t Automation Program

This program can be used to perform data gathering in a Pulsed C-t experiment and the subsequent Zerbst analysis. The program is designed in a structured fashion so that the programmed functions are available to the user through use of the software keys. The function available to the user are setup, measure graph, store, load, and analysis.

Typically, the user would first run SETUP which would prompt for needed input data. Following this task, the user would run MEASURE which would gather the data. Sometime during the measure routine (usually near the beginning) the user must press the "PULSE" key to apply the voltage pulse to the capacitor. When all the data is gathered, it can be graphed using the "GRAPH" function or stored for later use with the "STORE" function. Also at this point, the Zerbst analysis can be performed by pressing the "ZERBST" key. Previously measured data files are recalled with use of the "LOAD" key.

PROGRAM STRUCTURE



Variable Directory of COM Block  
/PULSECT\_DATA/

<u>Variable</u>	<u>Description</u>
NOTE\$ -	(STRING) 30 characters in which user may enter any comments or identifier; set by subroutine SETUP.
GENDATE\$ -	(STRING) Date fixed by measure subroutine indicating the date of measurement.
PACERATE\$ -	(STRING) User input parameter in subroutine SETUP indicating sampling rate of A/D converter; one character variable which can be letters A-F.
DIGPULSE\$ -	(STRING) Four character parameter generated by SETUP subroutine from user input of pulse height. Formatted output to D/A converter including scaler character (1 or 2) and 3 characters of digital counts.
DOPING_TYPE\$ -	(STRING) One character user input parameter in subroutine SETUP indicating doping type of device under test.
SETUP_FLAG -	(INTEGER) Switch set to 1 (true) when program has completed SETUP subroutine.
DATA_FLAG -	(INTEGER) Switch set to 1 (true) when program has successfully completed MEASURE subroutine.
THEO_EXP -	(INTEGER) Unused
CURVE_FIT -	(INTEGER) Switch set to 1 (true) when program has successfully completed LEAST SQUARE subroutine; reset by SETUP or MEASURE subroutines.
CAPACITANCE(1000) -	(REAL) measured data points of capacitance transient.
READTIME(1000) -	(REAL) measured data points of times when capacitance was read; filled by subroutine measure.
FUNC_COEF(10) -	(REAL) Fitted coefficients of functions determined by subroutine LEAST_SQUARE.
FIT_SLOPE -	(REAL) Fitted straight line slope determined by subroutine LINE_FIT

FIT\_INTERCEPT - (REAL) Fitted y-axis intercept for straight line determined by subroutine LINE\_FIT.

DOPING\_DENS - (REAL) User input parameter in subroutine SETUP indicating doping density of device under test.

THICK\_OXIDE - (REAL) Parameter determined by subroutine FIND\_TRANS indicating oxide thickness of device under test.

CINS - (REAL) Parameter determined by subroutine FIND\_TRANS indicating capacitance of insulator in D.U.T.

CO - (REAL) Unused.

CF - (REAL) Parameter determined by subroutine FIND\_TRANS indicating the final equilibrium capacitance of device after pulse has been applied.

KS - (REAL) User input parameter indicating the dielectric constant of silicon in the D.U.T.

KIN - (REAL) User input parameter in SETUP indicating the dielectric constant of the insulator in the D.U.T.

NI - (REAL) User input parameter in SETUP indicating the intrinsic carrier density in the D.U.T.

AREA - (REAL) User input parameter in SETUP indicating the area of the D.U.T.

DELTA - (REAL) Parameter determined in SETUP indicating the time interval between measurements determined from the sampling rate of the A/D converter.

LIFETIME - (REAL) Parameter determined by subroutine ZERBST indicating the measured generation lifetime of the D.U.T.

SURFACE\_VEL - (REAL) Parameter determined by subroutine ZERBST indicating the measured surface recombination velocity of the D.U.T.



Subroutine Directory  
Pulsed C-T Experiment Program

MEASURE

COM Blocks:

/PULSECT\_DATA/

Function:

Subroutine monitors the capacitance across the D.U.T. at the pacing rate determined by the sampling rate of the A/D converter. This subroutine also applies the voltage pulse to the device when defined software key is pressed by user.

SETUP

COM Blocks

/PULSECT\_DATA/

Function:

Subroutine re-initializes the data COM block to restart experiment. User input parameters are filled through user prompts.

CT PLOT

COM Blocks:

/PULSECT\_DATA/

/AXIS\_FLAG/

AXIS\_DRAWN - Switch indicating if axis drawn  
on graphics display.

Function:

This subroutine plots the data gathered by the measure subroutine in a plot of capacitance versus time.

## GAUSS ELIM

### Pass Parameters:

- N - (INTEGER) Number of rows in A matrix.
- A(\*) - (REAL) Augmented matrix of N rows which will be diagonalized.
- X(\*) - (REAL) Array of N elements giving the result of the gauss elimination process.

### Function:

This subroutine diagonalizes the A matrix by the method of Gauss Elimination. The X matrix or result matrix is determined by dividing the auxiliary row of the augmented matrix by the diagonal element of the A matrix.

## LEAST SQUARE

### Pass Parameters:

- X(\*) - (REAL) Array of independent parameters of data points.
- Y(\*) - (REAL) Array of dependant parameter values at the X value data points; array to be fitted.
- DATA\_POINTS - (INTEGER) Number of points in data array
- NO\_OF\_FUNCTIONS - (INTEGER) Number of functions to be fitted to the data.
- INFO\_FLAG - (INTEGER) Unused.
- COEFFICIENTS(\*) - (REAL) Coefficients of functions which give best least square fit.

### Function:

This subroutine creates the matrix to be solved by Gauss Elimination which is the set of equations which minimizes the squared error between the fit and the data.

## FUNCTIONS

Pass Parameters:

X - (REAL) Independent variable value.

FUNC(\*) - (REAL) Value of evaluated functions.

Function:

Evaluate programmed functions using given x value.

## STORE DATA

COM Blocks:

/PULSECT\_DATA/

Function:

This subroutine creates and writes a data disk file which holds the data from the COM Block /PULSECT\_DATA/

## LOAD DATA

COM Blocks:

/PULSECT\_DATA/

Function:

This subroutine loads a data file from disk properly formatted to fill the COM Block /PULSECT\_DATA/

## ZERBST

COM Blocks:

/PULSECT\_DATA/

Function:

This subroutine is the driver for the Zerbst method of data analysis of the capacitance transient. This subroutine extracts the recovery transient through a call to FIND TRANS after which it does a linear least square fit to the data. The subroutine then does the analytical derivation of the fitted functions and uses them to create the independent and dependent variables of the Zerbst relationship. Using these variables an optimal straight line fit is extracted and from the fitted straight line the generation lifetime and surface recombination velocity are calculated.

## FIND TRANS

COM Blocks:

/PULSECT\_DATA/

Pass Parameters:

ZERX(\*) - (REAL) Data array of the independent variable in the Zerbst relationship generated by this subroutine.

CURVE\_TO\_FIT(\*) - (REAL) Data array of the extracted capacitance recovery transient.

TIME\_TRAN(\*) - (REAL) Data array of the corresponding times for the recovery transient.

DATA\_POINTS - (INTEGER) No. of points in extracted data array.

ERROR\_FLAG - (INTEGER) Switch indicating processing error in subroutine.

Function:

This subroutine takes the raw data as it exists in the data arrays in the COM Block /PULSECT\_DATA/ and extracts the recovery transient. The subroutine finds

the beginning of the recovery transient by marking the end of the down transient. The end of transient is defined as the capacitance which has recovered to 97% of its final value. The transient is moved to the data array CURVE TO FIT and the Zerbst independant variable is calculated and saved in ZERX(\*) .

#### DERIV

Pass Parameters:

- X - (REAL) Independant variable value.
- DERIV(\*) - (REAL) Value of evaluated derivatives calculated by subroutine.

Function:

This subroutines evaluates the programmed derivatives using given X value.

#### LINE FIT

Pass Parameters:

- ZERX(\*) - (REAL) Independant variable of curve to be fitted.
- ZERY(\*) - (REAL) Dependant variable of curve to be fitted.
- DATA\_POINTS - (INTEGER) No. of data points in curve to fit.
- FIT\_SLOPE - (REAL) Extracted slope of optimally fitted line.
- FIT\_INTERCEPT - (REAL) Extracted y intercept of optimally fitted straight line.

Function:

This subroutine does a optimal straight line fit to the data in the ZERX(\*) and ZERY(\*) arrays. This is done by taking segments of the arrays and doing a least square error straight line fit to the segment. The optimal fit is chosen by finding the minimum residual varience of the fit.

## ZERBST PLOT

Pass Parameters:

ZERX(\*) - (REAL) x variable in Zerbst plot.

ZERY(\*) - (REAL) y variable in Zerbst plot.

DATA\_POINTS - (INTEGER) Number of points in  
data arrays.

Function:

This subroutine creates the plot of the final data created in the Zerbst analysis. The x variables is  $C_f/C - 1$  and the y variable is the time derivative of  $(C_o/C)$  squared.

```

*10  !*****
20  !      PULSED CAPACITANCE-VOLTAGE MEASUREMENTS PROGRAM
30  !*****
40  !
50  !      DECLARATIONS
60  !
61  COM /Pulsect_data/ Notes$(30)
70  COM /Pulsect_data/ Gendate$(11),Pacerate$(1),Digpulse$(4),Doping_type$(1)
80  COM /Pulsect_data/ INTEGER Setup_flag,Data_flag,Theo_exp,Curve_fit
90  COM /Pulsect_data/ REAL Capacitance(1000),Readtime(1000)
100 COM /Pulsect_data/ Function_coef(10),Fit_slope,Fit_intercept
110 COM /Pulsect_data/ Doping_dens,Thick_oxide,Cins,CO,Cf,Ks,Kin,Ni,Area,Delta
120 COM /Pulsect_data/ Lifetime,Surface_vel
130 !
140 DIM Blanks$(60)
150 Blanks$=""
160 !
170 !      DEFINE KEY FUNCTIONS
180 !
190 ON KEY 0 LABEL "HELP",1 GOSUB Dummy
200 ON KEY 1 LABEL "SETUP",7 CALL Setup
210 ON KEY 2 LABEL "MEASURE",6 CALL Measure
220 ON KEY 3 LABEL "PULSE",10 GOSUB Dummy
230 ON KEY 4 LABEL "CTPLOT",3 CALL Ct_plot
240 ON KEY 5 LABEL "ZERBST",4 CALL Zerbst
250 ON KEY 6 LABEL "THEORY",5 GOSUB Dummy
260 ON KEY 7 LABEL "LOAD",8 CALL Load_data
270 ON KEY 8 LABEL "STORE",3 CALL Store_data
280 ON KEY 9 LABEL "EXIT",.2 GOTO Ending
290 !
300 !      SET MACHINE IN IDLE LOOP WHILE WAITING FOR KEY INTERRUPTS
310 !
320 WHILE 1=1
330     DISP FNTIME$(TIMEDATE)&Blanks$&FNDATE$(TIMEDATE)
340 END WHILE
350 !
360 !      DUMMY SUBROUTINE
370 Dummy: !
380 RETURN
390 !
400 !      EXIT PROGRAM
410 !
420 Ending: !
430 END!

```

```

440 SUB Measure
450!
460! SUBROUTINE MEASURE TAKES DATA FROM PULSED CAPACITANCE-VOLTAGE EXPERIMENT
470!
480!
490!     DECLARATIONS
500!
501 COM /Pulsect_data/ Notes$(30)
510 COM /Pulsect_data/ Gendate$(11),Pacerate$(1),Dimpulse$(4),Doping_type$(1)
520 COM /Pulsect_data/ INTEGER Setup_flag,Data_flag,Theo_exp,Curve_fit
530 COM /Pulsect_data/ REAL Capacitance(1000),Readtime(1000)
540 COM /Pulsect_data/ Function_coef(10),Fit_slope,Fit_intercept
550 COM /Pulsect_data/ Doping_dens,Thick_oxide,Cins,C0,Cf,Ks,Kin,Ni,Area,Delt
560 COM /Pulsect_data/ Lifetime,Surface_vel
570!
580     INTEGER Done,Readings(1000)
590     DIM Blanks$(60)
600     Blanks$=""
610!
620!     CHECK TO SEE THAT SET UP IS COMPLETED FOR EXPERIMENT
630!
640 IF Setup_flag=0 THEN
650     OUTPUT 1;CHR$(12)
660     BEEP
670     OUTPUT 1;"ERROR: EXPERIMENT HAS NOT COMPLETED SETUP"
680     OUTPUT 1;"PRESS ""SET UP"" BEFORE MEASURE"
690     GOTO Endsub
700 ELSE
710!
720!     INITIALIZATION
730!
740     OUTPUT 1;CHR$(12)
750     OUTPUT 1;"***** MEASUREMENT PHASE *****"
760     OUTPUT 1;CHR$(10);CHR$(10);"PRESS ""PULSE"" KEY TO APPLY VOLTAGE PULSE T
0 DEVICE"
770     J=0
780     Done=0
790     ASSIGN @HpiB TO 7
800     SEND @HpiB;UNL LISTEN 6 MTA DATA "H2L"&Pacerate$ ! RESET A/D CONVERTOR
810     ON KEY 3 LABEL "PULSE",10 GOSUB Pulse ! ENABLE PULSE KEY
820!
830!     BEGIN TAKING READINGS FROM A/D CONVERTOR
840!
850     ON INTR 7,13 GOSUB Reading
860     SEND @HpiB;UNL LISTEN 6 MTA DATA "J" ! START A/D CONVERTOR
870     SEND @HpiB;CMD "?5F" ! UNL TALK 6 MLA
880     ENABLE INTR 7;2
890!
900!     PLACE MACHINE IN IDLE LOOP WHILE WAITING FOR DATA FROM A/D
910!
920     WHILE Done=0
930         DISP FNTimes$(TIMEDATE)
940     END WHILE
950!
960!     EXPERIMENT COMPLETE SET D/A TO ZERO
970!
980     SEND @HpiB;UNL LISTEN 7 MTA DATA "2000"

```



```

990 !
1000 ! CONVERT READINGS TO CAPACITANCE AND TIME
1010 !
1020 FOR I=1 TO 1000
1030   Capacitance(I)=Readings(I)/4
1040   SELECT Pacerate$
1050     CASE "B"
1060       Readtime(I)=(I*5.E-3)-(5.E-3)
1070     CASE "C"
1080       Readtime(I)=(I*1.0E-2)-(1.0E-2)
1090     CASE "D"
1100       Readtime(I)=(I*2.0E-2)-(2.0E-2)
1110     CASE "E"
1120       Readtime(I)=(I*5.0E-2)-(5.0E-2)
1130     CASE "F"
1140       Readtime(I)=(I*1.00E-1)-(1.00E-1)
1150     CASE "G"
1160       Readtime(I)=(I*2.00E-1)-(2.00E-1)
1170   END SELECT
1180 NEXT I
1190 !
1200 !   END OF PULSED C-T EXPERIMENTAL READINGS
1210 !
1220 Data_flag=1
1230 Theo_exp=1
1240 Curve_fit=0
1250 FOR I=1 TO 10
1260   Function_coef(I)=0
1270 NEXT I
1280 Fit_slope=0
1290 Fit_intercept=0
1300 Gendate$=FNDate$(TIMEDATE)
1310 OUTPUT 1;CHRS(12)
1320 GOTO Endsub
1330 END IF
1340 !
1350 !*****
1360 ! SERVICE SUBROUTINES FOR INTERRUPT EVENTS
1370 !*****
1380 !
1390 ! PULSE: APPLY VOLTAGE PULSE TO DEVICE
1400 !
1410 Pulse: !
1420   DISABLE
1430   SEND @HpiB;CMD "?U" DATA Digpulse$
1440   SEND @HpiB;CMD "?5F"
1450   ENABLE
1460   RETURN
1470 !
1480 ! READING: TAKE READING FROM A/D CONVERTOR
1490 !
1500 Reading: !
1510   J=J+1
1520   ENTER @HpiB USING "#,W";Readings(J)
1530   IF J<1000 THEN
1540     ENABLE INTR 7:2
1550   ELSE
1560     SEND @HpiB;UNL LISTEN 6 MTA DATA "I"
1570     Done=1
1580   END IF
1590   RETURN

```

1600!  
1610!       END OF SUBROUTINE MEASURE  
1620!  
1630 Endsub: !  
1640 SUBEND!

```

1650 SUB Setup
1660 !
1670 !*****
1680 ! SUBROUTINE SETUP GETS PARAMETERS FROM USER TO RUN EXPERIMENT
1690 !*****
1700 !
1710 ! DECLARATIONS
1720 !
1721 COM /Pulsect_data/ Notes${30}
1730 COM /Pulsect_data/ Gendate${11},Pacerate${1},Dimpulse${4},Doping_type${11}
1740 COM /Pulsect_data/ INTEGER Setup_flag,Data_flag,Theo_exp,Curve_fit
1750 COM /Pulsect_data/ REAL Capacitance(1000),Readtime(1000)
1760 COM /Pulsect_data/ Function_coef(10),Fit_slope,Fit_intercept
1770 COM /Pulsect_data/ Doping_dens,Thick_oxide,Cins,C0,Cf,Ks,Kin,Ni,Area,Delta
1780 COM /Pulsect_data/ Lifetime,Surface_vel
1790 !
1800 REAL Pulse_voltage
1810 !
1820 ! SANITY CHECK ON USER
1830 !
1840 OUTPUT 1;CHR$(12)
1850 IF Data_flag=1 THEN
1860 BEEP
1870 PRINT "WARNING: INTERNAL DATA FILE ABOUT TO BE RE-INITIALIZED, PRESS ""
STORE"" TO SAVE DATA ON DISK"
1880 WAIT 10
1890 END IF
1900 !
1910 !
1920 OUTPUT 1;CHR$(12)
1930 OUTPUT 1;"***** SET - UP PHASE *****"
*****"
1940 Gendate$=" "
1950 Pacerate$=" "
1960 Dimpulse$=" "
1970 Doping_type$=" "
1980 Setup_flag=0
1990 Data_flag=0
2000 Theo_exp=0
2010 Curve_fit=0
2020 FOR I=1 TO 1000
2030 Capacitance(I)=0
2040 Readtime(I)=0
2050 NEXT I
2060 FOR I=1 TO 10
2070 Function_coef(I)=0
2080 NEXT I
2090 Fit_slope=0
2100 Fit_intercept=0
2110 Doping_dens=0
2120 Thick_oxide=0
2130 Cins=0
2140 C0=0
2150 Cf=0
2160 Ks=0
2170 Kin=0
2180 Ni=0
2190 Area=0
2200 Delta=0
2210 Lifetime=0

```

```

2220 Surface_vel=0
2230 !
2240 ! INPUT PACING RATE CHARACTER TO BE OUTPUT TO A/D CONVERTOR
2250 !
2260 OUTPUT 1;"*** EXPERIMENT PARAMETERS ***"
2270 OUTPUT 1;CHR$(10)
2280 Get_pace: !
2290 OUTPUT 1;" "
2300 OUTPUT 1;"ENTER PACING RATE CHARACTER FOR A/D CONVERTOR(B-G):"
2310 INPUT Pacerate$
2320 !
2330 IF Pacerate$<"B" OR Pacerate$>"G" THEN
2340 OUTPUT 1;"INVALID PACERATE ENTRY, MUST BE ONE OF LETTERS B,C,D,E,F, OR
G"
2350 GOTO Get_pace
2360 END IF
2370 !
2380 ! RETRIEVE THE TIME INTERVAL OF MEASUREMENT FROM THE PACERATE
2390 !
2400 SELECT Pacerate$
2410 CASE "B"
2420 Delta=5.0E-3
2430 CASE "C"
2440 Delta=1.00E-2
2450 CASE "D"
2460 Delta=2.0E-2
2470 CASE "E"
2480 Delta=5.0E-2
2490 CASE "F"
2500 Delta=1.00E-1
2510 CASE "G"
2520 Delta=2.00E-1
2530 END SELECT
2540 !
2550 ! GET VOLTAGE PULSE HEIGHT AND CHANGE TO DIGITAL NUMBER
2560 ! (ASSUME FULL SCALE OF D/A SET TO 10 VOLTS)
2570 !
2580 Get_volt: !
2590 OUTPUT 1;" "
2600 OUTPUT 1;"ENTER VOLTAGE PULSE HEIGHT:"
2610 INPUT Pulse_voltage
2620 !
2630 IF Pulse_voltage>0 AND Pulse_voltage<10 THEN
2640 Digpulse=Pulse_voltage*1000/10
2650 ELSE
2660 PRINT "INVALID VOLTAGE ENTRY, MUST BE POSITIVE LESS THAN 40"
2670 GOTO Get_volt
2680 END IF
2690 Digpulse$="2"&VAL$(Digpulse)
2700 !
2710 ! GET D.U.T. PARAMETERS
2720 !
2721 OUTPUT 1
2722 OUTPUT 1
2730 OUTPUT 1;"*** DEVICE PARAMETERS ***"
2731 !
2732 OUTPUT 1;"ENTER DOPING TYPE OF DEVICE UNDER TEST(N OR P):"
2733 INPUT Doping_type$
2734 !
2740 OUTPUT 1;"ENTER DOPING DENSITY OF SILICON(CM^-3):"

```

```
2750 INPUT Doping_den
2760 !
2770 OUTPUT 1;"ENTER INTRINSIC CARRIER CONC(CM^-3):"
2780 INPUT Ni
2790 !
2800 OUTPUT 1;"ENTER DIELECTRIC CONSTANT OF SILICON:"
2810 INPUT Ks
2820 !
2830 OUTPUT 1;"ENTER DIELECTRIC CONSTANT OF INSULATOR:"
2840 INPUT Kin
2850 !
2860 OUTPUT 1;"ENTER AREA OF CAPACITOR(ANGSTROMS^2):"
2870 INPUT Area
2871 !
2872 OUTPUT 1;"ENTER COMMENTS:"
2873 INPUT Notes$
2880 !
2890 !      SET FLAG TO INDICATE THAT SETUP PHASE HAS BEEN COMPLETED
2900 !
2910 OUTPUT 1;CHR$(12)
2920 Setup_flag=1
2930 !
2940 SUBEND!
```

```

2950 SUB Ct_plot
2960 !
2970 !*****
2980 !      SUBROUTINE CT_PLOT DRAW CAPACITANCE VS. TIME PLOT
2990 !*****
3000 !
3010 !      DECLARATIONS
3020 !
3021 COM /Pulsect_data/ Notes${30]
3030 COM /Pulsect_data/ Gendate${11},Pacerate${11},Dimpulse${4},Doping_type${11]
3040 COM /Pulsect_data/ INTEGER Setup_flag,Data_flag,Theo_exp,Curve_fit
3050 COM /Pulsect_data/ REAL Capacitance(1000),Readtime(1000)
3060 COM /Pulsect_data/ Function_coef(10),Fit_slope,Fit_intercept
3070 COM /Pulsect_data/ Doping_dens,Thick_oxide,Cins,CO,Cf,Ks,Kin,Ni,Area,Delta
3080 COM /Pulsect_data/ Lifetime,Surface_vel
3090 !
3100 COM /Axis_flag/ Axes_drawn
3110 !
3120 DIM Label${30]
3130 !
3140 !      CLEAR DISPLAY SCREEN
3150 !
3160 OUTPUT 1;CHR$(12)
3170 !
3180 IF Data_flag=0 THEN
3190     BEEP
3200     OUTPUT 1;"ERROR: NO DATA AVAILABLE TO PLOT"
3210     GOTO Endsub
3220 END IF
3230 !
3240 !      SEE IF AXES ARE MULTIPLE PLOT AXES
3250 !
3260 IF Axes_drawn=1 THEN
3270     OUTPUT 1;"SHOULD DATA BE PLOTTED ON SAME AXIS (ANSWER YES OR NO):"
3280     INPUT Answer$
3290     IF Answer$<>"YES" THEN Axes_drawn=0
3300 END IF
3310 !
3320 !      BEGIN DRAWING PLOT
3330 !
3340 OUTPUT 1;CHR$(12)
3350 OUTPUT 1;"***** CAPACITANCE VS. TIME PLOT BEING GENERATED *****"
3360 !
3370 !      INITIALIZE GRAPHICS DISPLAY
3380 !
3390 DEG
3400 CLIP OFF
3410 PIVOT 0
3420 PEN 1
3430 LINE TYPE 1,5
3440 LORG 1
3450 CSIZE 5,.6
3460 LDIR 0
3470 MOVE 0,0
3480 !
3490 !      DRAW AXES IF NEEDED
3500 !
3510 IF Axes_drawn=0 THEN

```

```

3520 GCLEAR
3530 !
3540 !   DEFINE GRAPHICS UNITS
3550 !
3560 Fullheight=Capacitance(1)/.75
3570 Fullwidth=Readtime(1000)/.85
3580 Left=-.075*Fullwidth
3590 Right=Left+Fullwidth
3600 Bottom=-.075*Fullheight
3610 Top=Bottom+Fullheight
3620 WINDOW Left,Right,Bottom,Top
3630 !
3640 !   TITLE GRAPH
3650 !
3660 LORG 6
3670 CSIZE 6,.6
3680 MOVE Left+Fullwidth/2,Top
3690 LABEL "CAPACITANCE VS. TIME"
3700 !
3710 !   DATE GRAPH
3720 !
3730 LORG 9
3740 CSIZE 2,.6
3750 MOVE Right,Top
3760 LABEL "GRAPH DATE:"&FNDate$(TIMEDATE)
3770 !
3780 MOVE Right,Top-.02*(Top-Bottom)
3790 LABEL "MEAS. DATE:"&Gendate$
3800 !
3810 !   LABEL AXES
3820 !
3830 LORG 4
3840 LDIR 0
3850 CSIZE 5,.6
3860 MOVE Left+Fullwidth/2,Bottom
3870 LABEL "TIME(SECS)"
3880 !
3890 LORG 6
3900 LDIR 90
3910 MOVE Left,Bottom+Fullheight/2
3920 LABEL "CAPACITANCE (PF)"
3930 !
3940 !   PLACE KEY ON GRAPH
3950 !
3960 LORG 2
3970 LDIR 0
3980 CSIZE 3,.6
3990 !
4000 MOVE Left+.70*(Right-Left),Bottom+.80*(Top-Bottom)
4010 LABEL Notes$
4020 !
4030 MOVE Left+.70*(Right-Left),Bottom+.76*(Top-Bottom)
4040 LABEL Doping_type$&"-type Silicon"
4050 !
4060 OUTPUT Labels USING "K,D.DDESZZ,K";"Nd=",Doping_dens," cm^-3"
4070 MOVE Left+.70*(Right-Left),Bottom+.72*(Top-Bottom)
4080 LABEL Labels$
4090 !
4140 OUTPUT Labels USING "K,D.DDESZZ,K";"Area=",Area," cm^2"
4150 MOVE Left+.70*(Right-Left),Bottom+.68*(Top-Bottom)
4160 LABEL Labels$

```

```

4170      !
4180      !   NUMBER AXES
4190      !
4200      LORG 6
4210      LDIR 0
4220      CSIZE 3,.6
4230      FOR I=1 TO 1000 STEP 100
4240          MOVE Readtime(I),0
4250          LABEL Readtime(I)
4260      NEXT I
4270      !
4280      LORG 8
4290      CSIZE 2,.6
4300      Top=(INT(Capacitance(1)/.88)+1)*100
4310      FOR I=0 TO Top STEP Top/10
4320          IF Capacitance(1)/.88>I THEN
4330              MOVE 0,I
4340              LABEL I
4350          END IF
4360      NEXT I
4370      !
4380      !   DRAW AXES
4390      !
4400      CLIP 0,Readtime(1000),0,Capacitance(1)/.88
4410      AXES Readtime(101),Top/10,0,0,2,2
4420      CLIP OFF
4430      Axes_drawn=1
4440      END IF
4450      !
4460      ! ***** PLOT DATA POINTS *****
4470      !
4480      CLIP 0,Readtime(1000),0,Capacitance(1)/.88
4490      PENUP
4500      MOVE Readtime(1),Capacitance(1)
4510      FOR I=1 TO 1000
4520          DRAW Readtime(I),Capacitance(I)
4530      NEXT I
4540      PENUP
4550      CLIP OFF
4560      OUTPUT 1:CHR$(12)
4570      !
4580      Endsub: !
4590      SUBEND!

```



```

4600 SUB Gauss_elim(INTEGER N,REAL A(*),X(*)
4610 !
4620 !*****
4630 ! SUBROUTINE GAUSS_ELIM SOLVES A SET OF N SIMULTANEOUS EQUATIONS
4640 ! BY THE METHOD OF GAUSSIAN ELIMINATION
4650 !*****
4660 !
4670 ! DECLARATIONS
4680 !
4690 REAL Matrix(10,11),Biggest,Temp,Sum,Quot
4700 INTEGER I,J,K,Jj
4710 !
4720 ! ***** BEGIN GAUSSIAN ELIMINATION PROCESS *****
4730 !
4740 FOR K=1 TO N
4750 !
4760 ! SEARCH FOR LARGEST ELEMENT IN COLUMN
4770 !
4780 Jj=K
4790 Biggest=ABS(A(K,K))
4800 FOR I=K+1 TO N
4810 IF ABS(A(I,K))>Biggest THEN
4820 Biggest=ABS(A(I,K))
4830 Jj=I
4840 END IF
4850 NEXT I
4860 !
4870 ! ROW INTERCHANGE IF NECESSARY
4880 !
4890 IF Jj<>K THEN
4900 FOR J=K TO N+1
4910 Temp=A(Jj,J)
4920 A(Jj,J)=A(K,J)
4930 A(K,J)=Temp
4940 NEXT J
4950 END IF
4960 !
4970 ! CALCULATE NEW MATRIX
4980 !
4990 FOR I=K+1 TO N
5000 Quot=A(I,K)/A(K,K)
5010 FOR J=K+1 TO N+1
5020 A(I,J)=A(I,J)-Quot*A(K,J)
5030 NEXT J
5040 NEXT I
5050 !
5060 ! ZERO APPROPRIATE COLUMN
5070 !
5080 FOR I=K+1 TO N
5090 A(I,K)=0
5100 NEXT I
5110 NEXT K
5120 !
5130 ! BEGIN BACK SUBSTITUTION
5140 !
5150 X(N)=A(N,N+1)/A(N,N)
5160 FOR I=N-1 TO 1 STEP -1
5170 Sum=0
5180 FOR J=I+1 TO N
5190 Sum=Sum+A(I,J)*X(J)

```

```
5200     NEXT J
5210     X(I)=(A(I,N+1)-Sum)/A(I,I)
5220     NEXT I
5230     !
5240     !     EXIT
5250     !
5260     SUBEND!
```

```

5270 SUB Least_square(REAL X(*),Y(*),INTEGER Data_points,No_of_functions,Info_f
lag,REAL Coefficiants(*))
5280 !
5290 !*****
5300 ! SUBROUTINE LEAST_SQUARE DOES LEAST SQUARE CURVE FITTING BY FORMING
5310 ! MATRIX REPRESENTING SIMULTANEOUS EQUATIONS WHICH CAN SOLVE
5320 ! FOR COEFFICIANTS OF USER-DEFINED FUNCTIONS
5330 !*****
5340 !
5350 ! DECLARATIONS
5360 !
5370 REAL F(10),Matrix(10,11)
5380 !
5390 ! FILL MATRIX
5400 !
5410 FOR K=1 TO Data_points
5420 CALL Functions(X(K),F(*))
5430 !
5440 FOR I=1 TO No_of_functions
5450 FOR J=1 TO No_of_functions
5460 Matrix(I,J)=F(I)*F(J)+Matrix(I,J)
5470 Matrix(J,I)=Matrix(I,J)
5480 NEXT J
5490 Matrix(I,No_of_functions+1)=Matrix(I,No_of_functions+1)+F(I)*Y(K)
5500 NEXT I
5510 NEXT K
5520 !
5530 ! SOLVE SYSTEM OF SIMULTANEOUS EQUATIONS
5540 !
5550 CALL Gauss_elim(No_of_functions,Matrix(*),Coefficiants(*))
5560 !
5570 ! EXIT
5580 !
5590 SUBEND!

```

```

5600 DEF FNTIME$(Now) ! GIVEN 'SECONDS' RETURN 'HH:MM:SS'
5610 !
5620 Now=INT(Now) MOD 86400
5630 H=Now DIV 3600
5640 M=Now MOD 3600 DIV 60
5650 S=Now MOD 60
5660 OUTPUT T$ USING "#,ZZ,K";H,":",M,":",S
5670 RETURN T$
5680 FNEND!

```

```

5690 !
5700 DEF FNTIME(T$) ! GIVEN 'HH:MM:SS' RETURN 'SECONDS'
5710 !
5720 ON ERROR GOTO Err
5730 ENTER T$;H,M,S
5740 RETURN (3600*H+60*M+S) MOD 86400
5750 Err:OFF ERROR
5760 RETURN TIMEDATE MOD 86400
5770 FNEND!

```

```

5780 DEF FNDATE$(Seconds) !GIVEN 'SECONDS' RETURN "DD MMM YYYY"
5790 !
5800 DATA JAN,FEB,MAR,APR,MAY,JUN,JUL,AUG,SEP,OCT,NOV,DEC
5810 DIM Month$(1:12)[3]
5820 READ Month$(*)
5830 !
5840 Julian=Seconds DIV 86400-1721119
5850 Year=(4*Julian-1) DIV 146097
5860 Julian=(4*Julian-1) MOD 146097
5870 Day=Julian DIV 4
5880 Julian=(4*Day+3) DIV 1461
5890 Day=(4*Day+3) MOD 1461
5900 Day=(Day+4) DIV 4
5910 Month=(5*Day-3) DIV 153
5920 Day=(5*Day-3) MOD 153
5930 Day=(Day+5) DIV 5
5940 Year=100*Year+Julian
5950 IF Month<10 THEN
5960 Month=Month+3
5970 ELSE
5980 Month=Month-9
5990 Year=Year+1
6000 END IF
6010 OUTPUT D$ USING "#,ZZ,X,3A,X,4Z";Day,Month$(Month),Year
6020 RETURN D$
6030 FNEND!

```

```

6040 !
6050 DEF FNDATE(Dmy$) ! GEVEN 'DD MMM YYYY' RETURN 'SECONDS'
6060 !
6070 DATA JAN,FEB,MAR,APR,MAY,JUN,JUL,AUG,SEP,OCT,NOV,DEC
6080 DIM Month$(1:12)[3]
6090 READ Month$(*)
6100 !
6110 ON ERROR GOTO Err
6120 I$=Dmy$&"

```

```

6130 ENTER I$ USING "DD,4A,5D";Day,M$,Year
6140 IF Year<100 THEN Year=Year+1900
6150 FOR I=1 TO 12
6160 IF POS(M$,Month$(I)) THEN Month=I
6170 NEXT I
6180 IF Month=0 THEN Err
6190 IF Month>2 THEN
6200 Month=Month-3
6210 ELSE
6220 Month=Month+9
6230 Year=Year-1
6240 END IF
6250 Century=Year DIV 100
6260 Remainder=Year MOD 100
6270 Julian=146097*Century DIV 4+1461*Remainder DIV 4+(153*Month+2) DIV 5+Day
+1721119
6280 Julian=Julian*86400
6290 IF Julian<2.08662912E+11 OR Julian>=2.143252224E+11 THEN Err
6300 RETURN Julian ! RETURN JULIAN DATE IN SECONDS
6310 Err: OFF ERROR
6320 RETURN TIMEDATE ! RETURN CURRENT DATE
6330 FNEND!

```

```

6340 SUB Functions(X,Func(*))
6350 !
6360 !*****
6370 ! SUBROUTINE FUNCTIONS EVALUATES THE FUNCTIONS AT THE GIVEN X VALUES
6380 !*****
6390 !
6400 ! DECLARATIONS
6410 !
6411 COM /Pulsect_data/ Notes$(30)
6420 COM /Pulsect_data/ Gendate$(11),Pacerate$(1),Digpulse$(4),Doping_type$(1)
6430 COM /Pulsect_data/ INTEGER Setup_flag,Data_flag,Theo_exp,Curve_fit
6440 COM /Pulsect_data/ REAL Capacitance(1000),Readtime(1000)
6450 COM /Pulsect_data/ Function_coef(10),Fit_slope,Fit_intercept
6460 COM /Pulsect_data/ Doping_dens,Thick_oxide,Cins,CO,Cf,Ks,Kin,Ni,Area,Delta
6470 COM /Pulsect_data/ Lifetime,Surface_vel
6480 !
6490 ! EVALUATE FUNCTIONS
6500 !
6510 Func(1)=1.0
6520 Func(2)=X*.125
6530 Func(3)=X*.25
6540 Func(4)=X*.5
6550 Func(5)=X*.75
6560 Func(6)=X
6570 Func(7)=X^2
6580 Func(8)=(5.0*Delta)/(X+.1*Delta)
6590 Func(9)=(10.0*Delta)/(X+.3*Delta)
6600 !
6610 ! EXIT FUNCTION EVALUATING SUBROUTINE
6620 !
6630 SUBEND!

```

```

6640 SUB Store_data
6650 !
6660 !*****
6670 ! SUBROUTINE STORE_DATA STORES THE INTERNAL DATA FILE INTO A DISK
6680 !*****
6690 !
6700 ! DECLARATIONS
6710 !
6711 COM /Pulsect_data/ Notes${30}
6720 COM /Pulsect_data/ Gendate${11};Pacerate${1},Digpulse${4},Doping_type${1}
6730 COM /Pulsect_data/ INTEGER Setup_flag,Data_flag,Theo_exp,Curve_fit
6740 COM /Pulsect_data/ REAL Capacitance(1000),Readtime(1000)
6750 COM /Pulsect_data/ Function_coef(10),Fit_slope,Fit_intercept
6760 COM /Pulsect_data/ Doping_dens,Thick_oxide,Cins,C0,Cf,Ks,Kin,Ni,Area,Delta
6770 COM /Pulsect_data/ Lifetime,Surface_vel
6780 !
6790 DIM File_specifier${30},File_name${10},Answer${1}
6800 !
6810 ! DEFINE PROGRAM STATE TO USER
6820 !
6830 OUTPUT 1;CHR$(12)
6840 OUTPUT 1;"***** STORAGE OF INTERNAL DATA FILE ON DISK *****
*****"
6850 !
6860 ! GET NAME OF FILE FROM USER
6870 !
6880 OUTPUT 1;"ENTER FILE NAME:"
6890 INPUT File_name$
6900 !
6910 ! LEFT OR RIGHT HAND INTERNAL DISK DRIVE?
6920 !
6930 OUTPUT 1;"SPECIFY WHETHER STORAGE DISK IS MOUNTED IN LEFT OR RIGHT HAND DR
IVE"
6940 OUTPUT 1;"ENTER L OR R:"
6950 INPUT Answer$
6960 IF Answer$="L" THEN
6970 File_specifier$=File_name$&":INTERNAL,4,1"
6980 ELSE
6990 File_specifier$=File_name$&":INTERNAL,4,0"
7000 END IF
7010 !
7020 ! CREATE DISK FILE
7030 !
7040 CREATE BDAT File_specifier$,6,4096
7050 ASSIGN @File TO File_specifier$;FORMAT OFF
7060 !
7070 ! PLACE COM VARIABLE IN FILE
7080 !
7081 OUTPUT @File;Notes$
7090 OUTPUT @File;Gendate$;Pacerate$;Digpulse$;Doping_type$
7100 OUTPUT @File;Setup_flag;Data_flag;Theo_exp,Curve_fit
7110 OUTPUT @File;Capacitance(*)
7120 OUTPUT @File;Readtime(*)
7130 OUTPUT @File;Function_coef(*);Fit_slope;Fit_intercept
7140 OUTPUT @File;Doping_dens;Thick_oxide;Cins;C0;Cf;Ks;Kin;Ni;Area;Delta
7150 OUTPUT @File;Lifetime;Surface_vel
7160 !
7170 ! CLOSE I/O PATH
7180 !
7190 ASSIGN @File TO *

```

```
7200 OUTPUT 1;CHR$(12)
7210 !
7220 ! EXIT SUBROUTINE STORE_DATA
7230 !
7240 SUBEND!
```

```

7250 SUB Load_data
7250 !
7270 !*****
7280 ! SUBROUTINE LOAD_DATA RETRIEVES AN INTERNAL DATA FILE FROM DISK
7290 !*****
7300 !
7310 !   DECLARATIONS
7320 !
7321 COM /Pulsect_data/ Notes${30}
7330 COM /Pulsect_data/ Gendate${11},Pacerate${1},Digpulse${4},Doping_type${11}
7340 COM /Pulsect_data/ INTEGER Setup_flag,Data_flag,Theo_exp,Curve_fit
7350 COM /Pulsect_data/ REAL Capacitance(1000),Readtime(1000)
7360 COM /Pulsect_data/ Function_coef(10),Fit_slope,Fit_intercept
7370 COM /Pulsect_data/ Doping_dens,Thick_oxide,Cins,CO,Cf,Ks,Kin,Ni,Area,Delta
7380 COM /Pulsect_data/ Lifetime,Surface_vel
7390 !
7400 DIM File_specifier${30},File_name${10},Answer${11}
7410 !
7420 !   DEFINE PROGRAM STATE TO USER
7430 !
7440 OUTPUT 1;CHR$(12)
7450 OUTPUT 1;"***** LOAD OF INTERNAL DATA FILE FROM DISK *****
*****"
7460 !
7470 !   GET NAME OF FILE FROM USER
7480 !
7490 OUTPUT 1;"ENTER FILE NAME:"
7500 INPUT File_name$
7510 !
7520 !   LEFT OR RIGHT HAND INTERNAL DISK DRIVE?
7530 !
7540 OUTPUT 1;"SPECIFY WHETHER STORAGE DISK IS MOUNTED IN LEFT OR RIGHT HAND DR
IVE"
7550 OUTPUT 1;"ENTER L OR R:"
7560 INPUT Answer$
7570 IF Answer$="L" THEN
7580   File_specifier$=File_name$&":INTERNAL,4,1"
7590 ELSE
7600   File_specifier$=File_name$&":INTERNAL,4,0"
7610 END IF
7620 !
7630 !   CREATE DISK FILE
7640 !
7650 ASSIGN @File TO File_specifier$;FORMAT OFF
7660 !
7670 !   PLACE COM VARIABLE IN FILE
7680 !
7681 ENTER @File;Notes$
7690 ENTER @File;Gendate$;Pacerate$;Digpulse$;Doping_type$
7700 ENTER @File;Setup_flag;Data_flag;Theo_exp;Curve_fit
7710 ENTER @File;Capacitance(*)
7720 ENTER @File;Readtime(*)
7730 ENTER @File;Function_coef(*);Fit_slope;Fit_intercept
7740 ENTER @File;Doping_dens;Thick_oxide;Cins,CO,Cf,Ks,Kin,Ni,Area,Delta
7750 ENTER @File;Lifetime;Surface_vel
7760 !
7770 !   CLOSE I/O PATH
7780 !
7790 ASSIGN @File TO *
7800 OUTPUT 1;CHR$(12)
7810 !

```



```
7820 | EXIT SUBROUTINE STORE_DATA
7830 |
7840 SUBEND!
```

```

7850 SUB Zerbst
7860 !
7870 !*****
7880 ! SUBROUTINE ZERBST DOES ZERBST DATA ANALYSIS OF CAPACITANCE TRANSIENT
7890 !*****
7900 !
7910 ! DECLARATIONS
7920 !
7921 COM /Pulsect_data/ Notes$(30)
7930 COM /Pulsect_data/ Gendate$(11);Pacerate$(1),Digpulse$(4),Doping_type$(1)
7940 COM /Pulsect_data/ INTEGER Setup_flag,Data_flag,Theo_exp,Curve_fit
7950 COM /Pulsect_data/ REAL Capacitance(1000),Readtime(1000)
7960 COM /Pulsect_data/ Function_coef(10),Fit_slope,Fit_intercept
7970 COM /Pulsect_data/ Doping_dens,Thick_oxide,Cins,CO,Cf,Ks,Kin,Ni,Area,Delta
7980 COM /Pulsect_data/ Lifetime,Surface_vel
7990 !
8000 INTEGER Data_points,No_of_functions,Error_flag,Line_fit
8010 REAL Zerx(1000),Zery(1000),Curve_to_fit(1000),Time_tran(1000),F(10)
8020 REAL Sum,Squ.Mean,Var,Yfit
8021 REAL Lifetime_cor,Sur_vel(1000)
8030 !
8040 ! INITIALIZATION
8050 !
8060 IF Curve_fit=1 THEN Line_fit=1
8070 No_of_functions=9
8080 Error_flag=0
8090 OUTPUT 1;CHR$(12)
8100 !
8110 ! SANITY CHECK
8120 !
8130 IF Data_flag=0 THEN
8140 BEEP
8150 OUTPUT 1;"ERROR--NO DATA AVAILABLE TO ANALYZE. MEASUREMENTS MUST BE TAK
EN"
8160 ELSE
8170 OUTPUT 1;"***** DATA ANALYSIS OF PULSED CT DATA *****
*****"
8180 !
8190 ! FIND CAPACITANCE TRANSIENT
8200 !
8210 CALL Find_trans(Zerx(*),Curve_to_fit(*),Time_tran(*),Data_points,Error_
flag)
8220 IF Error_flag=0 THEN
8230 !
8240 ! FIT CURVE IF NOT ALREADY DONE
8250 !
8260 IF Curve_fit=0 THEN
8270 OUTPUT 1;"LEAST SQUARE CURVE FIT BEING PERFORMED"
8280 CALL Least_square(Time_tran(*),Curve_to_fit(*),Data_points,No_of_
functions,Error_flag,Function_coef(*))
8290 !
8300 ! LEAST SQUARE CURVE FIT REPORT
8310 !
8320 OUTPUT 708;CHR$(12)
8330 OUTPUT 708;"FUNCTION COEFFICIANTS AND RESIDUAL VARIENCE FROM CURV
E FIT"
8340 FOR I=1 TO 2
8350 OUTPUT 708;CHR$(10)
8360 NEXT I
8370 !

```

```

8380      ! . OUTPUT DERIVED FUNCTION COEFFICIENTS
8390      !
8400      OUTPUT 708;"COEFFICIENTS:"
8410      FOR I=1 TO No_of_functions
8420          OUTPUT 708;"A";I;"=":Function_coef(I)
8430      NEXT I
8440      !
8450      ! CALCULATE RESIDUAL VARIANCE OF CURVE FIT
8460      !
8470      Sum=0
8480      Squ=0
8490      FOR I=1 TO Data_points
8500          Yfit=0
8510          CALL Functions(Time_tran(I),F(*))
8520          FOR J=1 TO No_of_functions
8530              Yfit=Yfit+F(J)*Function_coef(J)
8540          NEXT J
8550          Diff=Curve_to_fit(I)-Yfit
8560          Squ=Squ+Diff^2
8570          Sum=Sum+Diff
8580      NEXT I
8590      Mean=Sum/Data_points
8600      Var=(1/(Data_points-1))*(Squ-Data_points*Mean^2)
8610      OUTPUT 708;CHR$(10)
8620      OUTPUT 708;"RESIDUAL VARIANCE=";Var
8630      !
8640      ! COMPARE SEVERAL POINTS ALONG CURVE
8650      !
8660      OUTPUT 708;CHR$(10)
8670      OUTPUT 708;CHR$(10)
8680      OUTPUT 708;"COMPARISION OF SEVERAL DATA POINTS WITH FITTED CURVE"
8690      OUTPUT 708;CHR$(10)
8700      OUTPUT 708 USING "K,10X,K,18X,K";"POINT NO.,""DATA POINTS","FITTE
D POINTS"
8710      FOR I=1 TO Data_points STEP INT(Data_points/20)
8720          Yfit=0
8730          CALL Functions(Time_tran(I),F(*))
8740          FOR J=1 TO No_of_functions
8750              Yfit=Yfit+F(J)*Function_coef(J)
8760          NEXT J
8770          OUTPUT 708 USING "3X,DDD,13X,DDDD.DDDD,20X,DDDD.DDDD";I,Curve
_to_fit(I),Yfit
8780      NEXT I
8790      !
8800      ! SET LOGIC FLAGS
8810      !
8820      Line_fit=0
8830      Curve_fit=1
8840      END IF
8850      !
8860      ! EXTRACT Y DATA FOR ZERBST PLOT
8870      !
8880      OUTPUT 1;"Y-AXIS DATA BEING EXTRACTED FOR ZERBST PLOT"
8890      !
8900      FOR I=1 TO Data_points
8910          CALL Deriv(Time_tran(I),F(*))
8920          FOR J=1 TO No_of_functions
8930              Zery(I)=Zery(I)-F(J)*Function_coef(J)
8940          NEXT J
8950      NEXT I

```

```

8960      !
8970      !   GET BEST STRAIGHT LINE FIT FOR ZERBST PLOT
8980      !
8990      IF Line_fit=0 THEN
9000         OUTPUT 1;"STRAIGHT LINE FIT BEING PERFORMED ON ZERBST PLOT"
9010         CALL Line_fit(Zerx(*),Zery(*),Data_points,Fit_slope,Fit_intercept
)
9020      END IF
9030      !
9040      !   CALCULATE LIFETIME AND SURFACE VELOCITY
9050      !
9060      IF Doping_dens<>0 AND Cf<>0 AND Fit_slope<>0 AND Ni<>0 AND Cins<>0 T
HEN
9070         Lifetime=(Ni*Cins)/(Doping_dens*Cf*Fit_slope)
9080         Surface_vel=(Fit_intercept*Doping_dens*Ks*8.85418E-14)/(2*Ni*Cins
*1.E-12)
9081         !
9082         !   CALCULATE CORRECTED VALUE OF LIFETIME (according to D.K.
9083         !   Schroder and H.C. Nathanson SCIENTIFIC PAPER 69-1F6CARTS-P2)
9084         !
9085         Lifetime_cor=1/(1/Lifetime+4*Surface_vel/((Area/PI)^.5/2))
9086         PRINT Lifetime_cor
9087         !
9088         !   CALCULATE SURFACE VELOCITY AS A FUNCTION OF TIME
9089         !
9090         FOR I=1 TO Data_points
9091             Sur_vel(I)=((Doping_dens/(2*Ni))*Zery(I)-(C0/Cf)*(Zerx(I)/Life
time_cor))*((Ks*Thick_oxide)/Kin)
9092         NEXT I
9093         !
9094         !   PLOT SURFACE VELOCITY VS. TIME CURVE
9095         !
9097         CALL Survel_plot(Readtime(*),Sur_vel(*),Data_points)
9098         PAUSE
9099     ELSE
9101         BEEP
9110         OUTPUT 1;"DATA FILE NOT COMPLETE, LIFETIME AND SURFACE VEL CANNOT
BE CALCULATED"
9120     END IF
9130     !
9140     !   CREATE ZERBST PLOT
9150     !
9160     CALL Zerbst_plot(Zerx(*),Zery(*),Data_points)
9170     END IF
9180     OUTPUT 1;CHR$(12)
9190 END IF
9200 !
9210 !   EXIT SUBROUTINE ZERBST
9220 !
9230 SUBEND!

```

```

9240 SUB Find_trans(REAL Zerx(*),Curve_to_fit(*),Time_tran(*),INTEGER Data_poin
ts,Error_flag)
9250 !
9260 !*****
9270 ! SUBROUTINE FIND_TRAN EXTRACT THE RECOVERING CAPACITANCE TRANSIENT
9280 ! FROM THE MEASURED DATA
9290 !*****
9300 !
9310 ! DECLARATION
9320 !
9321 COM /Pulsect_data/ Notes${30}
9330 COM /Pulsect_data/ Gendate${11},Pacerate${1},Dimpulse${4},Doping_type${1}
9340 COM /Pulsect_data/ INTEGER Setup_flag,Data_flag,Theo_exp,Curve_fit
9350 COM /Pulsect_data/ REAL Capacitance(1000),Readtime(1000)
9360 COM /Pulsect_data/ Function_coef(10).Fit_slope,Fit_intercept
9370 COM /Pulsect_data/ Doping_dens,Thick_oxide,Cins,CO,Cf,Ks,Kin,Ni,Area,Delta
9380 COM /Pulsect_data/ Lifetime,Surface_vel
9390 !
9400 INTEGER Done,I,Start,Finish,Index
9410 !
9420 ! FIND INSULATOR AND FINAL CAPACITANCE AND INSULATOR THICKNESS
9430 !
9440 Cins=183.2
9450 Cf=Capacitance(1000)
9460 Thick_oxide=(Kin*8.85418E-14*Area)/(Cins*1.E-12)
9470 !
9480 ! FIND START OF TRANSIENT
9490 !
9500 OUTPUT 1;"CAPACITANCE TRANSIENT BEING EXTRACTED FROM DATA"
9510 !
9520 Done=0
9530 I=1
9540 WHILE Done=0
9550 IF Capacitance(I)<.90*Capacitance(1) THEN
9560 !
9570 ! THROW OUT DOWN TRANSIENT AS EXPERIMENTAL ERROR
9580 !
9590 WHILE Capacitance(I+1)<Capacitance(I)
9600 I=I+1
9610 END WHILE
9620 Done=1
9630 END IF
9640 !
9650 ! INCREMENT COUNTER IF NOT DONE
9660 !
9670 IF Done=0 THEN I=I+1
9680 IF I=1000 THEN
9690 BEEP
9700 OUTPUT 1;"ERROR--NO PULSE TRANSIENT FOUND IN DATA"
9710 Error_flag=1
9720 Done=1
9730 END IF
9740 END WHILE
9750 !
9760 Start=I
9770 !
9780 ! FIND END OF CAPACITANCE TRANSIENT
9790 !
9800 Done=0

```

```

9810 I=Start
9820 IF Error_flag=0 THEN
9830   WHILE Done=0
9840     IF Capacitance(I)>.97*Cf THEN
9850       Done=1
9860     END IF
9870     IF Done=0 THEN I=I+1
9880   END WHILE
9890   !
9900   !   MARK END OF TRANSIENT AND MOVE TRANSIENT POINTS INTO TRAN ARRAYS
9910   !
9920   Finish=I
9930   Data_points=Finish-Start+1
9940   FOR I=Start TO Finish
9950     Index=I-Start+1
9960     Zerx(Index)=(Cf/Capacitance(I)-1)
9970     Curve_to_fit(Index)=(Cins/Capacitance(I))^2
9980     Time_tran(Index)=Readtime(I)-Readtime(Start)
9990   NEXT I
10000 END IF
10010 !
10020 !   EXIT FIND_TRAN SUBROUTINE
10030 !
10040 SUBEND!

```

```

10050 SUB Deriv(X,Deriv(*))
10060 !
10070 !*****
10080 ! SUBROUTINE DERIV CALCULATES THE DERIVATIVE OF THE FUNCS IN SUB FUNCS
10090 !*****
10100 !
10110 !     DECLARATIONS
10120 !
10121 COM /Pulsect_data/ Notes$[30]
10130 COM /Pulsect_data/ Gendate$[11],Pacerate$[1],Dimpulse$[4],Doping_type$[1]
10140 COM /Pulsect_data/ INTEGER Setup_flag,Data_flag,Theo_exp,Curve_fit
10150 COM /Pulsect_data/ REAL Capacitance(1000),Readtime(1000)
10160 COM /Pulsect_data/ Function_coef(10),Fit_slope,Fit_intercept
10170 COM /Pulsect_data/ Doping_dens,Thick_oxide,Cins,CO,Cf,Ks,Kin,Ni,Area,Delta
10180 COM /Pulsect_data/ Lifetime,Surface_vel
10190 !
10200 !     EVALUATE DERIVATIVES
10210 !
10220 Deriv(1)=0
10230 IF X<>0 THEN
10240     Deriv(2)=.125*X*(-.875)
10250     Deriv(3)=.25*X*(-.75)
10260     Deriv(4)=.5*X*(-.5)
10270     Deriv(5)=.75*X*(-.25)
10280 ELSE
10290     Deriv(2)=0
10300     Deriv(3)=0
10310     Deriv(4)=0
10320     Deriv(5)=0
10330 END IF
10340 Deriv(6)=1
10350 Deriv(7)=2*K
10360 Deriv(8)=(5.0*Delta)/(X+.1*Delta)^2
10370 Deriv(9)=(10.0*Delta)/(X+.3*Delta)^2
10380 !
10390 !     EXIT DERIVATIVE EVALUATING SUBROUTINE
10400 !
10410 SUBEND!

```

```

10420 SUB Line_fit(REAL Zerx(*),Zery(*),INTEGER Data_points,REAL Fit_slope,Fit_1
ntercept)
10430 !
10440 !*****
10450 ! SUBROUTINE LINE_FIT FITS A STRAIGHT LINE TO THE MOST LINEAR PART
10460 ! OF THE ZERBST PLOT
10470 !*****
10480 !
10490 !     DECLARATIONS
10500 !
10510 INTEGER Points_to_fit,Jump_interval,I,J
10520 REAL Xj,Yj,Xj2,Xjyj
10530 REAL Test_slope,Test_intercept,Squ,Sum,Yfit,Diff,Mean,Test_var,Low_var
10540 !
10550 !     INITIALIZATION
10560 !
10570 Low_var=1.E+36
10580 Points_to_fit=INT(Data_points/2)
10590 Jump_interval=INT(Data_points/24)
10600 !
10610 !     FORMAT REPORT
10620 !
10630 OUTPUT 708;CHR$(12)
10640 OUTPUT 708;"REPORT FROM LEAST SQUARE LINE FIT TO CURVE"
10650 OUTPUT 708;CHR$(10);CHR$(10);"TEST LINES:"
10660 OUTPUT 708 USING "3X,K,10X,K,10X,K";"SLOPE","INTERCEPT","RESIDUAL VAR"
10670 !
10680 !     SEARCH ALONG CURVE FOR GOOD STRAIGHT LINE FIT
10690 !
10700 FOR I=1 TO Data_points-Points_to_fit STEP Jump_interval
10710 !
10720 !     SUM THE MATRIX ELEMENTS NEEDED FOR A LEAST SQUARE FIT
10730 !
10740 Xj=0
10750 Yj=0
10760 Xj2=0
10770 Xjyj=0
10780 FOR J=I TO I+Points_to_fit
10790 Xj=Xj+Zerx(J)
10800 Yj=Yj+Zery(J)
10810 Xj2=Xj2+Zerx(J)^2
10820 Xjyj=Xjyj+Zerx(J)*Zery(J)
10830 NEXT J
10840 !
10850 !     DETERMINE TEST FIT SLOPE AND FIT INTERCEPT
10860 !
10870 Test_slope=(Yj*Xj-Points_to_fit*Xjyj)/(Xj^2-Points_to_fit*Xj2)
10880 Test_intercept=(Yj*Xj2-Xjyj*Xj)/(Points_to_fit*Xj2-Xj^2)
10890 !
10900 !     FIND RESIDUAL VARIENCE OF FITTED LINE
10910 !
10920 Squ=0
10930 Sum=0
10940 FOR J=I TO I+Points_to_fit
10950 Yfit=Test_slope*Zerx(J)+Test_intercept
10960 Diff=Zery(J)-Yfit
10970 Squ=Squ+Diff^2
10980 Sum=Sum+Diff
10990 NEXT J

```



```

11000 !
11010 Mean=Sum/Points_to_fit
11020 Test_var=(Squ-Points_to_fit*Mean^2)/(Points_to_fit-1)
11030 !
11040 ! OUTPUT PARAMETERS FROM FITTED LINE TO REPORT
11050 !
11060 IF Test_var<1.E+6 THEN
11070 OUTPUT 708 USING "DDDD.DDDD,10X,DDDD.DDDD,8X,DDDDDD.DDDDDD";Test_slo
pe,Test_intercept,Test_var
11080 END IF
11090 !
11100 ! TEST TO SEE IF OPTIMAL STRAIGHT LINE FIT ALONG CURVE
11110 !
11120 IF Test_var<Low_var THEN
11130 Low_var=Test_var
11140 Fit_intercept=Test_intercept
11150 Fit_slope=Test_slope
11160 END IF
11170 !
11180 ! MOVE ON TO NEXT CURVE SEGMENT
11190 !
11200 NEXT I
11210 !
11220 ! REPORT RESULTS OF LINE FIT
11230 !
11240 OUTPUT 708;CHR$(10)
11250 OUTPUT 708 USING "K,DDDD.DDDD":"FITTED SLOPE:";Fit_slope
11260 OUTPUT 708 USING "K,DDDD.DDDD":"FITTED INTER:";Fit_intercept
11270 !
11280 ! EXIT SUBROUTINE LINE_FIT
11290 !
11300 SUBEND!

```

```

11310 SUB Zerbst_plot(REAL Zerx(*),Zery(*),INTEGER Data_points)
11320 !
11330 !*****
11340 ! SUBROUTINE ZERBST PLOT CREATES PLOT FROM EXTRACTED DATA
11350 !*****
11360 !
11370 ! DECLARATIONS
11380 !
11381 COM /Pulsect_data/ Notes$(30)
11390 COM /Pulsect_data/ Gendate$(11),Pacerate$(1),Dimpulse$(4),Doping_type$(1)
11400 COM /Pulsect_data/ INTEGER Setup_flag,Data_flag,Theo_exp,Curve_fit
11410 COM /Pulsect_data/ REAL Capacitance(1000),Readtime(1000)
11420 COM /Pulsect_data/ Function_coef(10),Fit_slope,Fit_intercept
11430 COM /Pulsect_data/ Doping_dens,Thick_oxide,Cins,CO,Cf,Ks,Kin,Ni,Area,Delta
11440 COM /Pulsect_data/ Lifetime,Surface_vel
11450 !
11460 DIM Labels$(30)
11470 INTEGER High_x,High_y
11480 REAL Left,Right,Bottom,Top
11490 !
11500 ! RE-INITIALIZE GRAPHICS DISPLAY
11510 !
11520 DEG
11530 CLIP OFF
11540 PIVOT 0
11550 PEN 1
11560 LINE TYPE 1,5
11570 LORG 1
11580 CSIZE 5,.6
11590 LDIR 0
11600 MOVE 0,0
11610 GCLEAR
11620 !
11630 ! DEFINE GRAPHICS UNITS
11640 !
11650 High_x=INT(Zerx(INT(Data_points/10))+1)
11660 High_y=INT(Zery(INT(Data_points/10))+1)
11670 Left=-.10*High_x
11680 Right=1.1*High_x
11690 Bottom=-.10*High_y
11700 Top=1.1*High_y
11710 WINDOW Left,Right,Bottom,Top
11720 !
11730 ! TITLE GRAPH
11740 !
11750 LORG 6
11760 CSIZE 7,.6
11770 MOVE (Left+Right)/2,Top
11780 LABEL "ZERBST PLOT"
11790 !
11800 ! DATE GRAPH
11810 !
11820 LORG 9
11830 CSIZE 2,.6
11840 MOVE Right,Top
11850 LABEL "GRAPH DATE:"&FNDate$(TIMEDATE)
11860 !
11870 MOVE Right,Top-.02*(Top-Bottom)
11880 LABEL "MEAS. DATE:"&Gendate$
11890 !

```

```

11900 !   CREATE GRAPH KEY
11910 !
11920 LORG 2
11930 CSIZE 3,.6
11940 LDIR 0
11950 !
11960 MOVE Left+.60*(Right-Left),Bottom+.32*(Top-Bottom)
11970 LABEL Notes$
11980 !
11990 MOVE Left+.60*(Right-Left),Bottom+.28*(Top-Bottom)
12000 LABEL Doping_type$&"-type Silicon"
12010 !
12020 OUTPUT Label$ USING "K,DD.DDESZZ,K";"LIFETIME=",Lifetime," sec"
12030 MOVE Left+.60*(Right-Left),Bottom+.24*(Top-Bottom)
12040 LABEL Label$
12050 !
12060 OUTPUT Label$ USING "K,DD.DDESZZ,K";"SURF VEL=",Surface_vel," cm/sec"
12070 MOVE Left+.60*(Right-Left),Bottom+.20*(Top-Bottom)
12080 LABEL Label$
12090 !
12100 !   LABEL AXES
12110 !
12120 LORG 4
12130 LDIR 0
12140 CSIZE 5,.6
12150 MOVE (Left+Right)/2,Bottom
12160 LABEL "Cf/C - 1"
12170 !
12180 LORG 6
12190 LDIR 90
12200 MOVE Left,(Bottom+Top)/2
12210 LABEL "-d/dt([Co/C]^2)"
12220 !
12230 !   NUMBER AXES
12240 !
12250 LORG 6
12260 LDIR 0
12270 CSIZE 3,.6
12280 FOR I=0 TO High_x
12290     MOVE I,0
12300     LABEL I
12310 NEXT I
12320 !
12330 LORG 8
12340 FOR I=0 TO High_y
12350     MOVE 0,I
12360     LABEL I
12370 NEXT I
12380 !
12390 !   DRAW AXES
12400 !
12410 CLIP 0,High_x,0,High_y
12420 AXES 1,1,0,0,2,2
12430 !
12440 !   DRAW ZERBST PLOT
12450 !
12460 FOR I=1 TO Data_points
12470     PLOT Zerx(I),Zery(I)
12480 NEXT I
12490 !
12500 !   DRAW FITTED LINE

```

```
12510 !
12520 PENUM
12530 LINE TYPE 5
12540 FOR X=0 TO High_x STEP High_x
12550     DRAW X,Fit_slope*X+Fit_intercept
12560 NEXT X
12570 !
12580 !   EXIT SUBROUTINE ZERBST PLOT
12590 !
12600 SUBEND!
```

```
12610 SUB Survel_plot(REAL Readtime(*),Surface_vel(*),INTEGER Data_points)
12620 GCLEAR
12630 WINDOW 0,100.0,200
12631 MOVE Readtime(1),Surface_vel(1)
12640 FOR I=1 TO Data_points
12650     DRAW Readtime(I),Surface_vel(I)
12660 NEXT I
12670 SUBEND
```

## APPENDIX F

### Admittance Measurement Data Gathering Program

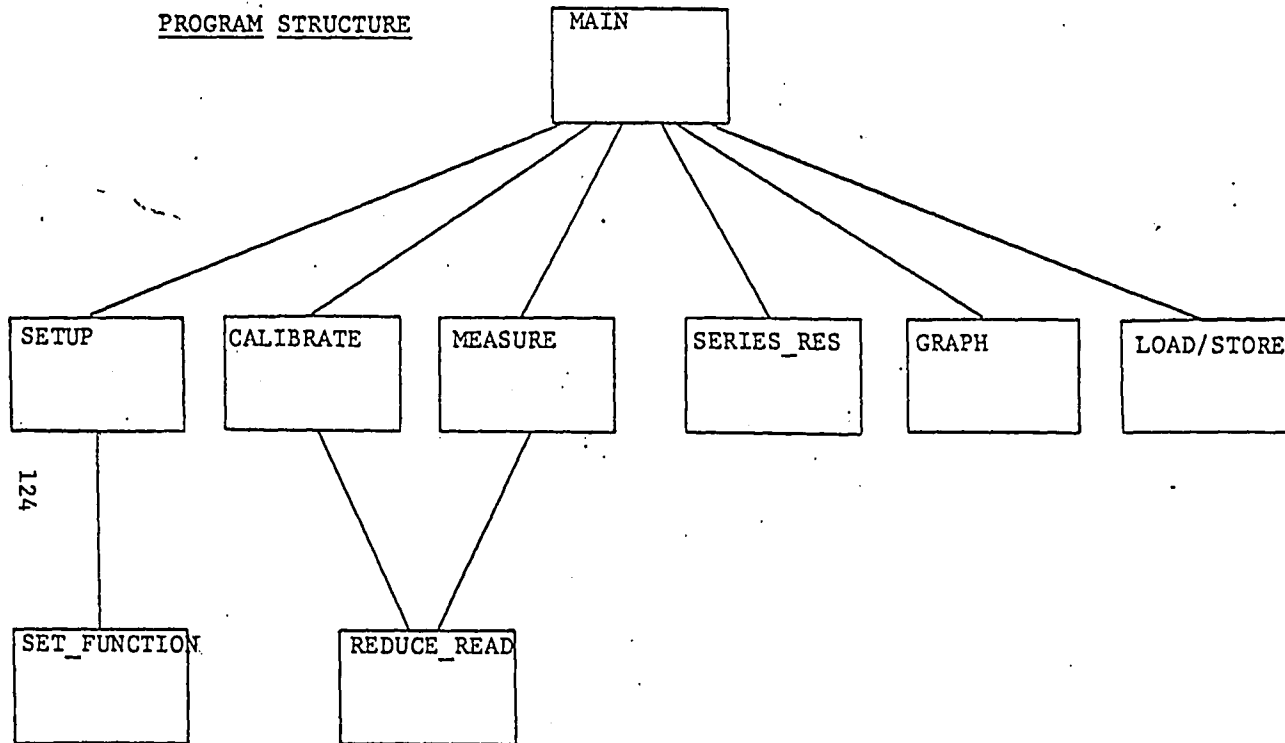
This program was written to gather admittance data from a lock-in amplifier. The program is written in a structured manner so that the program functions are available to the user with use of the software keys. The functions available are setup, calibrate, measure, graph, load and store.

The program uses the function generator, a D/A, and the A/D converter in control and data gathering. The function generator is set to the desired measurement frequency. The program controls the D/A to create the bias sweep across the device. Data is gathered from three channels of the A/D Converter; channel 1 is used to measure conductance, channel 2 capacitance, and channel 4 the bias across the device.

Typically, a user, after setting up the measurement instruments would run the setup phase of the program to enter input data and experimental parameters. At this point a known capacitor would be place in the D.U.T. position and the CALIBRATE subroutine would be run. After calibration the device can be put in place and measurements

taken. When data gathering is complete it can be graphed and stored. Old data files can be retrieved with the LOAD key. An additional processing feature allows the user to correct measured data for series resistance problems by pressing the SER\_RES key.

PROGRAM STRUCTURE





Variable Directory of OOM Block  
/CONDUCT\_DATA/

<u>Variable</u>	<u>Description</u>
NOTES\$ -	(STRING) 30 characters in which user may enter any comments or identifier; set by subroutine SETUP.
GENDATES\$ -	(STRING) string variable containing data of data creation. Set by subroutine MEASURE
DOPING_TYPE\$ -	(STRING) One character user input parameter in subroutine SETUP indicating doping type of device under test.
CALIBRATE_FLAG -	(INTEGER) Switch indicating whether or not subroutine CALIBRATE has been executed in current run.
DATA_FLAG -	(INTEGER) Switch indicating that the data arrays have been filled. Set by subroutine MEASURE.
SETUP_FLAG -	(INTEGER) Switch set to true (1) when program has successfully completed subroutine SETUP.
SER_RES -	(INTEGER) Switch set to true (1) when program has successfully completed subroutine SERIES_RES.
HIGH_VOLT -	(INTEGER) Variable indicating digital counts of D/A converter that highest output voltage corresponds to. Set by subroutine SETUP.
POINTS -	(INTEGER) Variable indicating number of points in data arrays. Set by subroutine MEASURE.
BIAS_VOLT(1000) -	(REAL) Measured data points of set bias voltages

CAPACITANCE(1000) - (REAL) Measured data points of capacitance across device under test.

CONDUCTANCE(1000) - (REAL) Measured data points of conductance across device under test.

CAPAC\_CONST - (REAL) Variable set by subroutine CALIBRATE which is multiplier for digital reading from A/D to obtain capacitance value.

CONDUCT\_CONST - (REAL) Variable set by subroutine CALIBRATE which is multiplier for conductance reading from A/D to obtain conductance value.

CAPAC\_OXIDE - (REAL) Variable set by subroutine SETUP which is the oxide capacitance across D.U.T.

MEAS\_FREQ - (REAL) Variable set by subroutine SETUP which indicates the measurement frequency.

SAMPLE\_CODE\$ - (STRING) Variable set by subroutine SETUP which indicates identifier for D.U.T.

DEV\_AREA - (REAL) User input parameter set by subroutine SETUP indicating the area of the D.U.T.

V\_SOURCE\_BULK - (REAL) User input parameter set by subroutine SETUP indicating the source to bulk voltage in 3 terminal measurements.

TEMPERATURE - (REAL) User input parameter set by subroutine SETUP indicating the temperature of the measurements

Subroutine Directory  
Admittance Measurement Data Gathering Program

SETUP

Function:

- a) set function generator to measurement frequency & amplitude
- b) get experimental parameters from user
  - sweep amplitude
  - source-bulk voltage (3 term meas)
  - temperature
  - sample id
  - device area
  - comments

CALIBRATE

Function:

- a) get multiplication factors on capacitance & conductance scale
- b) get value of standard capacitor
- c) read values on conductance & capacitance scale until conductance is zero and so capacitance reading corresponds to standard cap.

MEASURE

Function:

- a) control bias on device through sweep in 1mV steps
- b) read capacitance & conductance at each bias & store in data array

### SERIES RES

Function:

a) correct data array for series resistance according to formulas given in MOS Physics and Tech /10/ pg. 220

### GRAPH

Function:

a) Find upper & lower limits of data in data array

b) graph conductance & capacitance on same screen

### LOAD/STORE

Function:

a) put data on disk file for later analysis

```

10 !*****
20 ! NICOLLIAN AND GOETZBERGER TYPE CONDUCTANCE MEASUREMENT PROGRAM
30 !*****
40 !
50 !   DECLARATIONS
60 !
70 ! OPTION BASE 1
80 !
90 ! COM /Conduct_data/ Notes$(30)
100 ! COM /Conduct_data/ Gendate$(11),Doping_type$(1)
110 ! COM /Conduct_data/ INTEGER Calibrate_flag,Data_flag,Setup_flag,Ser_res
120 ! COM /Conduct_data/ INTEGER High_volt,Points
130 ! COM /Conduct_data/ REAL Bias_volt(1000),Capacitance(1000),Conductance(1000)
140 ! COM /Conduct_data/ Capac_const,Conduct_const,Capac_oxide,Meas_freq
150 ! COM /Conduct_data/ Sample_code$(10),Dev_area,V_source_bulk,Temperature
160 !
170 ! COM /Config/ @Hpib,@A_to_d,@D_to_a,@Func_gen,@Printer,@Plotter
180 !
190 ! DIM Blanks$(60)
200 ! Blanks$=""
210 !
220 !   ASSIGN I/O PATHS
230 !
240 ! ASSIGN @Hpib TO 7
250 ! ASSIGN @A_to_d TO 706
260 ! ASSIGN @D_to_a TO 707
270 ! ASSIGN @Func_gen TO 716
280 ! ASSIGN @Printer TO 708
290 ! ASSIGN @Plotter TO 705
300 !
310 !   SET UP SOFTWARE KEYS
320 !
330 ! ON KEY 0 LABEL "SETUP" CALL Setup
340 ! ON KEY 1 LABEL "CALIBRATE" CALL Calib
350 ! ON KEY 2 LABEL "MEASURE" CALL Measure
360 ! ON KEY 3 LABEL "GRAPH" CALL Graph
370 ! ON KEY 4 LABEL "ANALYZE" GOSUB Dummy
380 ! ON KEY 5 LABEL "LOAD" CALL Load
390 ! ON KEY 6 LABEL "STORE" CALL Store
400 ! ON KEY 7 LABEL "FREQ FILE" CALL Freq_file
410 ! ON KEY 8 LABEL "REDUCE/SER RES" CALL Reduce
420 ! ON KEY 9 LABEL "EXIT" GOTO Ending
421 ! ON KEY 18 LABEL "SER RES" CALL Series_res
430 !
440 !   SET MACHINE IN IDLE LOOP WAITING FOR INPUT
450 !
460 ! WHILE 1=1
470 !   DISP FNTime$(TIMEDATE)&Blanks$&FNDDate$(TIMEDATE)
480 ! END WHILE
490 !
500 !   DUMMY SUBROUTINE
510 !
520 ! Dummy: !
530 ! RETURN
540 !
550 !   EXIT
560 !
570 ! Ending: !
580 ! END
590 ! SUB Calib

```

```

600 !
610 ! *****
620 ! SUBROUTINE CALIBRATE GETS CALIBRATION CONSTANTS FOR CONVERSION OF
630 ! DIGITAL READINGS FROM CHANNEL 1&2 OF A/D TO CAPAC AND CONDUCT
640 ! *****
650 !
660 ! DECLARATIONS
670 !
680 OPTION BASE 1
690 !
700 COM /Conduct_data/ Notes$(30)
710 COM /Conduct_data/ Gendate$(11),Doping_type$(1)
720 COM /Conduct_data/ INTEGER Calibrate_flag,Data_flag,Setup_flag,Ser_res
730 COM /Conduct_data/ INTEGER High_volt,Points
740 COM /Conduct_data/ REAL Bias_volt(1000),Capacitance(1000),Conductance(1000
)
750 COM /Conduct_data/ Capac_const,Conduct_const,Capac_oxide,Meas_freq
760 COM /Conduct_data/ Sample_code$,Dev_area,V_source_bulk,Temperature
770 !
780 COM /Config/ @HpiB,@A_to_d,@D_to_a,@Func_gen,@Printer,@Plotter
790 !
800 REAL Known_capac,Capac_read,Conduct_read
810 INTEGER Read_cap(10),Read_cond(10),Cond_mult,Cap_mult
820 INTEGER Cap_chan_read
830 !
840 ! CHECK TO SEE IF SET UP COMPLETE
850 !
860 IF Setup_flag=0 THEN
870 OUTPUT 1;CHR$(12);"ERROR -- SETUP PHASE NOT COMPLETED, MUST BE DONE BEF
ORE CALIBRATION"
880 BEEP
890 GOTO Ending
900 END IF
910 !
920 ! SET UP SCREEN
930 !
940 OUTPUT 1;CHR$(12);"***** CALIBRATION PHASE *
*****"
950 OUTPUT 1 USING 960;CHR$(10),CHR$(10),"CHANNEL","R1","R2","R3","R4","R5","R
6","R7","R8","R9","R10","VALUE"
960 IMAGE A,A,7A,5X,2A,4X,2A,4X,2A,4X,2A,4X,2A,4X,2A,4X,2A,4X,2A,4X,2A,3X,3A,5
X,5A
970 !
980 ! GET VALUE OF KNOWN CAPACITOR FROM USER
990 !
1000 INPUT "ENTER VALUE OF KNOWN CAPACITOR IN PICO FARADS:",Known_capac
1010 !
1020 ! GET SCALUE MULTIPLIER IN CONDUCTANCE CHANNEL
1030 !
1040 Cond_mult=0
1050 WHILE (Cond_mult<>1 AND Cond_mult<>10 AND Cond_mult<>100)
1060 INPUT "ENTER MULTIPLICATION FACTOR ON CONDUCTANCE SCALE:",Cond_mult
1070 END WHILE
1080 !
1090 ! GET SCALE MULTIPLIER IN CAPACITANCE CHANNEL
1100 !
1110 Cap_mult=0
1120 WHILE (Cap_mult<>1 AND Cap_mult<>10 AND Cap_mult<>100)
1130 INPUT "ENTER MULTIPLICATION FACTOR ON CAPACITANCE SCALE:",Cap_mult
1140 END WHILE

```

```

1150 !
1160 !   SET UP SOFTWARE KEYS SO USER CAN DEFINE WHEN CONDUCT AND CAPACITANCE
1170 !                               CALIBRATIONS SHOULD TAKE PLACE
1180 !
1190 OFF KEY
1200 ON KEY 0 LABEL "CONDUCTANCE",10 GOSUB Conductance
1210 ON KEY 1 LABEL "CAPACITANCE",9 GOSUB Capacitance
1220 ON KEY 9 LABEL "EXIT",8 GOTO Complete
1230 !
1240 ENABLE
1250 Cap_chan_read=0
1260 !
1270 Idle: !
1280 DISP FNTIME$(TIMEDATE)
1290 GOTO Idle
1300 !
1310 !   CONDUCTANCE CHANNEL READ ROUTINE
1320 !
1330 Conductance: !
1340 !
1350 !   GET 10 CONDUCTANCE READINGS FROM CHANNEL 1
1360 !
1370 FOR I=1 TO 10
1380     OUTPUT @A_to_d USING "4A";"H1AJ"
1390     ENTER @A_to_d USING "#,W";Read_cond(I)
1400     WAIT .2
1410 NEXT I
1420 !
1430 !   REDUCE READINGS TO SINGLE VALUE
1440 !
1450 CALL Reduce_read(Read_cond(*),Conduct_read,10)
1460 !
1470 OUTPUT 1 USING 1480;"CONDUCT:";Read_cond(*);Conduct_read
1480 IMAGE 8A,2X,10(DDDDD,1X),1X,DDDDD.DD
1490 !
1500 RETURN
1510 !
1520 !   CAPACITANCE CALIBRATION SUBROUTINE
1530 !
1540 Capacitance: !
1550 !
1560 !   GET 10 READINGS FROM CHANNEL 2 OF A TO D
1570 !
1580 FOR I=1 TO 10
1590     OUTPUT @A_to_d USING "#,4A";"H2AJ"
1600     ENTER @A_to_d USING "#,W";Read_cap(I)
1610     WAIT .2
1620 NEXT I
1630 !
1640 !   REDUCE READINGS TO SINGLE VALUE
1650 !
1660 CALL Reduce_read(Read_cap(*),Capac_read,10)
1670 !
1680 OUTPUT 1 USING 1690;"CAPAC:";Read_cap(*);Capac_read
1690 IMAGE 6A,4X,10(DDDDD,1X),1X,DDDDD.DD
1700 !
1710 RETURN
1720 !
1730 Complete: !
1740 !
1750 !   GET CAPACITANCE CALIBRATION CONSTANT

```

```

1760 !
1770 IF Capac_read<>0 THEN
1780   Capac_const=Known_capac/Capac_read
1790   Conduct_const=Capac_const*Cap_mult/Cond_mult
1800   Calibrate_flag=1
1801   OUTPUT 1;CHR$(12)
1810 ELSE
1820   OUTPUT 1;"NO CAPACITANCE VALUE READ, CALIBRATION NOT COMPLETED"
1830 END IF
1840 !
1850 Ending: !
1860 SUBEND
1870 SUB Reduce_read(INTEGER Readings(*),REAL Read_value,INTEGER No_of_read)
1880 !*****
1890 ! SUBROUTINE TAKES GIVEN READINGS THROWS OUT HIGH AND LOW AND AVERAGES
1900 ! THE REMAINING TO GET VALUE OF READ
1910 !*****
1920 !
1930 !   DECLARATIONS
1940 !
1950 REAL Low_read,High_read,Sum_of_reads
1960 INTEGER Low_spot,High_spot
1970 !
1980 !   FIND LOW READING
1990 !
2000 Low_read=Readings(1)
2010 Low_spot=1
2020 !
2030 FOR I=1 TO No_of_read
2040   IF Readings(I)<Low_read THEN
2050     Low_read=Readings(I)
2060     Low_spot=I
2070   END IF
2080 NEXT I
2090 !
2100 !   FIND HIGH READING
2110 !
2120 High_read=Readings(No_of_read)
2130 High_spot=No_of_read
2140 !
2150 FOR I=1 TO No_of_read
2160   IF Readings(I)>High_read AND I<>Low_spot THEN
2170     High_read=Readings(I)
2180     High_spot=I
2190   END IF
2200 NEXT I
2210 !
2220 !   SUM ALL READINGS EXCEPT LOW AND HIGH
2230 !
2240 Sum_of_reads=0
2250 FOR I=1 TO No_of_read
2260   IF I<>Low_spot AND I<>High_spot THEN
2270     Sum_of_reads=Sum_of_reads+Readings(I)
2280   END IF
2290 NEXT I
2300 !
2310 !   FIND AVERAGE VALUE FROM SUM
2320 !
2330 Read_value=Sum_of_reads/(No_of_read-2)
2340 !

```



```

2350 ! EXIT
2360 !
2370 SUBEND
2380 DEF FNTime$(Now) ! GIVEN 'SECONDS' RETURN 'HH:MM:SS'
2390 !
2400 Now=INT(Now) MOD 86400
2410 H=Now DIV 3600
2420 M=Now MOD 3600 DIV 60
2430 S=Now MOD 60
2440 OUTPUT T$ USING "#,ZZ,K";H,":",M,":",S
2450 RETURN T$
2460 FNEND
2470 !
2480 DEF FNTime(T$) ! GIVEN 'HH:MM:SS' RETURN 'SECONDS'
2490 !
2500 ON ERROR GOTO Err
2510 ENTER T$;H,M,S
2520 RETURN (3600*H+60*M+S) MOD 86400
2530 Err:OFF ERROR
2540 RETURN TIMEDATE MOD 86400
2550 FNEND
2560 DEF FNDate$(Seconds) !GIVEN 'SECONDS' RETURN "DD MMM YYYY"
2570 !
2580 DATA JAN,FEB,MAR,APR,MAY,JUN,JUL,AUG,SEP,OCT,NOV,DEC
2590 DIM Month$(1:12)[3]
2600 READ Month$(*)
2610 !
2620 Julian=Seconds DIV 86400-1721119
2630 Year=(4*Julian-1) DIV 146097
2640 Julian=(4*Julian-1) MOD 146097
2650 Day=Julian DIV 4
2660 Julian=(4*Day+3) DIV 1461
2670 Day=(4*Day+3) MOD 1461
2680 Day=(Day+4) DIV 4
2690 Month=(5*Day-3) DIV 153
2700 Day=(5*Day-3) MOD 153
2710 Day=(Day+5) DIV 5
2720 Year=100*Year+Julian
2730 IF Month<10 THEN
2740 Month=Month+3
2750 ELSE
2760 Month=Month-9
2770 Year=Year+1
2780 END IF
2790 OUTPUT D$ USING "#,ZZ.X,3A.X,4Z";Day,Month$(Month),Year
2800 RETURN D$
2810 FNEND
2820 !
2830 DEF FNDate(Dmy$) ! GEVEN 'DD MMM YYYY' RETURN 'SECONDS'
2840 !
2850 DATA JAN,FEB,MAR,APR,MAY,JUN,JUL,AUG,SEP,OCT,NOV,DEC
2860 DIM Month$(1:12)[3]
2870 READ Month$(*)
2880 !
2890 ON ERROR GOTO Err
2900 I$=Dmy$&" "
2910 ENTER I$ USING "DD,4A,5D";Day,M$,Year
2920 IF Year<100 THEN Year=Year+1900
2930 FOR I=1 TO 12
2940 IF POS(M$,Month$(I)) THEN Month=I
2950 NEXT I

```

```

2960     IF Month=0 THEN Err
2970     IF Month>2 THEN
2980         Month=Month-3
2990     ELSE
3000         Month=Month+9
3010         Year=Year-1
3020     END IF
3030     Century=Year DIV 100
3040     Remainder=Year MOD 100
3050     Julian=146097*Century DIV 4+1461*Remainder DIV 4+(153*Month+2) DIV 5+Day
+1721119
3060     Julian=Julian*86400
3070     IF Julian<2.08662912E+11 OR Julian>=2.143252224E+11 THEN Err
3080     RETURN Julian      ! RETURN JULIAN DATE IN SECONDS
3090 Err:   OFF ERROR
3100     RETURN TIMEDATE    ! RETURN CURRENT DATE
3110     FNEND
3120     SUB Setup
3130     !*****
3140     !   SUBROUTINE SETUP GET EXPERIMENTAL PARAMETER FROM USER TO PERFORM
3150     !   CONDUCTANCE MEASUREMENTS
3160     !*****
3170     !
3180     !   DECLARATIONS
3190     !
3200     OPTION BASE 1
3210     !
3220     COM /Conduct_data/ Notes$[30]
3230     COM /Conduct_data/ Gendate$[11],Doping_type$[1]
3240     COM /Conduct_data/ INTEGER Calibrate_flag,Data_flag,Setup_flag,Ser_res
3250     COM /Conduct_data/ INTEGER High_volt,Points
3260     COM /Conduct_data/ REAL Bias_volt(1000),Capacitance(1000),Conductance(1000
)
3270     COM /Conduct_data/ Capac_const,Conduct_const,Capac_oxide,Meas_freq
3280     COM /Conduct_data/ Sample_code$,Dev_area,V_source_bulk,Temperature
3290     !
3300     COM /Config/ @Hpib,@A_to_d,@D_to_a,@Func_gen,@Printer,@Plotter
3310     !
3320     INTEGER Voltage_sweep
3330     !
3340     !   SET FUNCTION GENERATOR
3350     !
3360     OUTPUT 1;CHR$(12);"*****          SET FUNCTION GENERATOR      *****
*****"
3370     CALL Set_func_gen
3380     !
3390     !   GET EXPERIMENTAL PARAMETERS FROM USER
3400     !
3410     OUTPUT 1;CHR$(12);"*****          ENTER EXPERIMENTAL PARAMETERS      ****
*****"
3420     !
3430     Voltage_sweep=0
3440     WHILE (Voltage_sweep<1 OR Voltage_sweep>10)
3450         INPUT "ENTER NUMBER OF VOLTS TO BE SWEEP (SET START VOLT MANUALLY):",Vo
ltage_sweep
3460     END WHILE
3470     !
3480     High_volt=Voltage_sweep*100
3481     !
3482     !

```

```

3483 INPUT "ENTER SOURCE TO BULK VOLTAGE IN VOLT:",V_source_bulk
3484 !
3485 INPUT "ENTER TEMPERATURE IN DEG KELVIN:",Temperature
3490 !
3500 !   GET DEVICE PARAMETERS FROM USER
3510 !
3520 OUTPUT 1;CHR$(12);"*****   ENTER DEVICE PARAMETERS & COMMENTS   *
*****"
3530 !
3540 Doping_type$=""
3550 WHILE (Doping_type$<>"N" AND Doping_type$<>"P")
3560   INPUT "ENTER DOPING TYPE OF DEVICE (N OR P):",Doping_type$
3570 END WHILE
3580 !
3581 !
3582 INPUT "ENTER SAMPLE IDENTIFICATION CODE:",Sample_codes$
3583 !
3584 INPUT "ENTER DEVICE AREA IN CM^2:",Dev_area
3585 !
3590 INPUT "ENTER COMMENTS:",Notes$
3600 !
3610 !   EXIT SUBROUTINE SETUP
3620 !
3630 OUTPUT 1;CHR$(12)
3640 Setup_flag=1
3650 SUBEND
3660 SUB Set_func_gen
3670 !
3680 !*****
3690 !   SUBROUTINE TO SET FUNCTION GENERATOR TO APPLY SIGNAL TO DEVICE
3700 !*****
3710 !
3720 !   DECLARATIONS
3730 !
3731 OPTION BASE 1
3732 !
3733 COM /Conduct_data/ Notes$(30)
3734 COM /Conduct_data/ Gendate$(11),Doping_type$(1)
3735 COM /Conduct_data/ INTEGER Calibrate_flag,Data_flag,Setup_flag,Ser_res
3736 COM /Conduct_data/ INTEGER High_volt,Points
3737 COM /Conduct_data/ REAL Bias_volt(1000),Capacitance(1000),Conductance(1000
)
3738 COM /Conduct_data/ Capac_const,Conduct_const,Capac_oxide,Meas_freq
3739 COM /Conduct_data/ Sample_codes$,Dev_area,V_source_bulk,Temperature
3740 !
3742 COM /Config/ @Hpib,@A_to_d,@D_to_a,@Func_gen,@Printer,@Plotter
3750 !
3760 REAL Frequency,Device_voltage,Set_voltage
3770 DIM Func_gen_com$(100),Error_message$(20)
3780 !
3790 !   SETUP SERVICE ROUTINE FOR FUNCTION GENERATOR IF SERVICE REQUEST RAISED
3800 !
3810 ON INTR 7,10 GOSUB Serv_rout
3820 ENABLE INTR 7;2
3830 !
3840 !   INPUT SIGNAL FREQUENCY
3850 !
3860 Get_func: !
3870 INPUT "ENTER SIGNAL FREQUENCY IN HERTZ",Frequency
3871 Meas_freq=Frequency
3880 !

```

```

3890 ! INPUT SIGNAL AMPLITUDE THAT IS APPLIED TO DEVICE (.01X GEN SIGNAL)
3900 !
3910 INPUT "ENTER SIGNAL AMPLITUDE IN MV (AS APPLIED TO DEVICE)",Device_voltage
3920 Set_voltage=Device_voltage*1.0E-3*1.0E+2/2
3930 !
3940 ! SET-UP COMMAND LINE FOR FUNCTION GENERATOR
3950 !
3960 OUTPUT Func_gen_com$ USING "K,K,K,K,K";"M1,CT0,T0,H0,W1,FRQ ",Frequency,"
HZ,AMP ",Set_voltage," V,DFS,OV,LO,CO,DO,A0"
3970 !
3980 ! SEND COMMAND LINE TO FUNCTION GENERATOR
3990 !
4000 Done=1
4010 !
4020 REMOTE @Func_gen
4030 OUTPUT @Func_gen USING "K";Func_gen_com$
4040 !
4050 IF Done=1 THEN
4060 SUBEXIT
4070 ELSE
4080 GOTO Get_func
4090 END IF
4100 !
4110 ! SERVICE ROUTINE FOR SERVICE REQUEST FROM FUNCTION GEN
4120 !
4130 Serv_rout: !
4140 OUTPUT @Func_gen USING "K";"IERR"
4150 ENTER @Func_gen USING "K";Error_message$
4160 A=SPOLL(@Func_gen)
4170 OUTPUT 1;"ERROR RECIEVED FROM FUNCTION GENERATOR:";Error_message$;" ";A
4180 ENABLE INTR 7;2
4190 Done=0
4200 RETURN
4210 !
4220 ! EXIT
4230 !
4240 Ending: !
4250 SUBEND
4260 SUB Measure
4270 !*****
4280 ! SUBROUTINE MEASURE TAKE CAPACITANCE AND CONDUCTANCE READINGS AT
4290 ! DIFFERENT BIASES
4300 !*****
4310 !
4320 ! DECLARATIONS
4330 !
4340 OPTION BASE 1
4350 !
4360 COM /Conduct_data/ Notes$(30)
4370 COM /Conduct_data/ Gendate$(11),Doping_type$(1)
4380 COM /Conduct_data/ INTEGER Calibrate_flag,Data_flag,Setup_flag,Ser_res
4390 COM /Conduct_data/ INTEGER High_volt,Points
4400 COM /Conduct_data/ REAL Bias_volt(1000),Capacitance(1000),Conductance(1000
)
4410 COM /Conduct_data/ Capac_const,Conduct_const,Capac_oxide,Meas_freq
4420 COM /Conduct_data/ Sample_code$,Dev_area,V_source_bulk,Temperature
4430 !
4440 COM /Config/ @Hpib,@A_to_d,@D_to_a,@Func_gen,@Printer,@Plotter
4450 !
4460 INTEGER Read_volt(50),Read_cap(50),Read_cond(50)
4470 REAL Dig_volt,Dig_cap,Dig_cond

```

```

4480 !
4490 ! CHECK TO SEE IF CALIBRATION COMPLETE
4500 !
4510 IF Calibrate_flag=0 THEN
4520 BEEP
4530 OUTPUT 1;CHR$(12);"ERROR -- EXPERIMENT NOT CALIBRATED, MEASUREMENTS CAN
NOT BE PERFORMED"
4540 ELSE
4550 !
4560 ! PERFORM MEASUREMENTS
4570 !
4580 OUTPUT 1;CHR$(12);"***** MEASUREMENT PHASE *****
*****"
4590 Points=0
4600 !
4610 FOR Bias=0 TO High_volt
4620 !
4630 ! SET BIAS VOLTAGE
4640 !
4650 OUTPUT @D_to_a USING "ZZZZ";Bias+2000
4651 WAIT .3
4660 !
4670 ! READ BIAS VOLTAGE
4680 !
4690 FOR I=1 TO 8
4691 WAIT .01
4700 OUTPUT @A_to_d USING "#,4A";"H8AJ"
4710 ENTER @A_to_d USING "#,W";Read_volt(I)
4720 NEXT I
4730 !
4740 Dig_volt1=.02*Read_volt(1)+.10*Read_volt(2)+.16*Read_volt(3)+.23*Read_v
olt(4)
4741 Dig_volt2=.23*Read_volt(5)+.16*Read_volt(6)+.10*Read_volt(7)+.02*Read_v
olt(8)
4742 Dig_volt=Dig_volt1+Dig_volt2
4750 !
4760 ! READ CONDUCTANCE
4770 !
4780 FOR I=1 TO 8
4781 WAIT .01
4790 OUTPUT @A_to_d USING "#,4A";"H1AJ"
4800 ENTER @A_to_d USING "#,W";Read_cond(I)
4810 NEXT I
4820 !
4830 Dig_cond1=.02*Read_cond(1)+.10*Read_cond(2)+.16*Read_cond(3)+.23*Read_c
ond(4)
4831 Dig_cond2=.23*Read_cond(5)+.16*Read_cond(6)+.10*Read_cond(7)+.02*Read_c
ond(8)
4832 Dig_cond=Dig_cond1+Dig_cond2
4840 !
4850 ! READ CAPACITANCE
4860 !
4870 FOR I=1 TO 8
4871 WAIT .01
4880 OUTPUT @A_to_d USING "#,4A";"H2AJ"
4890 ENTER @A_to_d USING "#,W";Read_cap(I)
4900 NEXT I
4910 !
4920 Dig_cap1=.02*Read_cap(1)+.10*Read_cap(2)+.16*Read_cap(3)+.23*Read_cap(4
)
4921 Dig_cap2=.02*Read_cap(8)+.10*Read_cap(7)+.16*Read_cap(6)+.23*Read_cap(5

```

```

)
4922     Dig_cap=Dig_cap1+Dig_cap2
4930     !
4940     !   ENTER POINT INTO DATA FILE
4950     !
4960     Points=Points+1
4970     Bias_volt(Points)=Dig_volt/100
4980     Capacitance(Points)=Dig_cap*Capac_const
4990     Conductance(Points)=Dig_cond*Conduct_const
5000     !
5010     !   MOVE TO NEXT BIAS
5030     NEXT Bias
5031     !
5032     !   EXTRACT OXIDE CAPACITANCE
5033     !
5034     Capac_oxide=FNMax(Capacitance(*),Points)
5040     !
5050     !   END OF MEASUREMENTS
5060     !
5070     OUTPUT @D_to_a USING "ZZZ":2000
5080     OUTPUT 1;CHR$(12)
5081     BEEP
5082     BEEP
5090     END IF
5100     !
5110     !   EXIT MEASUREMENT SUBROUTINE
5120     !
5130     SUBEND
5140     SUB Store
5150     !*****
5160     !       SUBROUTINE "STORE" CREATES A DATA FILE AND STORES THE RELEVANT
5170     !                               DATA IN IT
5180     !*****
5190     !
5200     !       DECLARATIONS
5210     !
5220     OPTION BASE 1
5230     COM /Conduct_data/ Notes$(30)
5240     COM /Conduct_data/ Gendate$(11),Doping_type$(1)
5250     COM /Conduct_data/ INTEGER Calibrate_flag,Data_flag,Setup_flag,Ser_res
5260     COM /Conduct_data/ INTEGER High_volt,Points
5270     COM /Conduct_data/ REAL Bias_volt(1000),Capacitance(1000),Conductance(1000)
)
5280     COM /Conduct_data/ Capac_const,Conduct_const,Capac_oxide,Meas_freq
5290     COM /Conduct_data/ Sample_code$,Dev_area,V_source_bulk,Temperature
5300     !
5310     DIM Answer$(1),Data_file$(10),File_specifier$(30)
5320     !
5330     !   DEFINE PROGRAM STATE TO USER
5340     !
5350     OUTPUT 1;CHR$(12);"***** STORAGE OF INTERNAL DATA FILE DISK *****"
5380     !
5390     !   GET DATA FILE NAME AND LOCATION FROM USER
5400     !
5450     INPUT "ENTER DATA FILENAME:",Data_file$
5460     INPUT "SPECIFY LEFT OR RIGHT HAND DRIVE",Answer$
5470     IF Answer$="L" THEN
5480         File_specifier$=Data_file$&":INTERNAL,4,1"
5490     ELSE
5490         File_specifier$=Data_file$&":INTERNAL,4,0"
5500

```

```

5510 END IF
5520 !
5530 ! CREATE THE FILE AND STORE
5540 !
5550 CREATE BDAT File_specifier$,6,4096
5560 ASSIGN @Path1 TO File_specifier$;FORMAT OFF
5570 !
5580 !
5590 OUTPUT @Path1;Notes$
5600 OUTPUT @Path1;Gendate$,Doping_type$
5610 OUTPUT @Path1;High_volt,Points
5620 OUTPUT @Path1;Bias_volt(*),Capacitance(*),Conductance(*)
5630 OUTPUT @Path1;Capac_const,Conduct_const,Capac_oxide,Meas_freq
5640 OUTPUT @Path1;Sample_code$,Dev_area,V_source_bulk
5650 OUTPUT @Path1;Temperature
5660 !
5670 ! CLOSE I/O PATH AND EXIT
5680 !
5681 OUTPUT 1;CHR$(12)
5690 ASSIGN @Path1 TO *
5700 !
5710 SUBEND
5720 !
5730 SUB Load
5740 !*****
5750 ! SUBROUTINE "LOAD" RETRIEVES A DATA FILE FROM THE DISK
5760 !*****
5770 !
5780 ! DECLARATIONS
5790 !
5800 OPTION BASE 1
5810 !
5820 COM /Conduct_data/ Notes${30}
5830 COM /Conduct_data/ Gendate${11},Doping_type${1}
5840 COM /Conduct_data/ INTEGER Calibrate_flag,Data_flag,Setup_flag,Ser_res
5850 COM /Conduct_data/ INTEGER High_volt,Points
5860 COM /Conduct_data/ REAL Bias_volt(1000),Capacitance(1000),Conductance(1000
)
5870 COM /Conduct_data/ Capac_const,Conduct_const,Capac_oxide,Meas_freq
5880 COM /Conduct_data/ Sample_code$,Dev_area,V_source_bulk,Temperature
5890 !
5900 DIM Answer${1},File_specifier${30},Data_file${10}
5910 !
5920 ! DEFINE PROGRAM STATE TO USER
5930 !
5940 OUTPUT 1;CHR$(12);"***** LOAD OF INTERNAL FILE FROM DISK *****
*****"
5950 !
5960 ! GET FILE NAME AND LOCATION
5970 !
5980 INPUT "ENTER THE FILENAME:",Data_file$
5990 INPUT "SPECIFY LEFT OR RIGHT HAND DRIVE(L OR R):",Answer$
6000 IF Answer$="L" THEN
6010 File_specifier$=Data_file$&":INTERNAL,4,1"
6020 ELSE
6030 File_specifier$=Data_file$&":INTERNAL,4,0"
6040 END IF
6050 !
6060 ! LOAD THE DATA FILE
6070 !
6080 ASSIGN @Path2 TO File_specifier$;FORMAT OFF

```

```

6090 !
6100 !
6110 ENTER @Path2;Notes$
6120 ENTER @Path2;Gendate$,Doping_type$
6130 ENTER @Path2;High_volt,Points
6140 ENTER @Path2;Bias_volt(*),Capacitance(*),Conductance(*)
6150 ENTER @Path2;Capac_const,Conduct_const,Capac_oxide,Meas_freq
6160 ENTER @Path2;Sample_code$,Dev_area,V_source_bulk
6170 ENTER @Path2;Temperature
6171 !
6172 !   SET PROGRAM STATE FLAGS
6173 !
6174 Calibrate_flag=0
6175 Setup_flag=0
6176 Data_flag=1
6177 Ser_res=0
6180 !
6190 !   CLOSE I/O PATH AND EXIT
6200 !
6201 OUTPUT 1;CHR$(12)
6210 ASSIGN @Path2 TO *
6220 !
6230 SUBEND
6240 !
6250 SUB Graph
6260 !*****
6270 !       SUBROUTINE GRAPH PLOTS TO C-V CURVES AND THE G-V CURVES
6280 !*****
6290 !
6300 !   DECLARATIONS
6310 !
6320 OPTION BASE 1
6330 !
6340 COM /Conduct_data/ Notes${30}
6350 COM /Conduct_data/ Gendate${11},Doping_type${1}
6360 COM /Conduct_data/ INTEGER Calibrate_flag,Data_flag,Setup_flag,Ser_res
6370 COM /Conduct_data/ INTEGER High_volt,Points
6380 COM /Conduct_data/ REAL Bias_volt(1000),Capacitance(1000),Conductance(1000
)
6390 COM /Conduct_data/ Capac_const,Conduct_const,Capac_oxide,Meas_freq
6400 COM /Conduct_data/ Sample_code${10},Dev_area,V_source_bulk,Temperature
6410 !
6420 COM /Config/ @HpiB,@A_to_d,@D_to_a,@Func_gen,@Printer,@Plotter
6430 !
6440 COM /Graphics/ INTEGER Axes_drawn
6450 COM /Graphics/ Left,Right,Top_cap,Bottom_cap,Top_cond,Bottom_cond
6460 COM /Graphics/ High_cap,Low_cap,High_cond,Low_cond,Low_voltage,High_voltag
e
6470 COM /Graphics/ INTEGER Cond_range,Cap_range
6480 !
6490 DIM Answer${3}
6500 !
6510 !   RE-INITIALIZE GRAPHICS DISPLAY
6520 !
6530 DEG
6540 CLIP OFF
6550 PIVOT 0
6560 PEN 1
6570 LINE TYPE 1,5
6580 LORG 1

```



```

6590 CSIZE 5,.6
6600 LDIR 0
6610 MOVE 0,0
6620 !
6630 IF Axes_drawn=1 THEN
6640     INPUT "SHOULD DATA BE PLOTTED ON SAME AXES(YES OR NO)?",Answer$
6650 END IF
6660 !
6670 ! SET FLAG TO SEE WHETHER TO DRAW AXES
6680 !
6690 Init=((Axes_drawn=1 AND Answer$="NO") OR Axes_drawn=0)
6700 IF Init THEN
6710     GCLEAR
6720     !
6730     ! DEFINE GRAPHING LIMITS BY FINDING MAX'S AND MINS OF PARMS
6740     !
6750     High_cap=FNMax(Capacitance(*),Points)
6760     Low_cap=FNMin(Capacitance(*),Points)
6770     High_cond=FNMax(Conductance(*),Points)
6780     Low_cond=FNMin(Conductance(*),Points)
6790     !
6800     ! RE-DEFINE HIGH CAP AND COND ACCORDING TO GRAPHING LIMITS
6810     !
6820     Cond_range=-28
6830     WHILE (10^(Cond_range+1)<High_cond-Low_cond)
6840         Cond_range=Cond_range+1
6850     END WHILE
6860     !
6870     Cap_range=-28
6880     WHILE (10^(Cap_range+1)<High_cap-Low_cap)
6890         Cap_range=Cap_range+1
6900     END WHILE
6910     !
6920     !
6930     High_cap=INT(High_cap/10^Cap_range+1)*10^Cap_range
6940     Low_cap=INT(Low_cap/10^Cap_range)*10^Cap_range
6950     High_cond=INT(High_cond/10^Cond_range+1)*10^Cond_range
6960     Low_cond=INT(Low_cond/10^Cond_range)*10^Cond_range
6970     Low_voltage=INT(Bias_volt(Points))
6980     High_voltage=INT(Bias_volt(1)+1)
6990     !
7000     ! DEFINE GRAPHING LIMITS
7010     !
7020     Bottom_cap=-.1*(ABS(High_cap-Low_cap))+Low_cap
7030     Top_cap=1.1*(ABS(High_cap-Low_cap))+Low_cap
7040     Bottom_cond=-.1*(ABS(High_cond-Low_cond))+Low_cond
7050     Top_cond=1.1*(ABS(High_cond-Low_cond))+Low_cond
7060     Left=-.1*(ABS(High_voltage-Low_voltage))+Low_voltage
7070     Right=1.1*(ABS(High_voltage-Low_voltage))+Low_voltage
7080     !
7090     Axes_drawn=1
7100 END IF
7110 !
7120 ! SET UP GRAPHICS DISPLAY FOR CONDUCTANCE CURVES
7130 !
7140 WINDOW Left,Right,Bottom_cond,Top_cond
7150 !
7160 ! DRAW TITLE AND AXES IF INITIAL
7170 !
7180 IF Init THEN
7190     !

```

```

7200      !   TITLE GRAPH
7210      !
7220      CSIZE 6,.6
7230      MOVE (Left+Right)/2,Top_cond
7240      LORG 6
7250      LABEL "COND. AND CAP. VS VOLTAGE"
7260      !
7270      !   LABEL AXES
7280      !
7290      LDIR 90
7300      CSIZE 4,.6
7310      MOVE Left,(Bottom_cond+Top_cond)/2
7320      LORG 6
7330      LABEL "G/w (PF)"
7340      !
7350      LDIR 0
7360      MOVE (Left+Right)/2,Bottom_cond
7370      LORG 4
7380      LABEL "VOLTAGE"
7390      !
7400      CSIZE 3,.6
7410      LORG 8
7420      FOR I=Low_cond TO High_cond STEP 10^Cond_range
7430          MOVE Low_voltage,I
7440          LABEL I
7450      NEXT I
7460      !
7470      LORG 6
7480      FOR I=Low_voltage TO High_voltage
7490          MOVE I,Low_cond
7500          LABEL I
7510      NEXT I
7520      END IF
7530      !
7540      CLIP Low_voltage,High_voltage,Low_cond,High_cond
7550      IF Init THEN
7560          AXES 1,10^Cond_range,Low_voltage,Low_cond
7570      END IF
7580      !
7590      PENUP
7600      FOR I=1 TO Points
7610          PLOT Bias_volt(I),Conductance(I)
7620      NEXT I
7630      !
7640      CLIP OFF
7650      !
7660      !   MOVE TO CAPACITANCE GRAPH
7670      !
7680      WINDOW Left,Right,Bottom_cap,Top_cap
7690      !
7700      IF Init THEN
7710          !
7720          !   LABEL AXES
7730          !
7740          LDIR 90
7750          LORG 4
7760          CSIZE 4,.6
7770          MOVE Right,(Bottom_cap+Top_cap)/2
7780          LABEL "CAPACITANCE(PF)"
7790          !

```

```

7800     LDIR 0
7810     LORG 2
7820     CSIZE 3,.6
7830     FOR I=Low_cap TO High_cap STEP 10^Cap_range
7840         MOVE High_voltage,I
7850         LABEL I
7860     NEXT I
7870     !
7880 END IF
7890     !
7900 CLIP Low_voltage,High_voltage,Low_cap,High_cap
7910 IF Init THEN
7920     AXES 1,10^Cap_range,High_voltage,Low_cap
7930 END IF
7940     !
7950 PENUP
7960 FOR I=1 TO Points
7970     PLOT Bias_volt(I),Capacitance(I)
7980 NEXT I
7990     !
8000 CLIP OFF
8010     !
8020     !   EXIT
8030     !
8040 SUBEND
8050 DEF FNMax(REAL Array(*),INTEGER Elements)
8060 !*****
8070 !   SUBROUTINE FIND THE MAXIMUM VALUE OF AN ARRAY OF REAL NUMBERS
8080 !*****
8090     !
8100     !   DECLARATION
8110     !
8120 REAL Maximum
8130     !
8140 Maximum=1.E-99
8150 FOR I=1 TO Elements
8160     IF Array(I)>Maximum THEN Maximum=Array(I)
8170 NEXT I
8180     !
8190 RETURN Maximum
8200 FNEND
8210 DEF FNMin(REAL Array(*),INTEGER Elements)
8220 !*****
8230 !   SUBROUTINE FINDS THE MINIMUM VALUE OF AN ARRAY OF REAL NUMBERS
8240 !*****
8250     !
8260     !   DECLARATIONS
8270     !
8280 REAL Minimum
8290 Minimum=1.E+99
8300     !
8310 FOR I=1 TO Elements
8320     IF Array(I)<Minimum THEN Minimum=Array(I)
8330 NEXT I
8340     !
8350 RETURN Minimum
8360 FNEND
8370 SUB Freq_file
8380 !*****
8390 !   THIS SUBROUTINE ADDS A DATA POINT TO A CONDUCTANCE VS. FREQUENCY
8400 !   DATA FILE ON DISK

```

```

8410 !*****
8420 !
8430 !   DECLARATIONS
8440 !
8450 OPTION BASE 1
8460 !
8470 COM /Cond_freq_data/ Bias_voltage,Sample_id$(10),Temp,Dop_type$(1)
8480 COM /Cond_freq_data/ Pnts,Meas_fr(50),Conduct(50),Capac(50)
8490 !
8500 COM /Conduct_data/ Notes$(30)
8510 COM /Conduct_data/ Gendate$(11),Doping_type$(1)
8520 COM /Conduct_data/ INTEGER Calibrate_flag,Data_flag,Setup_flag,Ser_res
8530 COM /Conduct_data/ INTEGER High_volt,Points
8540 COM /Conduct_data/ REAL Bias_volt(1000),Capacitance(1000),Conductance(1000)
)
8550 COM /Conduct_data/ Capac_const,Conduct_const,Capac_oxide,Meas_freq
8560 COM /Conduct_data/ Sample_code$(10),Dev_area,V_source_bulk,Temperature
8570 !
8580 DIM Answer$(3),File_name$(10),File_specifier$(30)
8590 !
8600 INTEGER Data_point,Data_compatible,Count,Inc,Slot
8610 !
8620 !   DEFINE PROGRAM STATE TO USER
8630 !
8640 OUTPUT 1;CHR$(12);"**** STORAGE OF DATA POINT IN FREQ VS. CONDUCTANCE AND
CAPACITANCE FILE ****"
8650 !
8660 !   DECIDE IF OLD OR NEW DATA FILE
8670 !
8680 INPUT "ENTER ""NEW"" IF DATA FILE TO BE CREATED:",Answer$
8690 !
8700 IF Answer$="NEW" THEN
8710   INPUT "ENTER NEW FILE NAME:",File_name$
8720   INPUT "SPECIFY LEFT OR RIGHT HAND DRIVE(L OR R):",Answer$
8730   IF Answer$="L" THEN
8740     File_specifier$=File_name$&":INTERNAL,4,1"
8750   ELSE
8760     File_specifier$=File_name$&":INTERNAL,4,0"
8770   END IF
8780   !
8790   !   CREATE DISK FILE
8800   !
8810   CREATE BDAT File_specifier$,4,400
8820   ASSIGN @File TO File_specifier$;FORMAT OFF
8830   !
8840   !   GET BIAS VOLTAGE TO BE RECORDED
8850   !
8860   REPEAT
8870     INPUT "ENTER BIAS VOLTAGE TO BE RECORDED:",Bias_voltage
8880     UNTIL (Bias_voltage>Bias_volt(1) AND Bias_voltage<Bias_volt(Points)) OR
(Bias_voltage<Bias_volt(1) AND Bias_voltage>Bias_volt(Points))
8890     !
8900     !   ASSIGN REMAINING FILE PARAMETERS
8910     !
8920     Sample_id$=Sample_codes$
8930     Temp=Temperature
8940     Dop_type$=Doping_type$
8950     Pnts=0
8960     FOR I=1 TO 50
8970       Capac(I)=0

```

```

8980         Conduct(I)=0
8990         Meas_fr(I)=0
9000     NEXT I
9010     !
9020     !     WRITE RECORD 1 OF FILE
9030     !
9040     OUTPUT @File,1;Bias_voltage,Sample_id$,Temp,Dop_type$,Pnts
9050     OUTPUT @File,2;Meas_fr(*)
9060     OUTPUT @File,3;Conduct(*)
9070     OUTPUT @File,4;Capac(*)
9080 ELSE
9090     !
9100     !     GET EXISTING DATA FILE FROM DISK
9110     !
9120     REPEAT
9130         File_name$=""
9140         INPUT "ENTER EXISTING FILE NAME:",File_name$
9150         !
9160         !     IF USER ENTERS BLANK FILE NAME EXIT SUBROUTINE
9170         !
9180         IF File_name$="" THEN SUBEXIT
9190         INPUT "SPECIFY LEFT OR RIGHT HAND DRIVE(L OR R):",Answer$
9200         IF Answer$="L" THEN
9210             File_specifier$=File_name$&"":INTERNAL,4,1"
9220         ELSE
9230             File_specifier$=File_name$&"":INTERNAL,4,0"
9240         END IF
9250         !
9260         !     POINT TO DISK FILE
9270         !
9280         ASSIGN @File TO File_specifier$;FORMAT OFF
9290         !
9300         !     ENTER FILE INTO COM AREA
9310         !
9320         ENTER @File,1;Bias_voltage,Sample_id$,Temp,Dop_type$,Pnts
9330         ENTER @File,2;Meas_fr(*)
9340         ENTER @File,3;Conduct(*)
9350         ENTER @File,4;Capac(*)
9360         !
9370         !     CHECK FILE FOR CONSISTENCY WITH DATA
9380         !
9390         Data_compatible=(Sample_id$=Sample_code$ AND Temp=Temperature AND Do
p_type$=Doping_type$)
9400         !
9410         IF NOT Data_compatible THEN
9420             BEEP
9430             OUTPUT 1;CHR$(10);"ERROR -- DATA NOT COMPATABLE WITH DISK FILE";C
HR$(10)
9440             OUTPUT 1 USING "20X,13A,12X,9A";"INTERNAL DATA","DISK DATA"
9450             OUTPUT 1 USING "12A,9X,10A,14X,10A";"SAMPLE CODE:",Sample_code$,S
ample_id$
9460             OUTPUT 1 USING "12A,9X,DDD.DD,18X,DDD.DD";"TEMPERATURE:",Temperat
ure,Temp
9470             OUTPUT 1 USING "12A,9X,1A,23X,1A";"DOPING TYPE:",Doping_type$,Dop
_type$
9480         END IF
9490     UNTIL Data_compatible
9500 END IF
9510     !
9520     !     VERIFY DATA FILE TO USER
9530     !

```

```

9540 IMAGE 20A,DDDDD.DD,2A
9550 IMAGE 20A,10A
9560 OUTPUT 1;CHR$(10);"THE DISK DATA FILE IS SPECIFIED BY THE FOLLOWING PARAME
TERS:";CHR$(10)
9570 OUTPUT 1 USING 9540;"BIAS VOLTAGE-",Bias_voltage
9580 OUTPUT 1 USING 9550;"SAMPLE CODE-",Sample_id$
9590 OUTPUT 1 USING 9540;"TEMPERATURE-",Temp
9600 OUTPUT 1 USING 9550;"DOPING TYPE-",Dop_type$
9610 !
9620 ! FIND DATA POINT IN INTERNAL FILE TO BE SAVED
9630 !
9640 IF Bias_volt(1)>Bias_volt(Points) THEN
9650     Count=Points
9660     Inc=-1
9670 ELSE
9680     Count=1
9690     Inc=1
9700 END IF
9710 !
9720 WHILE Bias_volt(Count)<Bias_voltage
9730     Count=Count+Inc
9740 END WHILE
9750 !
9760 ! EXTRACT CLOSEST POINT TO GIVEN BIAS VOLTAGE
9770 !
9780 IF ABS(Bias_volt(Count)-Bias_voltage)<ABS(Bias_volt(Count-Inc)-Bias_voltag
e) THEN
9790     Data_point=Count
9800 ELSE
9810     Data_point=Count-Inc
9820 END IF
9830 !
9840 ! FIND SLOT TO SAVE DATA POINT IN FREQUENCY FILE
9850 !
9860 IF Pnts=0 OR Meas_freq<=Meas_fr(1) THEN
9870     Slot=1
9880 ELSE
9881     Slot=2
9882     WHILE Meas_freq>Meas_fr(Slot) AND Meas_fr(Slot)<>0
9883         Slot=Slot+1
9890     END WHILE
9891 END IF
9900 !
9910 ! CHECK TO SEE THAT DATA NOT ALREADY ENTERED FOR MEAS FREQUENCY
9920 !
9930 IF Meas_fr(Slot)=Meas_freq THEN
9940     BEEP
9950 OUTPUT 1;CHR$(10);"ERROR -- THE FOLLOWING POINT ALREADY EXISTS IN FILE:
";CHR$(10)
9960 OUTPUT 1 USING "20X,10A,10X,11A,9X,11A";"FREQUENCY","CONDUCTANCE","CAPA
CITANCE"
9970     IMAGE 10A,10X,DDDDD.DD,"Hz",10X,DDDDD.DD,"pF",9X,DDDDD.DD,"pF"
9980     OUTPUT 1 USING 9970;"DATA FILE:",Meas_fr(Slot),Conduct(Slot),Capac(Slot
)
9990     OUTPUT 1 USING 9970;"INTL FILE:",Meas_freq,Conductance(Data_point),Capa
citanace(Data_point)
9991     PAUSE
10000 ELSE
10010 !
10020 ! VERIFY DATA POINT ADDITION WITH USER

```

```

10030      !
10040      OUTPUT 1;CHR$(10);"THE FOLLOWING POINT WILL BE ADDED TO THE DATA FILE:"
;CHR$(10)
10050      IMAGE 15A,10X,DDDDD.DD,3A
10060      OUTPUT 1 USING 10050;"BIAS VOLTAGE:",Bias_volt(Data_point),"V"
10070      OUTPUT 1 USING 10050;"FREQUENCY-",Meas_freq,"Hz"
10080      OUTPUT 1 USING 10050;"CONDUCTANCE-",Conductance(Data_point),"pF"
10090      OUTPUT 1 USING 10050;"CAPACITANCE-",Capacitance(Data_point),"pF"
10100      Answer$=""
10110      INPUT "HIT ENTER TO CONTINUE, ANYTHING ELSE WILL ABORT:",Answer$
10120      IF Answer$="" THEN
10130          !
10140          !     ENTER POINT IN FILE
10150          !
10160          FOR I=Pnts TO Slot STEP -1
10170              Meas_fr(I+1)=Meas_fr(I)
10180              Conduct(I+1)=Conduct(I)
10190              Capac(I+1)=Capac(I)
10200          NEXT I
10210          !
10220          Meas_fr(Slot)=Meas_freq
10230          Conduct(Slot)=Conductance(Data_point)
10240          Capac(Slot)=Capacitance(Data_point)
10250          !
10260          Pnts=Pnts+1
10270          !
10280          !     RE-WRITE DATA FILE
10290          !
10300          OUTPUT @File,1;Bias_voltage,Sample_id$,Temp,Dop_type$,Pnts
10310          OUTPUT @File,2;Meas_fr(*)
10320          OUTPUT @File,3;Conduct(*)
10330          OUTPUT @File,4;Capac(*)
10340          !
10350          !     NORMAL EXIT OF FREQ FILE SUBROUTINE
10360          !
10370          OUTPUT 1;CHR$(12)
10380      END IF
10390  END IF
10400  !
10410  !     EXIT SUBROUTINE FREQ FILE
10420  !
10430  SUBEND
10440  SUB Series_res
10450  !*****
10460  !     SUBROUTINE SERIES_RES MAKES CORRECTION FOR SERIES RESITANCE
10470  !     ACCORDING TO MODEL OF NICOLLIAN AND BREWS IN MOS PHYSICS AND TECH
10480  !     BOOK PAGE 220
10490  !*****
10500  !
10510  !     DECLARATION
10520  !
10530  OPTION BASE 1
10540  !
10550  COM /Conduct_data/ Notes${30}
10560  COM /Conduct_data/ Gendate${11}.Doping_type${1}
10570  COM /Conduct_data/ INTEGER Calibrate_flag,Data_flag,Setup_flag,Ser_res
10580  COM /Conduct_data/ INTEGER High_volt,Points
10590  COM /Conduct_data/ REAL Bias_volt(1000),Capacitance(1000),Conductance(1000
)
10600  COM /Conduct_data/ Capac_const,Conduct_const,Capac_oxide,Meas_freq
10610  COM /Conduct_data/ Sample_code$,Dev_area,V_source_bulk,Temperature

```

```

10620 !
10630 INTEGER Accum_point
10640 REAL Series_resist,Num_factor,Den_factor,A
10641 IF NOT Data_flag THEN
10642     BEEP
10643     OUTPUT 1;"ERROR -- NO DATA TAKEN TO CORRECT FOR SERIES RESISTANCE"
10644     SUBEXIT
10645 END IF
10646 !
10647 !   DEFINE PROGRAM STATE TO USER
10648 !
10649 OUTPUT 1;CHR$(12);"***** DATA FILE BEING CORRECTED FOR SERIES
RESITANCE *****"
10651 !
10660 !   DECIDE WHICH END BIAS POINT IS TAKEN IN ACCUMULATION
10670 !
10680 IF ABS(Capacitance(1)-Capac_oxide)<ABS(Capacitance(Points)-Capac_oxide) TH
EN
10690     Accum_point=1
10700 ELSE
10710     Accum_point=Points
10720 END IF
10730 !
10820 !   GET SERIES RESISTANCE AND OXIDE CAPACITANCE
10830 !
10840 Series_resist=Conductance(Accum_point)/((Conductance(Accum_point))^2+(Capa
citanace(Accum_point))^2)
10850 !
10860 Capac_oxide=Capacitance(Accum_point)*(1+(Conductance(Accum_point)/(Capacit
ance(Accum_point)))^2)
10870 !
10880 !   CORRECT DATA FILE FOR SERIES RESISTANCE
10890 !
10900 FOR I=1 TO Points
10910     Num_factor=Conductance(I)^2+(Capacitance(I))^2
10920     A=Conductance(I)-Num_factor*Series_resist
10930     Den_factor=A^2+(Capacitance(I))^2
10940     !
10950     Capacitance(I)=Num_factor*Capacitance(I)/Den_factor
10960     Conductance(I)=Num_factor*A/Den_factor
10970     !
10980 NEXT I
10990 !
11000 !   EXIT SERIES RESISTANCE SUBROUTINE
11010 !
11011 Ser_res=1
11012 OUTPUT 1;CHR$(12)
11013 !
11020 SUBEND
11030 SUB Reduce
11040 !*****
11050 !   SUBROUTINE REDUCE CHANGES THE MEASURE CAPACITANCES AND CONDUCTANCES
11060 !   TO EQUIVALENT PARALLEL CAPACITANCE AND CONDUCTANCE
11070 !   REF: H. DEULING,E. KLAUSMANN AND A. GOETZBURGER,SOL ST ELEC,15,
11080 !       559-571(1972)
11090 !*****
11100 !
11110 !   DECLARATIONS
11120 !
11130 OPTION BASE 1

```



```

11140 !
11150 COM /Conduct_data/ Notes$(30)
11160 COM /Conduct_data/ Gendate$(11),Doping_type$(1)
11170 COM /Conduct_data/ INTEGER Calibrate_flag,Data_flag,Setup_flag,Ser_res
11180 COM /Conduct_data/ INTEGER High_volt,Points
11190 COM /Conduct_data/ REAL Bias_volt(1000),Capacitance(1000),Conductance(1000
)
11200 COM /Conduct_data/ Capac_const,Conduct_const,Capac_oxide,Meas_freq
11210 COM /Conduct_data/ Sample_code$,Dev_area,V_source_bulk,Temperature
11220 !
11230 REAL Den_factor
11240 !
11250 !   GET w*Cox
11260 !
11280 FOR I=1 TO Points
11290   Den_factor=(Conductance(I)/Capac_oxide)^2+(1-Capacitance(I)/Capac_oxide
)^2
11300   !
11310   !   GET EQUIVALENT PARALLEL CONDUCTANCE
11320   !
11321   IF Den_factor<>0 THEN
11330     Conductance(I)=(Conductance(I)/Capac_oxide)/Den_factor
11331   END IF
11340   !
11350   !   GET EQUIVALENT PARALLEL CAPACITANCE
11360   !
11361   IF Den_factor<>0 THEN
11370     Capacitance(I)=((1-Capacitance(I)/Capac_oxide)/Den_factor)-1
11371   END IF
11380 NEXT I
11390 !
11400 !   EXIT
11410 !
11420 SUBEND

```

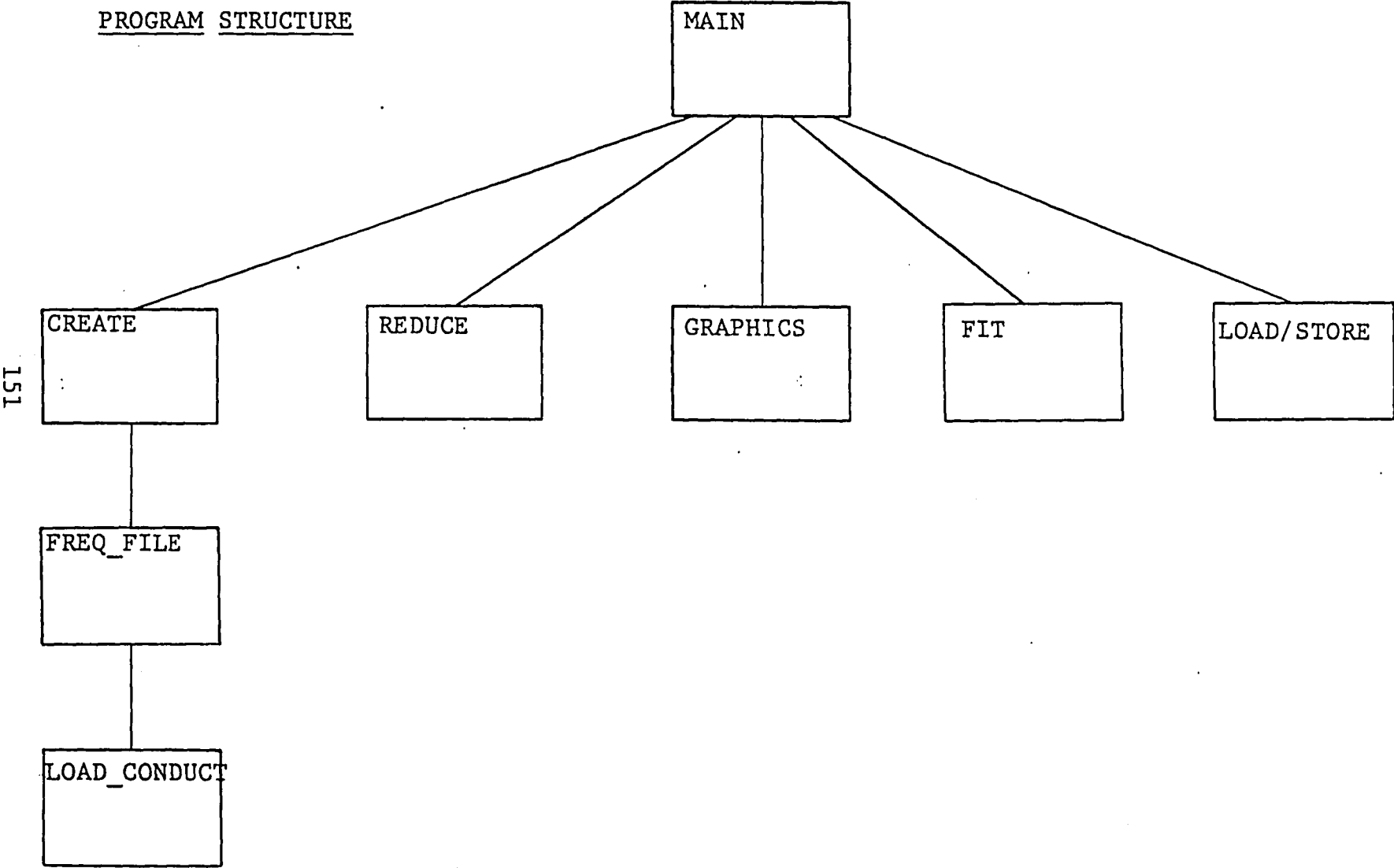
## APPENDIX G

### Admittance Measurement Analysis Program

This program was written to analyze admittance measurements according to the theory developed by Nicollian & Goetzburger. The program is written in a structured manner with file creation, reduction, fitting as well as graphics available to the user.

The program is typically used by first creating a Conductance versus Frequency file by use of the CREATE key. This function cross sections input files at a given bias level. Before the created data can be compared to theory it must be reduced to an equivalent parallel capacitance and conductance by use of the REDUCE key. Fits can then be attempted with the user providing input parameters. Comparison of measured and fitted data can be done graphically. Load and store functions are provided so that both fitted and measured data can be saved on disk.

PROGRAM STRUCTURE



Subroutine Directory  
Admittance Measurement Analysis Program

CREATE

Function:

- a) get bias voltage to be analyzed from user
- b) get list of disk file names from user which contain conductance & capacitance vs. bias data taken at different frequencies on same device
- c) pass list to subroutine frequency file which searches disk files & extracts conductance & capacitance at given bias
- d) result is a conductance & capacitance vs. frequency file at a fixed surface potential.

REDUCE

Function:

- a) takes measured conductance & capacitance data and reduces them to equivalent parallel conductance & capacitance according to formulas given by H. Deuling, E. Klausmann and A. Goetzburger, Sol. St. Elec., 15, 559-571, (1972)

GRAPHICS

Function:.

- a) maintains separate graphics screens of conductance vs. frequency and capacitance vs. frequency (can either graph measured or theoretical data).

## FIT

Function:

a) gets device parameters from user from which it generates theoretical curves of the conductance & capacitance vs. frequency.

## LOAD/STORE

Function:

a) store/load data on disk for later analysis.

Variable Directory of COMBBlock  
/COND\_FREQ\_DATA/

- BIAS\_VOLTAGE - User input parameter indicating the bias voltage to be examined. Set by subroutine CREATE.
- SAMPLE\_ID\$ - (STRING) 10 Character input parameter in data file indicating sample identification code.
- TEMP - (REAL) Parameter in data file indicating the temperature at measurement time.
- DOP\_TYPE\$ - (STRING) 1 Character in data file indicating the doping type of sample.
- PNTS - (REAL) Variable indicating the number of points in data file.
- MEAS\_FR(50) - (REAL) Data array of cross sectioned data indicating measurement frequency of data point.
- CONDUCT\_M(50) - (REAL) Data array of measured conductances at corresponding measurement frequency.
- CAPAC\_M(50) - (REAL) Data array of measured capacitances at corresponding measurement frequency.
- CONDUCT\_P(50) - (REAL) Created data array set by subroutine REDUCE which is the parallel conductance extracted from the measured conductance.
- CAPAC\_P(50) - (REAL) Created data array set by subroutine REDUCE which is the parallel capacitance extracted from the measured capacitance and conductance.
- COND\_P\_FIT(100) - (REAL) Created data array set by subroutine FIT which is the created theoretical conductance data.

CAP\_P\_FIT(100) - (REAL) Created data array set by subroutine FIT which is the created theoretical capacitance data.

FREQ\_FIT(100) - (REAL) Created data array of the frequencies which theoretical data is calculated for. Set by subroutine FIT

OX\_CAP - (REAL) User input parameter in subroutine FIT which indicates the sample oxide capacitance.

SIGMA\_S - (REAL) User input parameter used for fitting indicating the variance in the surface potential.

DIT - (REAL) User input parameter in subroutine FIT indicating the interface state density.

TAU\_N - (REAL) User input parameter in subroutine FIT indicating the trap time constant.

AREA - (REAL) User input parameter in subroutine FIT indicating the device area.

CAL\_POINTS - (REAL) Create variable in subroutine FIT indicating the number of theoretical data points calculated

CD - (REAL) User input parameter in subroutine FIT indicating the device depletion capacitance.

```

10 !*****
20 ! PROGRAM FOR ANALYSIS OF CONDUCTANCE VS. FREQUENCY DATA
30 !*****
40 !
50 ! DECLARATION
60 !
70 OPTION BASE 1
80 !
90 COM /Cond_freq_data/ Bias_voltage,Sample_id$(10),Temp,Dop_type$(1)
100 COM /Cond_freq_data/ Pnts,Meas_fr(50),Conduct_m(50),Capac_m(50)
110 COM /Cond_freq_data/ Conduct_p(50),Capac_p(50)
120 COM /Cond_freq_data/ Cond_p_fit(100),Cap_p_fit(100),Freq_fit(100)
130 COM /Cond_freq_data/ Ox_cap,Sigma_s,Dit,Tau_n,Area,Cal_points,Cd
140 !
150 ON KEY 0 LABEL "REDUCE" CALL Reduce
160 ON KEY 1 LABEL "VIEW G/C" CALL View_cond
161 ON KEY 11 CALL View_cap
170 ON KEY 2 LABEL "GRAPH G/C" CALL Graph
171 ON KEY 12 CALL Cap_graph
180 ON KEY 3 LABEL "ANALYZE" GOSUB Dummy
190 ON KEY 4 LABEL "CREATE" CALL Create_file
200 ON KEY 5 LABEL "LOAD" CALL Load
210 ON KEY 6 LABEL "STORE" CALL Store
220 ON KEY 7 LABEL "FIT" CALL Fit
221 ON KEY 8 LABEL "FIT LOAD/STORE" CALL Load_fit
222 ON KEY 18 CALL Store_fit
230 ON KEY 9 LABEL "EXIT" GOTO Ending
240 !
250 ! SET MACHINE IN IDLE LOOP
260 !
270 WHILE 1=1
280 DISP FNTIME$(TIMEDATE)
290 END WHILE
300 !
310 ! DUMMY SUBROUTINE
320 !
330 Dummy: !
340 RETURN
350 !
360 Ending: !
370 END!

```



```

380 SUB Reduce
390 !*****
400 ! SUBROUTINE REDUCE CHANGES THE MEASURE CAPACITANCES AND CONDUCTANCES
410 ! TO EQUIVALENT PARALLEL CAPACITANCE AND CONDUCTANCE
420 ! REF: H. DEULING,E. KLAUSMANN AND A. GOETZBURGER,SOL ST ELEC,15,
430 ! 559-571(1972)
440 !*****
450 !
460 ! DECLARATIONS
470 !
480 OPTION BASE 1
490 !
500 COM /Cond_freq_data/ Bias_voltage,Sample_id$(10),Temp,Dop_type$(1)
510 COM /Cond_freq_data/ Pnts,Meas_fr(50),Conduct_m(50),Capac_m(50)
520 COM /Cond_freq_data/ Conduct_p(50),Capac_p(50)
530 COM /Cond_freq_data/ Cond_p_fit(100),Cap_p_fit(100),Freq_fit(100)
531 COM /Cond_freq_data/ Ox_cap,Sigma_s,Dit,Tau_n,Area,Cal_points,Cd
550 !
560 REAL Den_factor,Cap_ox
570 !
580 ! GET OXIDE CAPACITANCE
590 !
600 INPUT "ENTER OXIDE CAPACITANCE(PF):",Cap_ox
610 !
620 ! REDUCE MEASURED CAP AND COND TO EQUIVALENT PARALLEL CAP AND COND
630 !
640 FOR I=1 TO Pnts
650 Den_factor=(Conduct_m(I)/Cap_ox)^2+(1-Capac_m(I)/Cap_ox)^2
660 !
670 IF Den_factor<>0 THEN
680 Conduct_p(I)=(Conduct_m(I)/Cap_ox)/Den_factor
690 Capac_p(I)=((1-Capac_m(I)/Cap_ox)/Den_factor)-1
700 END IF
710 !
720 NEXT I
730 !
740 ! EXIT
750 !
760 SUBEND!

```

```

770 SUB Load
780 !*****
790 ! SUBROUTINE LOAD RETRIEVES DATA FROM DISK FILE
800 !*****
810 !
820 OPTION BASE 1
830 !
840 COM /Cond_freq_data/ Bias_voltage,Sample_id$(10),Temp,Dop_typ$(1)
850 COM /Cond_freq_data/ Pnts,Meas_fr(50),Conduct_m(50),Capac_m(50)
860 COM /Cond_freq_data/ Conduct_p(50),Capac_p(50)
870 COM /Cond_freq_data/ Cond_p_fit(100),Cap_p_fit(100),Freq_fit(100)
871 COM /Cond_freq_data/ Ox_cap,Sigma_s,Dit,Tau_n,Area,Cal_points,Cd
890 !
900 DIM Answer$(3),File_name$(10),File_specifier$(30)
910 !
920 ! DEFINE PROGRAM STATE TO USER
930 !
940 OUTPUT 1;"***** LOAD OF DATA FILE FROM DISK *****
*****"
950 !
960 ! GET FILE
970 !
980 INPUT "ENTER FILE NAME:",File_name$
990 INPUT "SPECIFY LEFT OR RIGHT HAND DRIVE(L OR R):",Answer$
1000 IF Answer$="L" THEN
1010 File_specifier$=File_name$&":INTERNAL,4,1"
1020 ELSE
1030 File_specifier$=File_name$&":INTERNAL,4,0"
1040 END IF
1050 !
1060 ! POINT TO DISK FILE
1070 !
1080 ASSIGN @File TO File_specifier$;FORMAT OFF
1090 !
1100 ! ENTER FILE INTO COM AREA
1110 !
1120 ENTER @File,1;Bias_voltage,Pnts
1130 ENTER @File,2;Meas_fr(*)
1140 ENTER @File,3;Conduct_m(*)
1150 ENTER @File,4;Capac_m(*)
1160 ENTER @File,5;Conduct_p(*)
1170 ENTER @File,6;Capac_p(*)
1180 !
1190 ! EXIT LOAD SUBROUTINE
1200 !
1210 SUBEND!

```

```

1220 DEF FNTIME$(Now) ! GIVEN 'SECONDS' RETURN 'HH:MM:SS'
1230 !
1240 Now=INT(Now) MOD 86400
1250 H=Now DIV 3600
1260 M=Now MOD 3600 DIV 60
1270 S=Now MOD 60
1280 OUTPUT T$ USING "#,ZZ,K";H,"",M,"",S
1290 RETURN T$
1300 FNEND
1310 !
1320 DEF FNTIME(T$) ! GIVEN 'HH:MM:SS' RETURN 'SECONDS'
1330 !
1340 ON ERROR GOTO Err
1350 ENTER T$;H,M,S
1360 RETURN (3600*H+60*M+S) MOD 86400
1370 Err:OFF ERROR
1380 RETURN TIMEDATE MOD 86400
1390 FNEND
1400 DEF FNDATE$(Seconds) !GIVEN 'SECONDS' RETURN "DD MMM YYYY"
1410 !
1420 DATA JAN,FEB,MAR,APR,MAY,JUN,JUL,AUG,SEP,OCT,NOV,DEC
1430 DIM Month$(1:12)[3]
1440 READ Month$(*)
1450 !
1460 Julian=Seconds DIV 86400-1721119
1470 Year=(4*Julian-1) DIV 146097
1480 Julian=(4*Julian-1) MOD 146097
1490 Day=Julian DIV 4
1500 Julian=(4*Day+3) DIV 1461
1510 Day=(4*Day+3) MOD 1461
1520 Day=(Day+4) DIV 4
1530 Month=(5*Day-3) DIV 153
1540 Day=(5*Day-3) MOD 153
1550 Day=(Day+5) DIV 5
1560 Year=100*Year+Julian
1570 IF Month<10 THEN
1580 Month=Month+3
1590 ELSE
1600 Month=Month-9
1610 Year=Year+1
1620 END IF
1630 OUTPUT D$ USING "#,ZZ,X,3A,X,4Z";Day,Month$(Month),Year
1640 RETURN D$
1650 FNEND
1660 !
1670 DEF FNDATE(Dmy$) ! GEVEN 'DD MMM YYYY' RETURN 'SECONDS'
1680 !
1690 DATA JAN,FEB,MAR,APR,MAY,JUN,JUL,AUG,SEP,OCT,NOV,DEC
1700 DIM Month$(1:12)[3]
1710 READ Month$(*)
1720 !
1730 ON ERROR GOTO Err
1740 I$=Dmy$&" "
1750 ENTER I$ USING "DD,4A,5D";Day,M$,Year
1760 IF Year<100 THEN Year=Year+1900
1770 FOR I=1 TO 12
1780 IF POS(M$,Month$(I)) THEN Month=I
1790 NEXT I
1800 IF Month=0 THEN Err

```

```
1810 IF Month>2 THEN
1820   Month=Month-3
1830 ELSE
1840   Month=Month+9
1850   Year=Year-1
1860 END IF
1870 Century=Year DIV 100
1880 Remainder=Year MOD 100
1890 Julian=146097*Century DIV 4+1461*Remainder DIV 4+(153*Month+2) DIV 5+Day
+1721119
1900 Julian=Julian*86400
1910 IF Julian<2.08662912E+11 OR Julian>=2.143252224E+11 THEN Err
1920 RETURN Julian ! RETURN JULIAN DATE IN SECONDS
1930 Err: OFF ERROR
1940 RETURN TIMEDATE ! RETURN CURRENT DATE
1950 FNEND!
```

```

1960 SUB Graph
1970 !*****
1980 ! SUBROUTINE GRAPH MAKES THE Gp/w VS. w CURVES FOR THE DATA FILE
1990 !*****
2000 !
2010 ! DECLARATIONS
2020 !
2030 OPTION BASE 1
2040 !
2050 COM /Cond_freq_data/ Bias_voltage,Sample_id$(10),Temp,Dop_type$(1)
2060 COM /Cond_freq_data/ Pnts,Meas_fr(50),Conduct_m(50),Capac_m(50)
2070 COM /Cond_freq_data/ Conduct_p(50),Capac_p(50)
2080 COM /Cond_freq_data/ Cond_p_fit(100),Cap_p_fit(100),Freq_fit(100)
2081 COM /Cond_freq_data/ Ox_cap,Sigma_s,Dit,Tau_n,Area,Cal_points,Cd
2100 !
2110 COM /Graphics/ INTEGER Axes_drawn,Cond_screen(12480)
2111 COM /Graphics/ REAL Left,Right,Top,Bottom
2120 !
2130 DIM Answer$(3),Plot_fit$(3)
2140 !
2150 ! RE-INITIALIZE GRAPHICS DISPLAY
2160 !
2170 DEG
2180 CLIP OFF
2190 PIVOT 0
2200 PEN 1
2210 LINE TYPE 1,5
2220 LORG 1
2230 CSIZE 5,.6
2240 LDIR 0
2250 MOVE 0,0
2260 !
2270 IF Axes_drawn THEN
2271 GLOAD Cond_screen(*)
2280 INPUT "SHOULD DATA BE PLOTTED ON SAME AXES(YES OR NO)?",Answer$
2290 END IF
2300 !
2310 ! SET FLAG TO SEE WHETHER TO DRAW AXES
2320 !
2330 Init=((Axes_drawn AND Answer$="NO") OR NOT Axes_drawn)
2340 IF Init THEN
2350 GCLEAR
2360 Axes_drawn=1
2370 !
2380 ! DEFINE GRAPHING LIMITS
2390 !
2400 Bottom=-.1
2410 Top=1.1
2420 Left=-.1*6
2430 Right=1.1*6
2440 !
2441 END IF
2442 !
2450 WINDOW Left,Right,Bottom,Top
2451 !
2452 IF Init THEN
2460 !
2470 ! TITLE GRAPH
2480 !

```

```

2490 CSIZE 6,.6
2500 MOVE (Left+Right)/2,Top
2510 LORG 6
2520 LABEL "Gp/wCox VS. w CURVE"
2530 !
2540 ! LABEL AXES
2550 !
2560 LDIR 90
2570 CSIZE 4,.6
2580 MOVE Left,(Bottom+Top)/2
2590 LORG 6
2600 LABEL "Gp/wCox"
2610 !
2620 LDIR 0
2630 MOVE (Left+Right)/2,Bottom
2640 LORG 4
2650 LABEL "FREQUENCY"
2660 !
2670 CSIZE 3,.6
2680 LORG 8
2690 FOR I=0 TO 1 STEP .1
2700 MOVE 0,I
2710 LABEL I
2720 NEXT I
2730 !
2740 LORG 6
2750 FOR I=0 TO 6
2760 MOVE I,0
2770 LABEL 10^I
2780 NEXT I
2790 !
2800 ! DRAW AXES
2810 !
2820 CLIP 0,6,0,1
2830 AXES 1,.1,0,0
2840 !
2850 END IF
2860 !
2870 INPUT "DO YOU WANT TO PLOT FIT (YES OR NO)".Plot_fit$
2880 IF Plot_fit$="YES" THEN GOTO 2990
2890 ! DRAW DATA POINTS
2900 !
2910 PENUP
2920 CSIZE 3,.6
2930 FOR I=1 TO Pnts
2940 MOVE LGT(Meas_fr(I)),Conduct_p(I)
2950 LORG 5
2960 LABEL "*"
2970 NEXT I
2980 GOTO 3034
2990 ! PLOT THE FIT
3000 PENUP
3010 FOR I=1 TO Cal_points
3020 PLOT LGT(Freq_fit(I)),Cond_p_fit(I)
3030 NEXT I
3031 !
3032 ! STORE THE CONDUCTANCE GRAPHICS SCREEN
3033 !
3034 GSTORE Cond_screen(*)
3040 !
3050 SUBEND!

```

```

3060 SUB Load_conduct(File_specifier$,INTEGER Error_flag)
3070 !*****
3080 !   SUBROUTINE "LOAD" RETRIEVES A DATA FILE FROM THE DISK
3090 !*****
3100 !
3110 !   DECLARATIONS
3120 !
3130 OPTION BASE 1
3140 !
3150 COM /Conduct_data/ Notes$(30)
3160 COM /Conduct_data/ Gendate$(11),Doping_type$(1)
3170 COM /Conduct_data/ INTEGER Calibrate_flag,Data_flag,Setup_flag,Ser_res
3180 COM /Conduct_data/ INTEGER High_volt,Points
3190 COM /Conduct_data/ REAL Bias_volt(1000),Capacitance(1000),Conductance(1000)
3200 COM /Conduct_data/ Capac_const,Conduct_const,Capac_oxide,Meas_freq
3210 COM /Conduct_data/ Sample_code$(10),Dev_area,V_source_bulk,Temperature
3220 !
3230 !   LOAD THE DATA FILE
3240 !
3250 ON ERROR GOSUB Error_hand
3260 ASSIGN @Path2 TO File_specifier$;FORMAT OFF
3270 OFF ERROR
3280 !
3290 !
3300 ENTER @Path2;Notes$
3310 ENTER @Path2;Gendate$,Doping_type$
3320 ENTER @Path2;High_volt,Points
3330 ENTER @Path2;Bias_volt(*),Capacitance(*),Conductance(*)
3340 ENTER @Path2;Capac_const,Conduct_const,Capac_oxide,Meas_freq
3350 ENTER @Path2;Sample_code$,Dev_area,V_source_bulk
3360 ENTER @Path2;Temperature
3370 !
3380 !   SET PROGRAM STATE FLAGS
3390 !
3400 Calibrate_flag=0
3410 Setup_flag=0
3420 Data_flag=1
3430 Ser_res=0
3440 !
3450 !   CLOSE I/O PATH AND EXIT
3460 !
3470 OUTPUT 1;CHR$(12)
3480 ASSIGN @Path2 TO *
3490 SUBEXIT
3500 !
3510 !   ERROR HANDLING SUBROUTINE
3520 !
3530 Error_hand: !
3540 BEEP
3550 OUTPUT 1;CHR$(12),"ERROR WHILE OPENING INPUT FILE WITH ERROR:";ERRN
3560 Error_flag=1
3570 SUBEXIT
3580 RETURN
3590 !
3600 SUBEND!

```

```

3610 SUB Freq_file(Infile_spec$,REAL Bias,INTEGER New,Error_flag)
3620 !*****
3630 ! THIS SUBROUTINE ADDS A DATA POINT TO A CONDUCTANCE VS. FREQUENCY
3640 ! DATA FILE ON DISK
3650 !*****
3660 !
3670 ! DECLARATIONS
3680 !
3690 OPTION BASE 1
3700 !
3710 COM /Cond_freq_data/ Bias_voltage,Sample_id$(10),Temp,Dop_type$(1)
3720 COM /Cond_freq_data/ Pnts,Meas_fr(50),Conduct_m(50),Capac_m(50)
3730 COM /Cond_freq_data/ Conduct_p(50),Capac_p(50)
3740 COM /Cond_freq_data/ Cond_p_fit(100),Cap_p_fit(100),Freq_fit(100)
3741 COM /Cond_freq_data/ Ox_cap,Sigma_s,Dit,Tau_n,Area,Cal_points,Cd
3760 !
3770 COM /Conduct_data/ Notes$(30)
3780 COM /Conduct_data/ Gendate$(11),Doping_type$(1)
3790 COM /Conduct_data/ INTEGER Calibrate_flag,Data_flag,Setup_flag,Ser_res
3800 COM /Conduct_data/ INTEGER High_volt,Points
3810 COM /Conduct_data/ REAL Bias_volt(1000),Capacitance(1000),Conductance(1000)
3820 COM /Conduct_data/ Capac_const,Conduct_const,Capac_oxide,Meas_freq
3830 COM /Conduct_data/ Sample_code$(10),Dev_area,V_source_bulk,Temperature
3840 !
3850 INTEGER Data_point,Data_compatible,Count,Inc,Slot
3860 !
3870 ! RETRIEVE CONDUCTANCE FILE
3880 !
3890 CALL Load_conduct(Infile_spec$,Error_flag)
3900 IF NOT Error_flag THEN
3910 !
3920 ! DECIDE IF OLD OR NEW DATA FILE
3930 !
3940 IF New THEN
3950 !
3960 ! INITIALIZE INTERNAL FILE
3970 !
3980 Bias_voltage=Bias
3990 Sample_id$=Sample_code$
4000 Temp=Temperature
4010 Dop_type$=Doping_type$
4020 !
4030 Pnts=0
4040 FOR I=1 TO 50
4050 Capac_m(I)=0
4060 Conduct_m(I)=0
4070 Capac_p(I)=0
4080 Conduct_p(I)=0
4090 Meas_fr(I)=0
4100 NEXT I
4110 !
4120 ELSE
4130 !
4140 ! CHECK FILE FOR CONSISTENCY WITH DATA
4150 !
4160 Data_compatible=(Sample_id$=Sample_code$ AND Temp=Temperature AND Do
p_type$=Doping_type$)
4170 !
4180 IF NOT Data_compatible THEN

```



```

4190          BEEP
4200          OUTPUT 1;CHR$(10);"ERROR -- DATA NOT COMPATABLE WITH DISK FILE";C
HR$(10)
4210          OUTPUT 1 USING "20X,13A,12X,9A";"INTERNAL DATA","DISK DATA"
4220          OUTPUT 1 USING "12A,9X,10A,14X,10A";"SAMPLE CODE:",Sample_code$,S
ample_id$
4230          OUTPUT 1 USING "12A,9X,DDD.DD,18X,DDD.DD";"TEMPERATURE:",Temperat
ure,Temp
4240          OUTPUT 1 USING "12A,9X,1A,23X,1A";"DOPING TYPE:",Doping_type$,Dop
_type$
4250          Error_flag=1
4260          SUBEXIT
4270          END IF
4280      END IF
4290      !
4300      !   FIND DATA POINT IN INTERNAL FILE TO BE SAVED
4310      !
4320      IF Bias_volt(1)>Bias_volt(Points) THEN
4330          Count=Points
4340          Inc=-1
4350          !
4360          !   CHECK TO SEE THAT BIAS IS IN RANGE
4370          !
4380          IF Bias_voltage>Bias_volt(1) OR Bias_voltage<Bias_volt(Points) THEN
4390              BEEP
4400              OUTPUT 1;"ERROR -- BIAS TO BE RECORDED NOT INCLUDED IN FILE"
4410              OUTPUT 1;"CONDUCTANCE FILE BIAS FROM ";Bias_volt(Points);" TO ";B
ias_volt(1)
4420              Error_flag=1
4430              SUBEXIT
4440          END IF
4450      ELSE
4460          Count=1
4470          Inc=1
4480          !
4490          !   CHECK TO SEE THAT BIAS IS IN RANGE
4500          !
4510          IF Bias_voltage<Bias_volt(1) OR Bias_voltage>Bias_volt(Points) THEN
4520              BEEP
4530              OUTPUT 1;"ERROR -- BIAS TO BE RECORDED NOT INCLUDED IN FILE"
4540              OUTPUT 1;"CONDUCTANCE FILE BIAS FROM ";Bias_volt(1);" TO ";Bias_v
olt(Points)
4550              Error_flag=1
4560              SUBEXIT
4570          END IF
4580      END IF
4590      !
4600      WHILE Bias_volt(Count)<Bias_voltage
4610          Count=Count+Inc
4620      END WHILE
4630      !
4640      !   EXTRACT CLOSEST POINT TO GIVEN BIAS VOLTAGE
4650      !
4660      IF ABS(Bias_volt(Count)-Bias_voltage)<ABS(Bias_volt(Count-Inc)-Bias_vol
tage) THEN
4670          Data_point=Count
4680      ELSE
4690          Data_point=Count-Inc
4700      END IF
4710      !

```

```

4720      !   FIND SLOT TO SAVE DATA POINT IN FREQUENCY FILE
4730      !
4740      IF Pnts=0 OR Meas_freq<=Meas_fr(1) THEN
4750          Slot=1
4760      ELSE
4770          Slot=2
4780          WHILE Meas_freq>Meas_fr(Slot) AND Meas_fr(Slot)<>0
4790              Slot=Slot+1
4800          END WHILE
4810      END IF
4820      !
4830      !   CHECK TO SEE THAT DATA NOT ALREADY ENTERED FOR MEAS FREQUENCY
4840      !
4850      IF Meas_fr(Slot)=Meas_freq THEN
4860          BEEP
4870          OUTPUT 1;CHR$(10);"ERROR -- THE FOLLOWING POINT ALREADY EXISTS IN FI
LE:";CHR$(10)
4880          OUTPUT 1 USING "20X,10A,10X,11A,9X,11A";"FREQUENCY","CONDUCTANCE","C
APACITANCE"
4890          IMAGE 10A,10X,DDDDD.DD,"Hz",10X,DDDDD.DD,"pF",9X,DDDDD.DD,"pF"
4900          OUTPUT 1 USING 4890;"FREQ FILE:",Meas_fr(Slot),Conduct_m(Slot),Capac
_m(Slot)
4910          OUTPUT 1 USING 4890;"COND FILE:",Meas_freq,Conductance(Data_point),C
apacitance(Data_point)
4920      !
4930      !   CHECK FOR POINT REPLACEMENT
4940      !
4950      Answer$=""
4960      INPUT "HIT ENTER TO REPLACE POINT IN FREQ FILE, ANYTHING ELSE WILL A
BORT",Answer$
4970      !
4980      IF Answer$="" THEN
4990          !
5000          !   REPLACE POINT
5010          !
5020          Meas_fr(Slot)=Meas_freq
5030          Conduct_m(Slot)=Conductance(Data_point)
5040          Capac_m(Slot)=Capacitance(Data_point)
5050          !
5060      ELSE
5070          Error_flag=1
5080      END IF
5090  ELSE
5100      !
5110      !   VERIFY DATA POINT ADDITION WITH USER
5120      !
5130      !   OUTPUT 1;CHR$(10);"THE FOLLOWING POINT WILL BE ADDED TO THE DATA FIL
E:";CHR$(10)
5140      !   IMAGE 15A,10X,DDDDDD.DD.3A
5150      !   OUTPUT 1 USING 4760;"BIAS VOLTAGE:",Bias_volt(Data_point),"V"
5160      !   OUTPUT 1 USING 4760;"FREQUENCY-",Meas_freq,"Hz"
5170      !   OUTPUT 1 USING 4760;"CONDUCTANCE-",Conductance(Data_point),"pF"
5180      !   OUTPUT 1 USING 4760;"CAPACITANCE-",Capacitance(Data_point),"pF"
5190      !   Answer$=""
5200      !   INPUT "HIT ENTER TO CONTINUE, ANYTHING ELSE WILL ABORT:",Answer$
5210      !   IF Answer$="" THEN
5220          !
5230          !   ENTER POINT IN FILE
5240          !
5250          FOR I=Pnts TO Slot STEP -1
5260              Meas_fr(I+1)=Meas_fr(I)

```

```

5270         Conduct_m(I+1)=Conduct_m(I)
5280         Capac_m(I+1)=Capac_m(I)
5290     NEXT I
5300     !
5310     Meas_fr(Slot)=Meas_freq
5320     Conduct_m(Slot)=Conductance(Data_point)
5330     Capac_m(Slot)=Capacitance(Data_point)
5340     !
5350     Pnts=Pnts+1
5360     !
5370     !     NORMAL EXIT OF FREQ FILE SUBROUTINE
5380     !
5390     OUTPUT 1;CHR$(12)
5400 !     ELSE
5410 !     OUTPUT 1;"USER ABORT"
5420 !     Error_flag=1
5430 !     END IF
5440     END IF
5450 END IF
5460 !
5470 !     EXIT SUBROUTINE FREQ FILE
5480 !
5490 SUBEND!

```

```

5500 SUB Create_file
5510 !
5520 !*****
5530 ! THIS SUBROUTINE CREATE A FREQUENCY FILE FROM INPUT CONDUCTANCE
5540 ! DATA FILES
5550 !*****
5560 !
5570 ! DECLARATIONS
5580 !
5590 OPTION BASE 1
5600 !
5610 COM /Hold_logic/ Infiles$(900),INTEGER No_of_files
5620 !
5630 REAL Bias_voltage
5640 INTEGER Create_flag,Pass_flag,Error_flag,Input_flag
5650 DIM Answer$(10),Infile_spec$(30),File_name$(10)
5660 DIM Drive_spec$(3)
5670 !
5680 !-----
5690 !
5700 ! CHECK FOR RE-INITIALIZATION OF INTERNAL COM AREA
5710 !
5720 INPUT "IS INTERNAL FILE TO BE RE-INITIALIZED(YES OR NO)?",Answer$
5730 !
5740 IF Answer$="Y" OR Answer$="YES" THEN
5750     Create_flag=1
5760     !
5770     ! GET BIAS VOLTAGE WHICH FILE IS TO BE CREATED AT
5780     !
5790     INPUT "ENTER BIAS VOLTAGE TO BE RECORDED",Bias_voltage
5800 ELSE
5810     Create_flag=0
5820 END IF
5830 !
5840 ! GET INPUT CONDUCTANCE FILES AND PROCESS
5850 !
5860 IF No_of_files<>0 THEN
5870     INPUT "USE LIST OF INPUT FILES FROM LAST CREATION",Answer$
5880     IF Answer$="YES" THEN
5890         Input_flag=0
5900
5910         OUTPUT 1;CHR$(12);"FREQUENCY FILE WILL BE CREATED FROM FOLLOWING FIL
ES:"
5920         FOR I=1 TO No_of_files
5930             Start_byte=(I-1)*30+1
5940             End_byte=Start_byte+29
5950             OUTPUT 1;Infiles$(Start_byte,End_byte)
5960         NEXT I
5970         Answer$=""
5980         INPUT "HIT 'ENTER' TO CONTINUE,ANYTHING ELSE WILL ABORT",Answer$
5990         IF Answer$<>"" THEN SUBEXIT
6000     ELSE
6010         Input_flag=1
6020         Answer$=""
6030         INPUT "RE-INITIALIZE FILE LIST OR ADD NAMES TO EXISTING LIST(R OR A)
:",Answer$
6040         IF Answer$="R" THEN
6050             No_of_files=0
6060             Infiles$=""

```

```

6060         END IF
6070     END IF
6080 ELSE
6090     Input_flag=1
6100 END IF
6110 !
6120 IF Input_flag THEN
6130     REPEAT
6140         File_name$=""
6150         INPUT "ENTER FILE NAME (HIT 'ENTER' TO EXIT):",File_name$
6160         !
6170         IF File_name$<>"" THEN
6180             !
6190             ! PROCESS INPUT FILE
6200             !
6210             No_of_files=No_of_files+1
6220             Drive_spec$=""
6230             INPUT "SPECIFY WHERE FILE EXISTS(L,R,EL,ER):",Drive_spec$
6240             SELECT Drive_spec$
6250                 CASE "L"
6260                     Infile_spec$=File_name$":INTERNAL,4,1"
6270                 CASE "EL"
6280                     Infile_spec$=File_name$":HP82901,703,0"
6290                 CASE "ER"
6300                     Infile_spec$=File_name$":HP82901,703,1"
6310                 CASE ELSE
6320                     Infile_spec$=File_name$":INTERNAL,4,0"
6330             END SELECT
6340             !
6350             Error_flag=0
6360             Pass_flag=Create_flag AND (No_of_files=1)
6370             CALL Freq_file(Infile_spec$,Bias_voltage,Pass_flag,Error_flag)
6380             !
6390             IF Error_flag THEN
6400                 No_of_files=No_of_files-1
6410                 OUTPUT 1;"FILE ";File_name$;" NOT ADDED TO FREQUENCY FILE"
6420             ELSE
6430                 List_flag=1
6440                 Start_byte=(No_of_files-1)*30+1
6450                 End_byte=Start_byte+29
6460                 Infiles$(Start_byte,End_byte)=Infile_spec$
6470             END IF
6480             !
6490         END IF
6500         !
6510         !
6520     UNTIL (File_name$="")
6530 ELSE
6540     FOR I=1 TO No_of_files
6550         !
6560         Start_byte=(I-1)*30+1
6570         End_byte=Start_byte+29
6580         Infile_spec$=Infiles$(Start_byte,End_byte)
6590         Pass_flag=Create_flag AND (I=1)
6600         Error_flag=0
6610         CALL Freq_file(Infile_spec$,Bias_voltage,Pass_flag,Error_flag)
6620         IF Error_flag THEN
6630             OUTPUT 1;"FILE ";Infile_spec$;" NOT ADDED TO FREQ FILE"
6640         END IF
6650     NEXT I
6660 END IF

```

6670 !  
6680 ! EXIT CREATE FILE SUBROUTINE  
6690 !  
6700 SUBEND!

```

6710 SUB Store
6720 !*****
6730 ! SUBROUTINE STORE STORES DATA FROM INTL FILE TO DISK
6740 !*****
6750 !
6760 OPTION BASE 1
6770 !
6780 COM /Cond_freq_data/ Bias_voltage,Sample_id${10},Temp,Dop_typ${11}
6790 COM /Cond_freq_data/ Pnts,Meas_fr(50),Conduct_m(50),Capac_m(50)
6800 COM /Cond_freq_data/ Conduct_p(50),Capac_p(50)
6810 COM /Cond_freq_data/ Cond_p_fit(100),Cap_p_fit(100),Freq_fit(100)
6811 COM /Cond_freq_data/ Qx_cap,Sigma_s,Dit,Tau_n,Area.Cal_points,Cd
6830 !
6840 DIM Answer${3},File_name${10},File_specifier${30}
6850 !
6860 ! DEFINE PROGRAM STATE TO USER
6870 !
6880 OUTPUT 1:"***** STORAGE OF DATA FILE ONTO DISK *****"
*****"
6890 !
6900 ! GET FILE NAME
6910 !
6920 INPUT "ENTER FILE NAME TO BE CREATED:",File_name$
6930 INPUT "SPECIFY LEFT OR RIGHT HAND DRIVE(L OR R):",Answer$
6940 IF Answer$="L" THEN
6950 File_specifier$=File_name$&":INTERNAL,4,1"
6960 ELSE
6970 File_specifier$=File_name$&":INTERNAL,4,0"
6980 END IF
6990 !
7000 ! POINT TO DISK FILE
7010 !
7020 CREATE BDAT File_specifier$,6,400
7030 ASSIGN @File TO File_specifier$;FORMAT OFF
7040 !
7050 ! ENTER FILE INTO COM AREA
7060 !
7070 OUTPUT @File,1;Bias_voltage,Sample_id$,Temp,Dop_type$,Pnts
7080 OUTPUT @File,2;Meas_fr(*)
7090 OUTPUT @File,3;Conduct_m(*)
7100 OUTPUT @File,4;Capac_m(*)
7110 OUTPUT @File,5;Conduct_p(*)
7120 OUTPUT @File,6;Capac_p(*)
7130 !
7140 ! EXIT LOAD SUBROUTINE
7150 !
7160 SUBEND!

```

```

7170 !
7180 !
7190 SUB Fit
7200 !*****
7210 ! SUBROUTINE FIT CALCULATES PARALLEL CONDUCTANCE AND CAPACITANCE
7220 ! FOR GIVEN VALUES OF AREA,OX_CAP,SIGMA_S,DIT,TAU_N
7230 !*****
7240 !
7250 ! DECLARATIONS
7260 !
7270 OPTION BASE 1
7280 !
7290 COM /Cond_freq_data/ Bias_voltage,Sample_id$(10),Temp,Dop_typ$(1)
7300 COM /Cond_freq_data/ Pnts,Meas_fr(50).Conduct_m(50),Capac_m(50)
7310 COM /Cond_freq_data/ Conduct_p(50),Capac_p(50)
7320 COM /Cond_freq_data/ Cond_p_fit(100),Cap_p_fit(100),Freq_fit(100)
7321 COM /Cond_freq_data/ Ox_cap,Sigma_s,Dit,Tau_n,Area,Cal_points,Cd
7340 !
7370 REAL F(101),F4(101)
7380 INTEGER J,L,M,N
7390 REAL Constant,Eata,D_eata,I,Integral
7400 !
7410 ! GET THE FITTING PARAMETERS FROM THE USER
7420 !
7430 INPUT "ENTER OXIDE CAPACITANCE IN PF",Ox_cap
7440 Ox_cap=Ox_cap*1.E-12
7450 INPUT "ENTER SIGMA_S",Sigma_s
7460 INPUT "ENTER DIT in Cm^-2ev^-1",Dit
7470 INPUT "AREA IN Cm^2",Area
7480 INPUT "ENTER TAU_N IN SEC ",Tau_n
7481 INPUT "ENTER DEPLETION CAPACITANCE",Cd
7600 !
7610 ! SET UP FREQ LOOP
7620 J=1
7630 Cal_points=0
7640 FOR I=0 TO 5 STEP .1
7650 !
7660 Freq_fit(J)=10^I
7670 D_eata=.4
7680 !
7690 FOR L=1 TO 51
7700 Eata=-10+(L-1)*D_eata
7710 F1=EXP(-Eata^2/(2*Sigma_s^2))
7720 F2=EXP(-Eata)*LOG(1+4*PI^2*Freq_fit(J)^2*Tau_n^2*EXP(2*Eata))
7721 F3=EXP(-Eata)*ATN(2*PI*Freq_fit(J)*Tau_n*EXP(Eata))
7730 F(L)=F1*F2
7731 F4(L)=F1*F3
7740 NEXT L
7750 !
7760 CALL Integration(51,D_eata,F(*),Integral)
7761 CALL Integration(51,D_eata,F4(*),Integral1)
7770 Constant=Area*1.6E-19*Dit/(2*Ox_cap*2*PI*Freq_fit(J)*Tau_n*SQR(2*PI*Si
7780 gma_s^2))
Cond_p_fit(J)=Constant*Integral

7790 Cal_points=Cal_points+1
7880 J=J+1
7890 NEXT I
7900 SUBEND!

```



```

7910      !
7920      SUB Integration(INTEGER N,REAL Step_size,F(*),Integral)
7930      !*****
7940      !   SUBROUTINE INTEGRATION TAKES N# OF POINTS (N ODD) AND USES
7950      !   SIMPSON'S RULE TO INTEGRATE ARRAY F(*)
7960      !*****
7970      !
7980      ! Declarations
7990      OPTION BASE 1
8000      INTEGER I
8010      Integral=0
8020      !
8030      FOR I=1 TO N-2 STEP 2
8040          Integral=Integral+(Step_size/3)*(F(I)+4*F(I+1)+F(I+2))
8050      NEXT I
8060      !
8070      SUBEND!

```

```

8080      SUB Cap_graph
8090      !*****
8100      ! SUBROUTINE CAP_GRAPH MAKES THE CAPAC VS. w CURVES FOR THE DATA
8110      !*****
8120      !
8130      !   DECLARATIONS
8140      !
8150      OPTION BASE 1
8160      !
8170      COM /Cond_freq_data/ Bias_votage,Sample_id$(10),Temp,Dop_type$(1)
8180      COM /Cond_freq_data/ Pnts,Meas_fr(50),Conduct_m(50),Capac_m(50)
8190      COM /Cond_freq_data/ Conduct_p(50),Capac_p(50)
8200      COM /Cond_freq_data/ Cond_p_fit(100),Cap_p_fit(100),Freq_fit(100)
8201     COM /Cond_freq_data/ Ox_cap,Sigma_s,Dit,Tau_n,Area,Cal_points,Cd
8220      !
8230      COM /Cap_graphics/ INTEGER Axes_drawn_cap,Cap_screen(12480)
8231      COM /Cap_graphics/ REAL Left,Right,Top,Bottom
8240      !
8250      !   RE-INITIALIZE GRAPHICS DISPLAY
8260      DEG
8270      CLIP OFF
8280      PIVOT 0
8290      PEN 1
8300      LINE TYPE 1,5
8310      LORG 1
8320      CSIZE 5,.6
8330      LDIR 0
8340      MOVE 0,0
8350      !
8360      IF Axes_drawn_cap THEN
8361         GLOAD Cap_screen(*)
8362         WINDOW Left,Right,Bottom,Top
8370         INPUT "SHOULD DATA BE PLOTTED ON SAME CAP AXES(YES OR NO)?",Answer$
8380      END IF
8390      !
8400      !   SET FLAG TO SEE WHETHER TO DRAW AXES
8410      !
8420      Init=((Axes_drawn_cap AND Answer$="NO") OR NOT Axes_drawn_cap)
8430      IF Init THEN
8440         GCLEAR
8450         Axes_drawn_cap=1
8460         !
8470         !   DEFINE GRAPHIC LIMITS
8480         !
8490         Bottom=-.5
8500         Top=2.5
8510         Left=-.1*6
8520         Right=1.1*6
8530         !
8531      END IF
8532      !
8533      !
8543      WINDOW Left,Right,Bottom,Top
8553      !
8554      IF Init THEN
8555         !
8560         !   TITLE GRAPH
8570         !
8580         CSIZE 6,.6
8590         MOVE (Left+Right)/2,Top

```

```

8600      LORG 6
8610      LABEL "Cp/Cox VS. w CURVE"
8620      !
8630      ! LABEL AXES
8640      !
8650      LDIR 90
8660      CSIZE 4,.6
8670      MOVE Left,(Bottom+Top)/2
8680      LORG 6
8690      LABEL "Cp/Cox"
8700      !
8710      LDIR 0
8720      MOVE (Left+Right)/2,Bottom
8730      LORG 4
8740      LABEL "FREQUENCY"
8750      !
8760      CSIZE 3,.6
8770      LORG 8
8780      FOR I=0 TO 2 STEP .5
8790          MOVE 0,I
8800          LABEL I
8810      NEXT I
8820      !
8830      LORG 6
8840      FOR I=0 TO 6
8850          MOVE I,0
8860          LABEL 10^I
8870      NEXT I
8880      !
8890      ! DRAW AXES
8900      !
8910      CLIP 0,6,0,2
8920      AXES 1,1,0,0
8930      !
8940      END IF
8950      !
8960      INPUT "DO YOU WANT TO PLOT FIT (YES OR NO):",Plot_fit$
8970      !
8980      IF Plot_fit$="YES" THEN
8990          !
9000          ! PLOT FIT
9010          !
9020          PENUP
9030          FOR I=1 TO Cal_points
9040              PLOT LGT(Freq_fit(I)),Cap_p_fit(I)
9050          NEXT I
9060      ELSE
9070          !
9080          ! PLOT DATA
9090          !
9100          PENUP
9101          LORG 5
9102          CSIZE 3,.6
9110          FOR I=1 TO Pnts
9120              MOVE LGT(Meas_fr(I)),Capac_p(I)
9121              LABEL "*"
9130          NEXT I
9140      END IF
9141      !
9142      ! STORE THE CAPACITANCE GRAPHICS SCREEN

```

```
9143      !  
9144      !   GSTORE Cap_screen(*)  
9150      !  
9160      !   EXIT SUBROUTINE  
9170      !  
9180      SUBEND!
```

```

9190 SUB Store_fit
9200 !*****
9210 ! SUBROUTINE STORE STORES DATA FROM INTL FILE TO DISK
9220 !*****
9230 !
9240 OPTION BASE 1
9250 !
9260 COM /Cond_freq_data/ Bias_voltage,Sample_id$(10),Temp,Dop_typ$(1)
9270 COM /Cond_freq_data/ Pnts,Meas_fr(50),Conduct_m(50),Capac_m(50)
9280 COM /Cond_freq_data/ Conduct_p(50),Capac_p(50)
9290 COM /Cond_freq_data/ Cond_p_fit(100),Cap_p_fit(100),Freq_fit(100)
9291 COM /Cond_freq_data/ Ox_cap,Sigma_s,Dit,Tau_n,Area,Cal_points,Cd
9310 !
9320 DIM Answer$(3),File_name$(10),File_specifier$(30)
9330 !
9340 ! DEFINE PROGRAM STATE TO USER
9350 !
9360 OUTPUT 1;"***** STORAGE OF FIT FILE ONTO DISK *****"
*****
9370 !
9380 ! GET FILE NAME
9390 !
9400 INPUT "ENTER FILE NAME TO BE CREATED:",File_name$
9410 INPUT "SPECIFY LEFT OR RIGHT HAND DRIVE(L OR R):",Answer$
9420 IF Answer$="L" THEN
9430 File_specifier$=File_name$&":INTERNAL,4,1"
9440 ELSE
9450 File_specifier$=File_name$&":INTERNAL,4,0"
9460 END IF
9470 !
9480 ! POINT TO DISK FILE
9490 !
9500 CREATE BDAT File_specifier$,4,800
9510 ASSIGN @File TO File_specifier$;FORMAT OFF
9520 !
9530 ! ENTER FILE INTO COM AREA
9540 !
9545 OUTPUT @File,1;Tau_n,Ox_cap,Sigma_s,Area,Temp,Cal_points,Cd
9560 OUTPUT @File,2;Freq_fit(*)
9570 OUTPUT @File,3;Cond_p_fit(*)
9580 OUTPUT @File,4;Cap_p_fit(*)
9610 !
9620 ! EXIT LOAD SUBROUTINE
9630 !
9640 SUBEND!

```

```
14060 SUB View_cond
14070 !
14071 OPTION BASE 1
14072 !
14080 COM /Graphics/ INTEGER Axes_drawn,Cond_screen(12480)
14090 COM /Graphics/ REAL Top,Bottom,Left,Right
14100 !
14110 GLOAD Cond_screen(*)
14120 SUBEND
14130 SUB View_cap
14140 !
14141 OPTION BASE 1
14142 !
14150 COM /Cap_graphics/ INTEGER Axes_drawn_cap,Cap_screen(12480)
14160 COM /Cap_graphics/ REAL Top,Bottom,Left,Right
14170 !
14180 GLOAD Cap_screen(*)
14190 SUBEND!
```

```

14200 SUB Load_fit
14210 !*****
14220 !   SUBROUTINE LOAD RETRIEVES DATA FROM DISK FILE
14230 !*****
14240 !
14250 OPTION BASE 1
14260 !
14270 COM /Cond_freq_data/ Bias_voltage,Sample_id${10},Temp,Dop_typ${11}
14280 COM /Cond_freq_data/ Pnts,Meas_fr(50),Conduct_m(50),Capac_m(50)
14290 COM /Cond_freq_data/ Conduct_p(50),Capac_p(50)
14300 COM /Cond_freq_data/ Cond_p_fit(100),Cap_p_fit(100),Freq_fit(100)
14301 COM /Cond_freq_data/ Ox_cap,Sigma_s,Dit,Tau_n,Area,Cal_points,Cd
14320 !
14330 DIM Answer${3},File_name${10},File_specifier${30}
14340 !

14350 ! DEFINE PROGRAM STATE TO USER
14360 !
14370 OUTPUT 1;"***** LOAD OF FIT FILE FROM DISK *****"
*****"
14380 !
14390 ! GET FILE
14400 !
14410 INPUT "ENTER FILE NAME:",File_name$
14420 INPUT "SPECIFY LEFT OR RIGHT HAND DRIVE(L OR R):",Answer$
14430 IF Answer$="L" THEN
14440   File_specifier$=File_name$&":INTERNAL,4,1"
14450 ELSE
14460   File_specifier$=File_name$&":INTERNAL,4,0"
14470 END IF
14480 !
14490 ! POINT TO DISK FILE
14500 !
14510 ASSIGN @File TO File_specifier$;FORMAT OFF
14520 !
14530 ! ENTER FILE INTO COM AREA
14540 !
14550 ENTER @File,1;Tau_n,Ox_cap,Sigma_s,Area,Temp,Cal_points,Cd
14560 ENTER @File,2;Freq_fit(*)
14570 ENTER @File,3;Cond_p_fit(*)
14580 ENTER @File,4;Cap_p_fit(*)
14610 !
14620 ! EXIT LOAD SUBROUTINE
14630 !
14640 SUBEND!

```

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## VITA

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